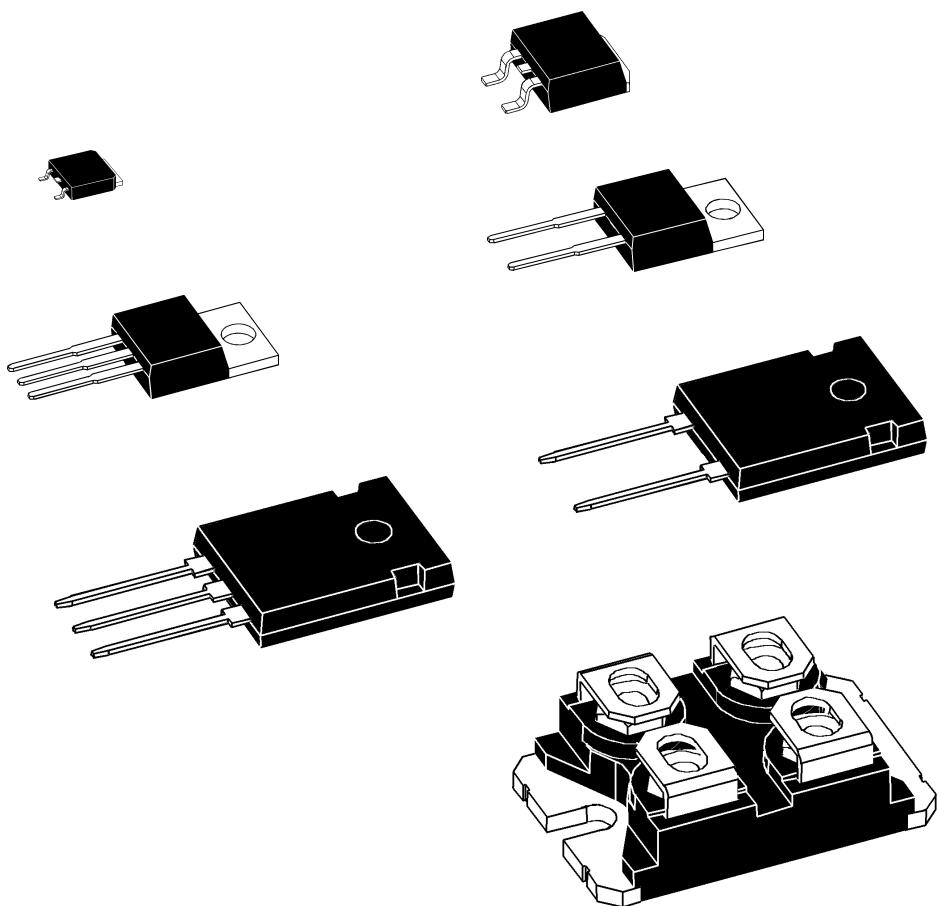
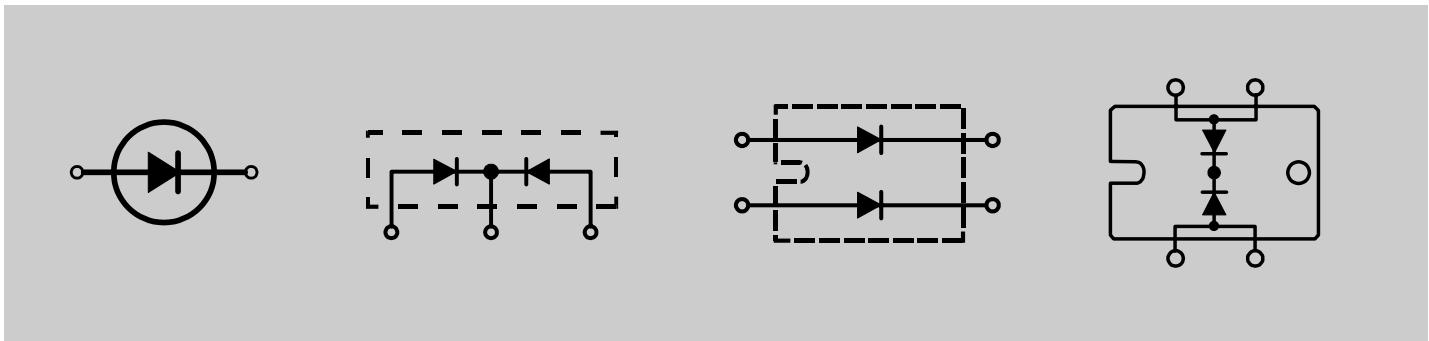
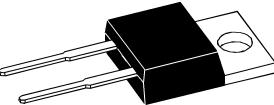
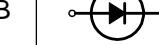
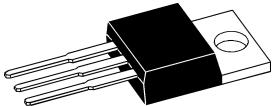
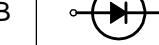
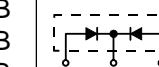
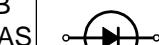
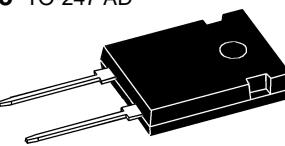
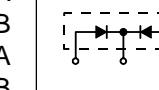
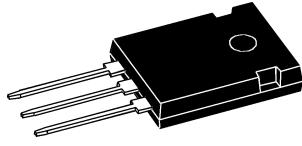
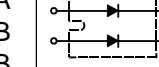
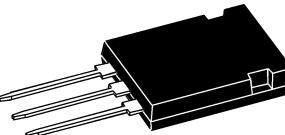
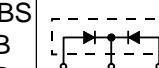
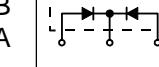


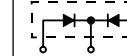
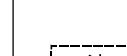
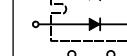
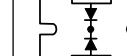
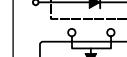
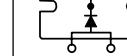
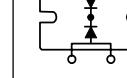
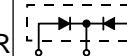
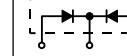
Power Schottky Rectifier Diodes



Contents

Package style		Voltage V_{RRM} V	Current I_{FAV} A	V_F V	Type	Version	Circuit Diagram	Page	
								D2 -	
1 TO-220 AC		1 6 6	15 15 15	20 2x 20 2x 35	0.33 0.32 0.33	DSS 20 DSSK 40 DSSK 70	B B B	 	4 6 8
2 TO-220 AB		1 2 6 5	25 25 25 25	25 2x 25 2x 25 2x 40	0.44 0.44 0.42 0.39	DSS 25 DSSK 48 DSSK 50 DSSK 80	B B B B	 	10 12 13 16
3 TO-263 AB		3 5	30 30	2x 25 2x 40	0.35 0.39	DSSK 48 DSSK 80	BS B		15 16
4 TO-252 AA		4 1 1 1 / 3 1 1 5	45 45 45 45 45 45 45	6 10 10 16 16 25 60	0.53 0.58 0.40 0.57 0.42 0.59 0.57	DSS 6 DSS 10 DSS 10 DSS 16 DSS 16 DSS 25 DSS 60	A A B A/AS B A B	 	17 18 20 22 24 26 28
5 TO-247 AD		2 2 2 2 6 6 6 6	45 45 45 45 45 45 45 45	2x 10 2x 10 2x 14 2x 14 2x 15 2x 15 2x 30 2x 30	0.58 0.40 0.57 0.42 0.57 0.41 0.60 0.44	DSSK 20 DSSK 20 DSSK 28 DSSK 28 DSSK 30 DSSK 30 DSSK 60 DSSK 60	A B A B A B A B		30 32 34 36 37 39 41 43
6 TO-247 AD		8 8 8	45 45 45	2x 60 2x 80 2x 120	0.66 0.64 0.59	DSS 2x 61 DSS 2x 81 DSS 2x 121	A B B		47 49 51
7 ISOPLUS 247™		8 2/3 6 6	45 60 60 60	2x 160 2x 15 2x 20 2x 40	0.73 0.52 0.50 0.51	DSS 2x 160 DSSK 28 DSSK 40 DSSK 80	A B/BS B B	 	53 55 56 57
		6 6	80 80	2x 20 2x 35	0.57 0.66	DSSK 40 DSSK 70	B A		58 59

Contents

Package style		Voltage V_{RRM} V	Current I_{FV} A	V_F V	Type	Version	Circuit Diagram	Page D2 -
8 SOT-227 B, miniBLOC	1 / 3	100	10	0.65	DSS 10	A/AS		60
	1 / 3	100	16	0.64	DSS 16	A/AS		62
	2	100	2x 8	0.65	DSSK 16	A/AS		64
	2	100	2x 15	0.64	DSSK 28	A		66
	6	100	2x 15	0.64	DSSK 30	A		67
	6	100	2x 25	0.65	DSSK 50	A		69
	8	100	2x 40	0.70	DSS 2x 41	A		71
	8	100	2x 60	0.73	DSS 2x 61	A		73
	8	100	2x 160	0.80	DSS 2x 160	A		75
	2	130/150	2x 10	0.65	DSSK 20	A		77
	6 / 7	130/150	2x 30	0.69	DSSK 60	A/AR		79
	8	150	2x 100	0.78	DSSK 2x101	A		81
	2	180	2x 5	0.62	DSSK 10	A		83
	6	180	2x 15	0.72	DSSK 30	A		85

Dimensions

D2 - 87-88

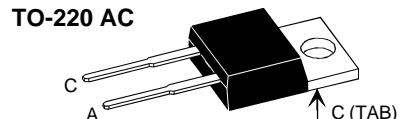
Note: .. S = SMD package
 .. R = ISOPLUS™ (DCB isolated package)

Power Schottky Rectifier

I_{FAV} = 20 A
V_{RRM} = 15 V
V_F = 0.33 V

Preliminary Data

V _{RSM}	V _{RRM}	Type
V	V	
15	15	DSS 20-0015B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAVM}	T _C = 135°C; rectangular, d = 0.5	20	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	350	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dV/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	10 200	mA mA
V _F	I _F = 20 A; T _{VJ} = 125°C I _F = 20 A; T _{VJ} = 25°C I _F = 40 A; T _{VJ} = 125°C	0.33 0.45 0.43	V V V
R _{thJC} R _{thCH}		0.5	1.4 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

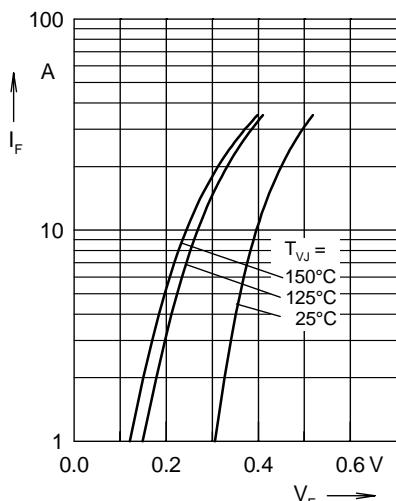


Fig. 1 Maximum forward voltage drop characteristics

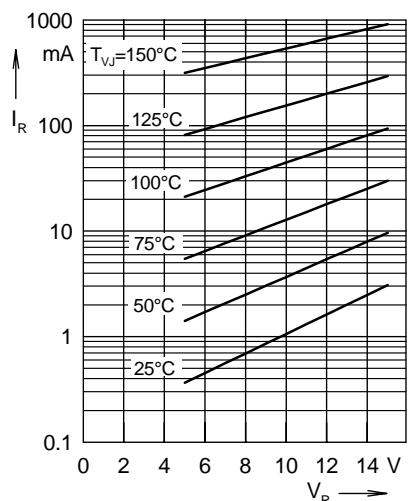


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

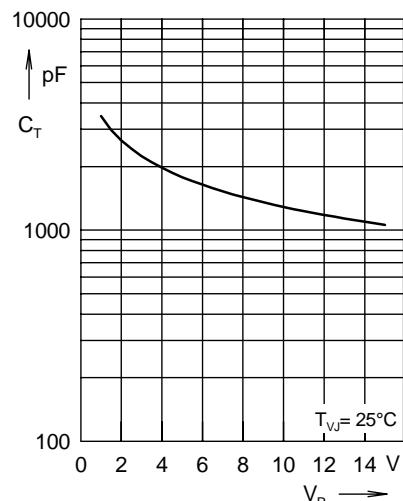


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

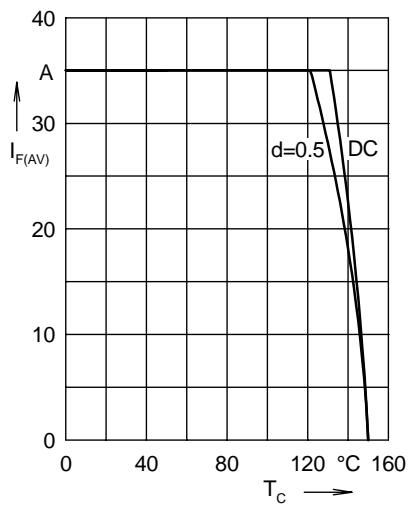


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

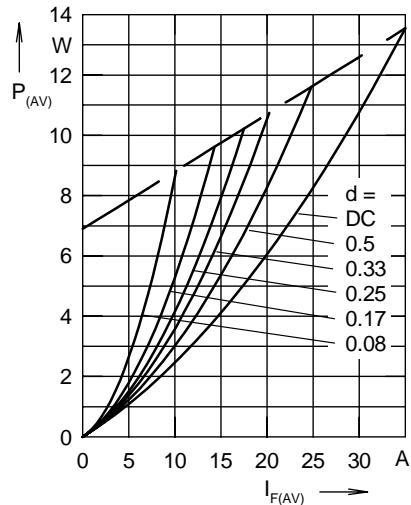


Fig. 5 Forward power loss characteristics

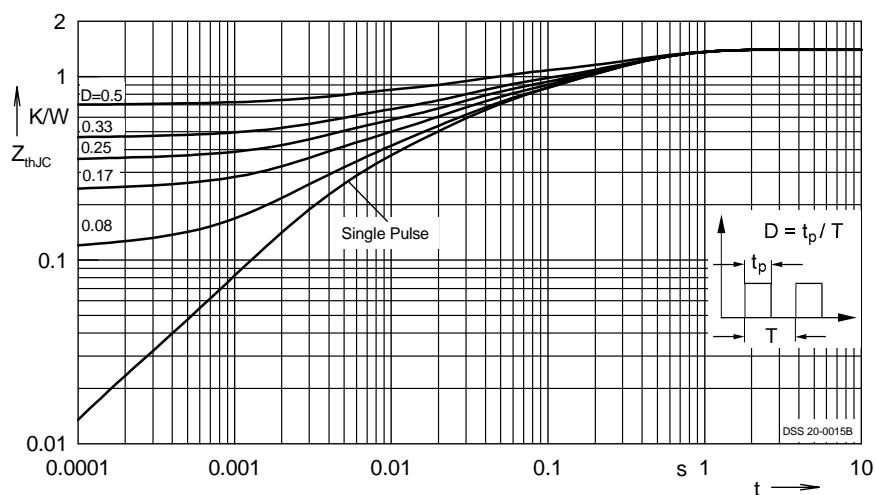
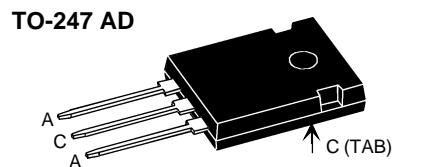
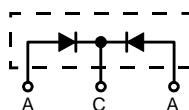


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Power Schottky Rectifier with common cathode

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
15	15	DSSK 40-0015B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		50	A
I_{FAV}	$T_c = 135^\circ\text{C}$; rectangular, $d = 0.5$	20	A
I_{FAV}	$T_c = 135^\circ\text{C}$; rectangular, $d = 0.5$; per device	40	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	350	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_c = 25^\circ\text{C}$	90	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	① $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	10 200	mA mA
V_F	$I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 40 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.32 0.44 0.41	V V V
R_{thJC}		1.4	K/W
R_{thCH}		0.25	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

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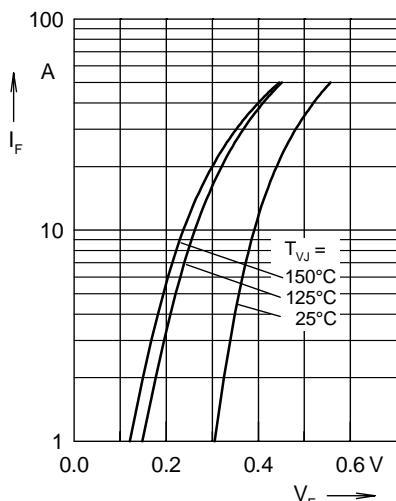


Fig. 1 Maximum forward voltage drop characteristics

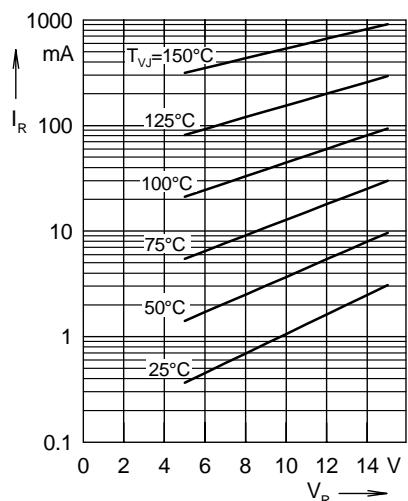


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

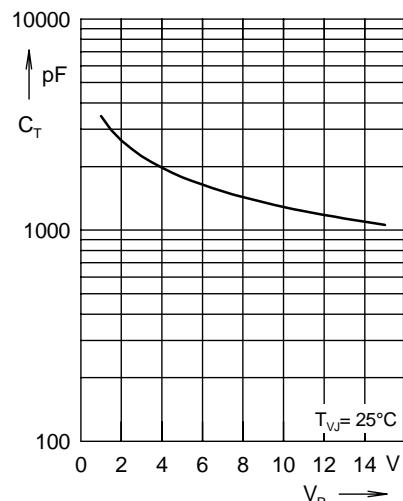


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

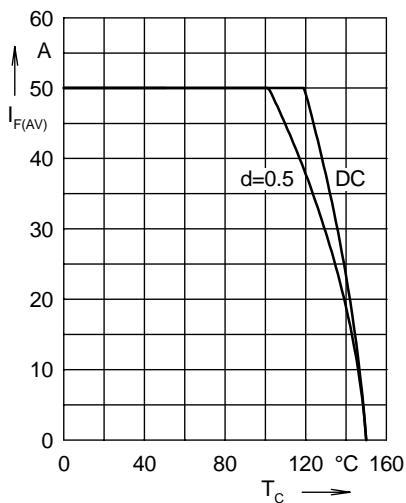


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

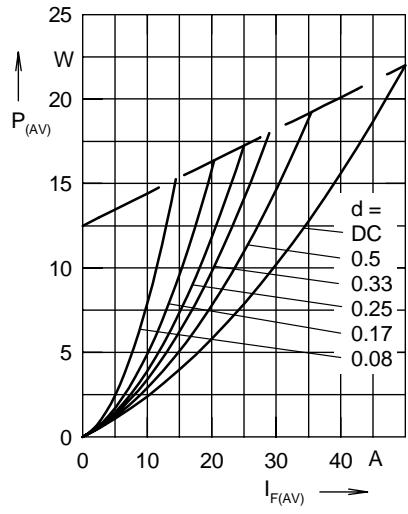


Fig. 5 Forward power loss characteristics

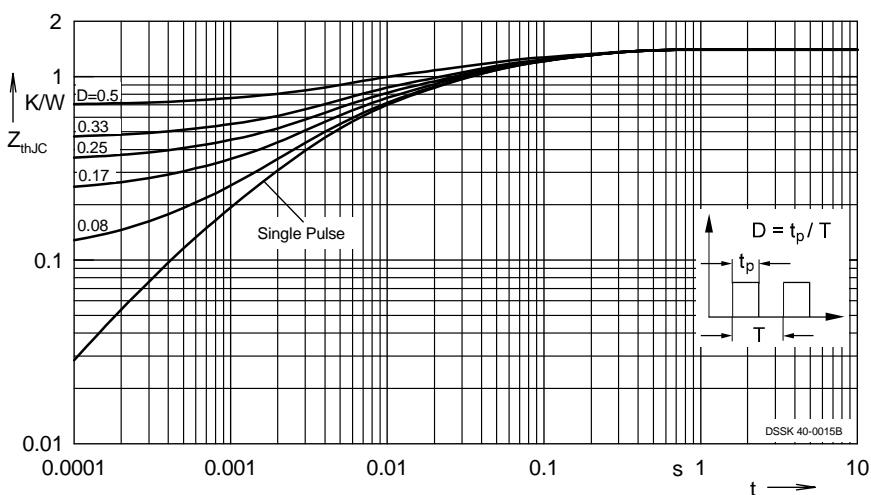


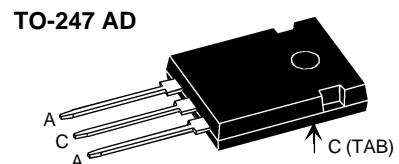
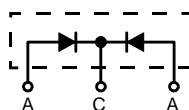
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
15	15	DSSK 70-0015B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$	35	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$; per device	70	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	660	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	115	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$\textcircled{1}$ $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	20 350	mA mA
V_F	$I_F = 35 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 35 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 70 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.33 0.45 0.45	V V V
R_{thJC}		1.1	K/W
R_{thCH}		0.25	K/W

Pulse test: $\textcircled{1}$ Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

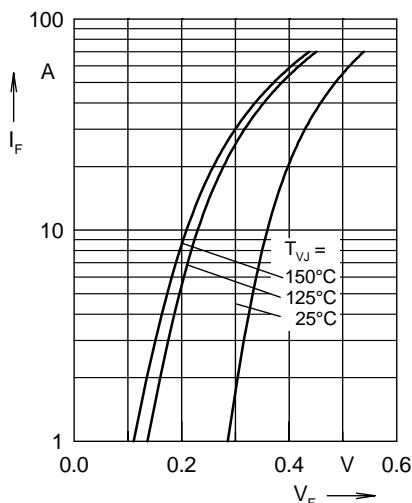


Fig. 1 Maximum forward voltage drop characteristics

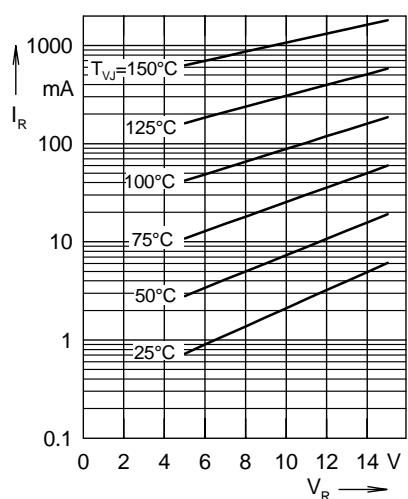


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

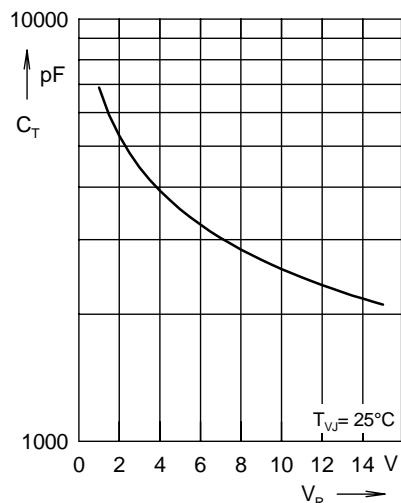


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

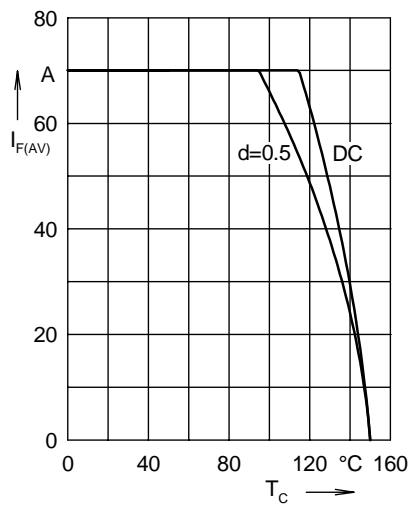


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

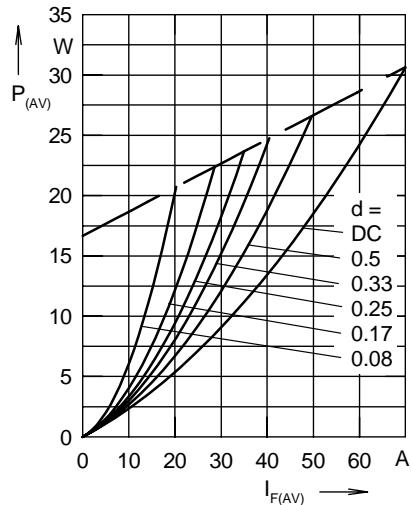


Fig. 5 Forward power loss characteristics

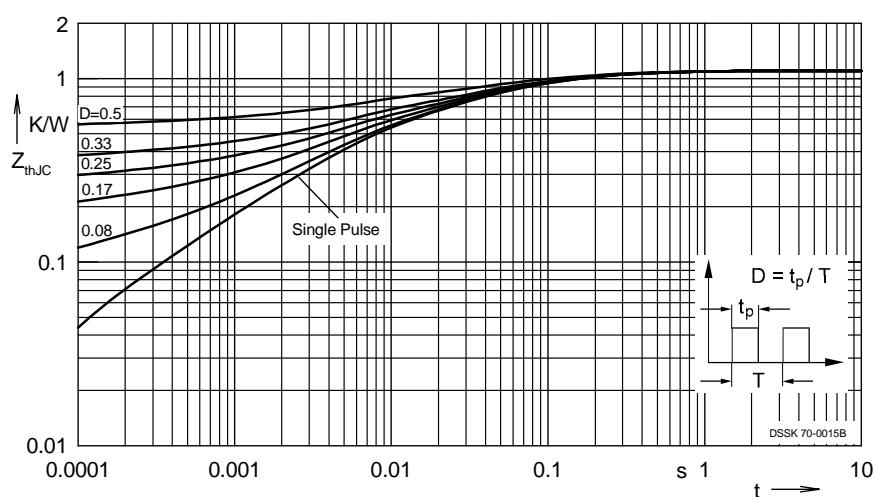


Fig. 6 Transient thermal impedance junction to case at various duty cycles

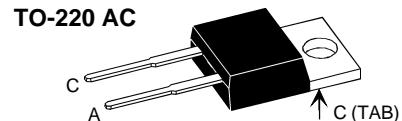
Note: All curves are per diode

Power Schottky Rectifier

I_{FAV} = 25 A
V_{RRM} = 25 V
V_F = 0.44 V

Preliminary Data

V _{RSM}	V _{RRM}	Type
V	V	
25	25	DSS 25-0025B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAVM}	T _C = 125°C; rectangular, d = 0.5	25	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	330	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dv/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	20 80	mA mA
V _F	I _F = 25 A; T _{VJ} = 125°C I _F = 25 A; T _{VJ} = 25°C I _F = 50 A; T _{VJ} = 125 °C	0.44 0.52 0.66	V V V
R _{thJC}		1.4	K/W
R _{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

025

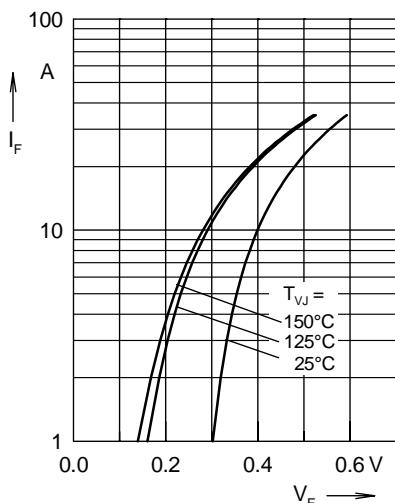


Fig. 1 Maximum forward voltage drop characteristics

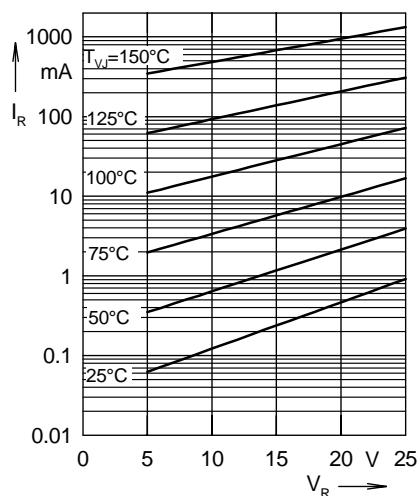


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

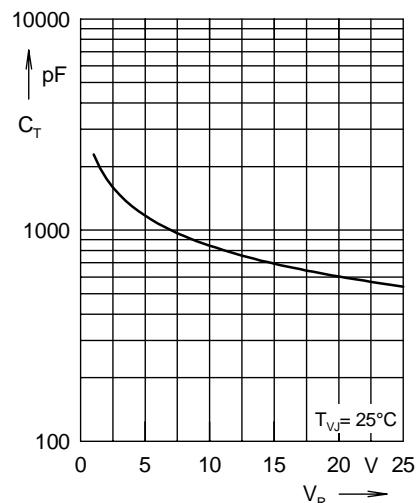


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

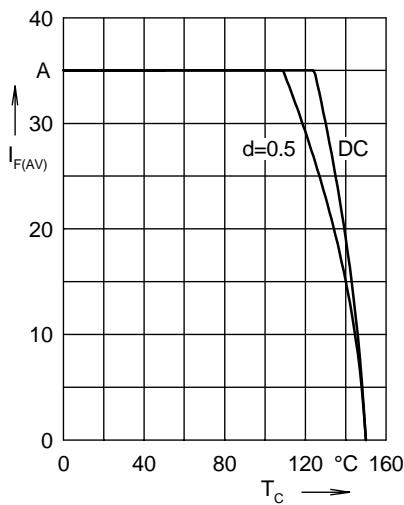


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

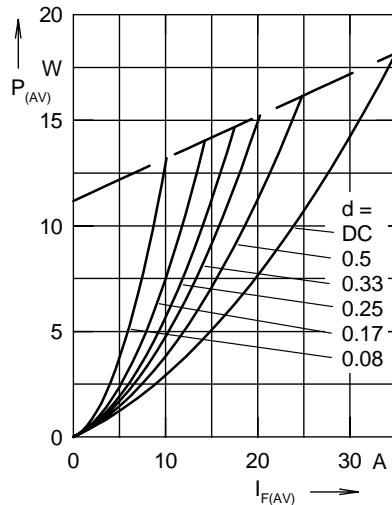


Fig. 5 Forward power loss characteristics

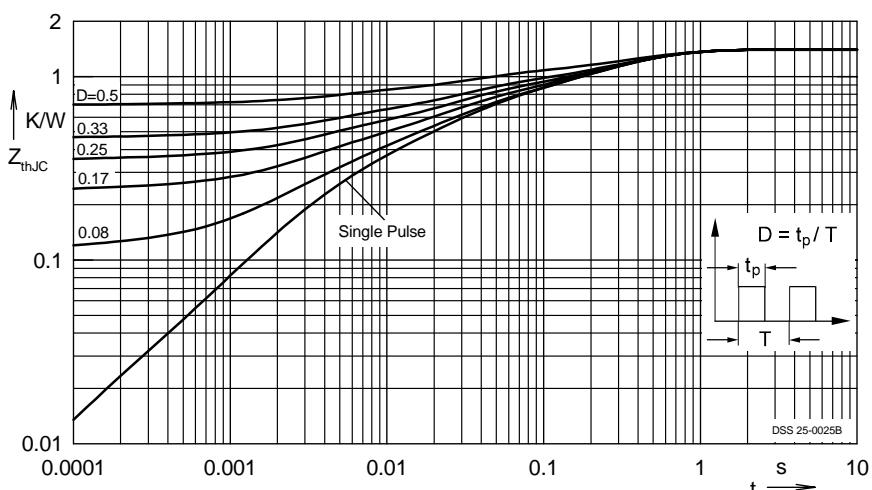


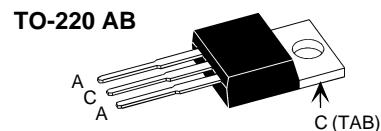
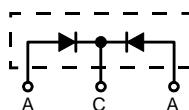
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
25	25	DSSK 48-0025B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$	25	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$; per device	50	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	420	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	105	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	① $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	20 60	mA mA
V_F	$I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 40 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.35 0.44 0.48	V V V
R_{thJC}		1.2	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

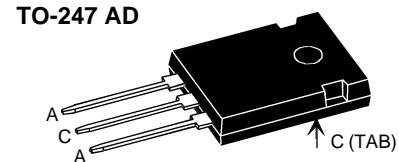
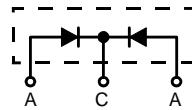
IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier with common cathode

I_{FAV} = 2x25 A
V_{RRM} = 25 V
V_F = 0.42 V

Preliminary Data

V _{RSM} V	V _{RRM} V	Type
25	25	DSSK 50-0025B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		50	A
I _{FAV}	T _C = 125°C; rectangular, d = 0.5	25	A
I _{FAV}	T _C = 125°C; rectangular, d = 0.5; per device	50	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	330	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dV/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	12 80	mA mA
V _F	I _F = 25 A; T _{VJ} = 125°C I _F = 25 A; T _{VJ} = 25°C I _F = 50 A; T _{VJ} = 125°C	0.42 0.51 0.63	V V V
R _{thJC} R _{thCH}		0.25	1.4 K/W K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

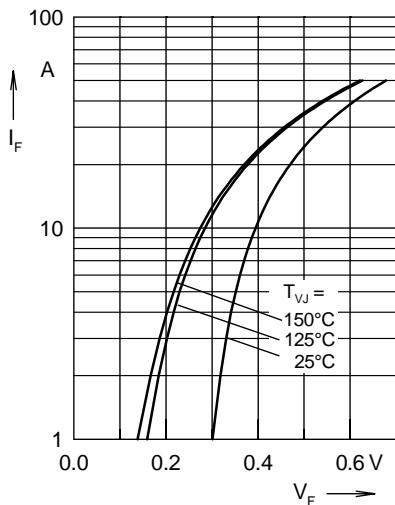


Fig. 1 Maximum forward voltage drop characteristics

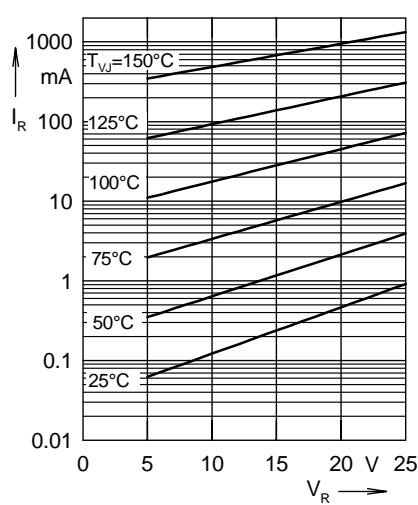


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

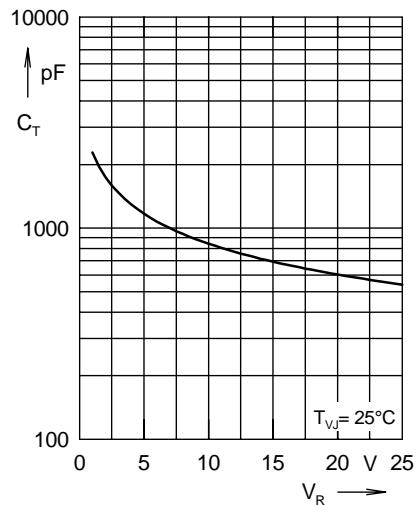


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

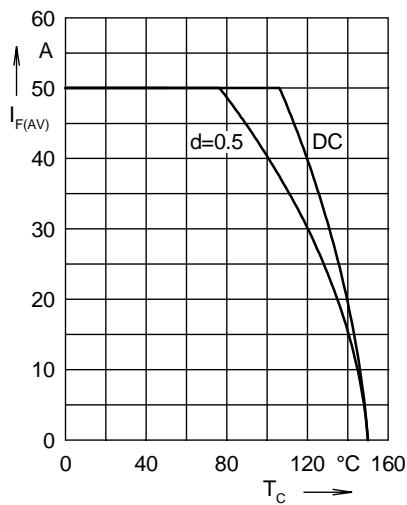


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

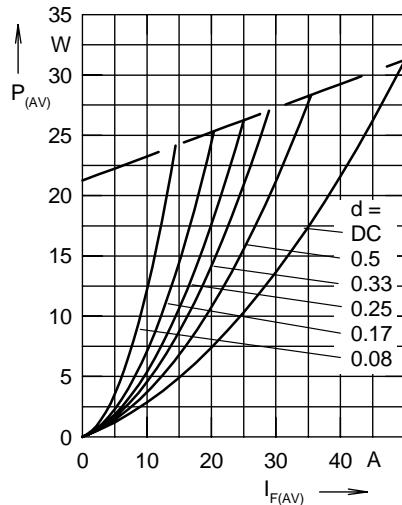


Fig. 5 Forward power loss characteristics

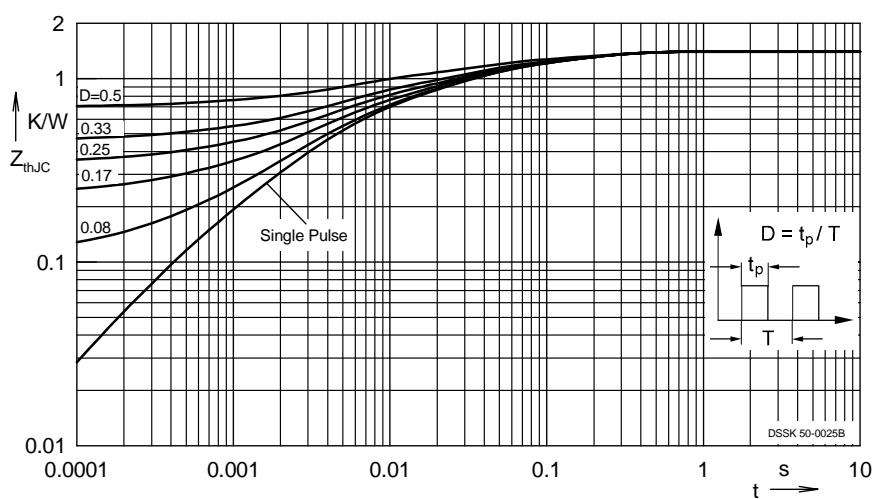


Fig. 6 Transient thermal impedance junction to case at various duty cycles

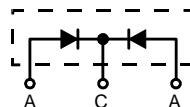
Note: All curves are per diode

Power Schottky Rectifier with common cathode

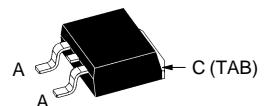
I_{FAV} = 2x25 A
V_{RRM} = 30 V
V_F = 0.35 V

Preliminary Data

V _{RSM}	V _{RRM}	Type
V	V	
30	30	DSSK 48-003BS



TO-263 AB
(BS-Type)



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings		
I _{FRMS}		35		A
I _{FAV}	T _C = 130°C; rectangular, d = 0.5	25		A
I _{FAV}	T _C = 130°C; rectangular, d = 0.5; per device	50		A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	420		A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ	
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd		A
(dV/dt) _{cr}		tbd	V/µs	
T _{VJ}		-55...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-55...+150	°C	
P _{tot}	T _C = 25°C	105		W
Weight	typical	2		g

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C; V _R = V _{RRM} T _{VJ} = 100°C; V _R = V _{RRM}	20 100	mA mA
V _F	I _F = 20 A; T _{VJ} = 125°C I _F = 20 A; T _{VJ} = 25°C I _F = 40 A; T _{VJ} = 125°C	0.35 0.44 0.48	V V V
R _{thJC} R _{thCH}	(Version B only)	0.5	1.2 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%

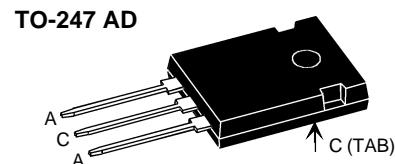
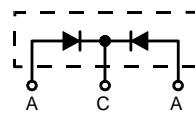
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

Power Schottky Rectifier with common cathode

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
25	25	DSSK 80-0025B
30	30	DSSK 80-003B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAV}	$T_c = 130^\circ\text{C}$; rectangular, $d = 0.5$	40	A
I_{FAV}	$T_c = 130^\circ\text{C}$; rectangular, $d = 0.5$; per device	80	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	800	A
E_{AS}	$I_{AS} = 6 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	10	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	6	A
$(dv/dt)_{cr}$		5000	V/ μ s
T_{VJ}		-55...+150	°C
T_{VJM}		150	°C
T_{stg}		-55...+150	°C
P_{tot}	$T_c = 25^\circ\text{C}$	90	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	① $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	40 250	mA mA
V_F	$I_F = 40 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 40 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 80 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.39 0.48 0.56	V V V
R_{thJC}		0.25	0.8
R_{thCH}			K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

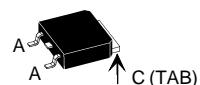
Power Schottky Rectifier

I_{FAV} = 6 A
V_{RRM} = 45 V
V_F = 0.53 V

V _{RSM} V	V _{RRM} V	Type DSS 6-0045AS	marking on product 6Y045AS
45	45		



TO-252 AA



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		20	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5	6	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	80	A
E _{AS}	I _{AS} = 13 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	24	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.3	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	50	W
Weight	typical	0.3	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	0.3 2.5	mA mA
V _F	I _F = 6 A; T _{VJ} = 125°C I _F = 6 A; T _{VJ} = 25°C I _F = 12 A; T _{VJ} = 125 °C	0.53 0.64 0.61	V V V
R _{thJC}		3.0	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

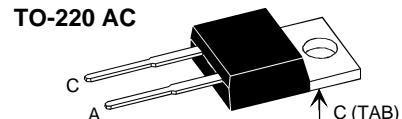
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
 Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier

I_{FAV} = 10 A
V_{RRM} = 45 V
V_F = 0.58 V

V _{RSM}	V _{RRM}	Type
V	V	
45	45	DSS 10-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5	10	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	140	A
E _{AS}	I _{AS} = 13 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	24	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.3	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	0.3 2.5	mA mA
V _F	I _F = 10 A; T _{VJ} = 125°C I _F = 10 A; T _{VJ} = 25°C I _F = 20 A; T _{VJ} = 125°C	0.58 0.68 0.70	V V V
R _{thJC} R _{thCH}		0.5	1.7 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

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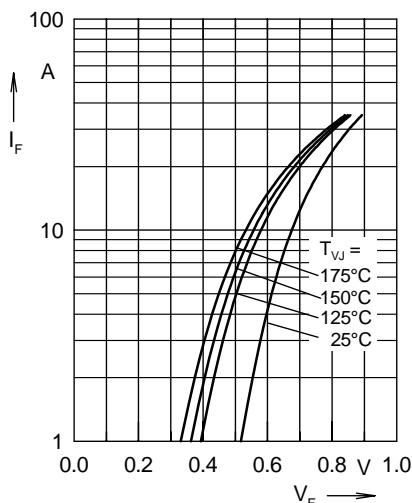


Fig. 1 Maximum forward voltage drop characteristics

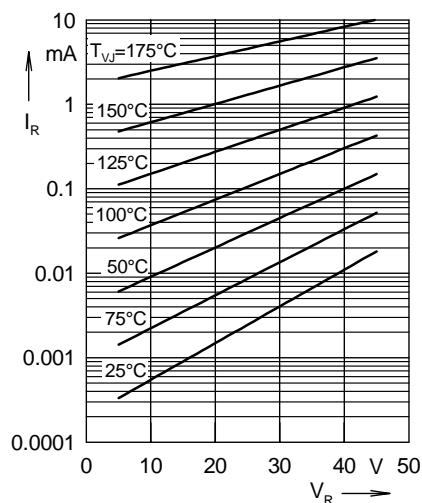


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

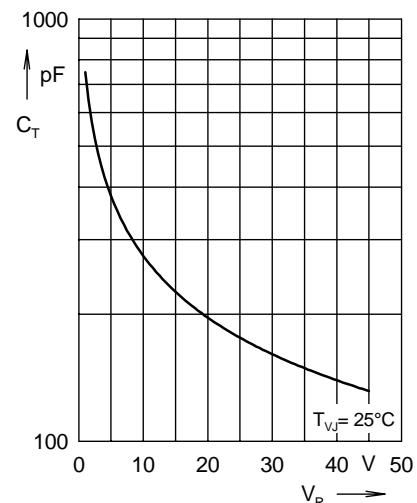


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

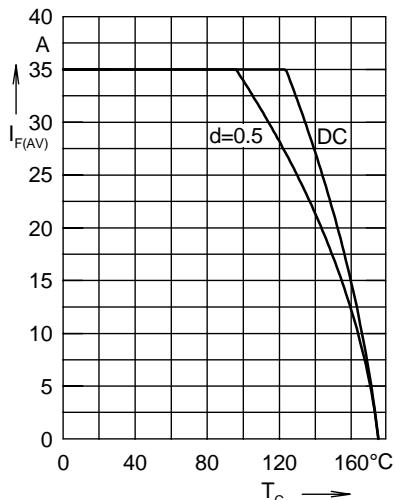


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

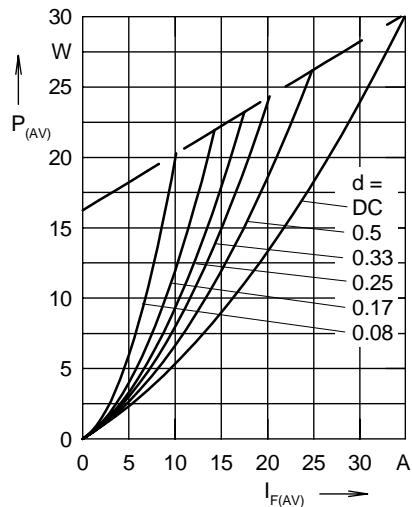


Fig. 5 Forward power loss characteristics

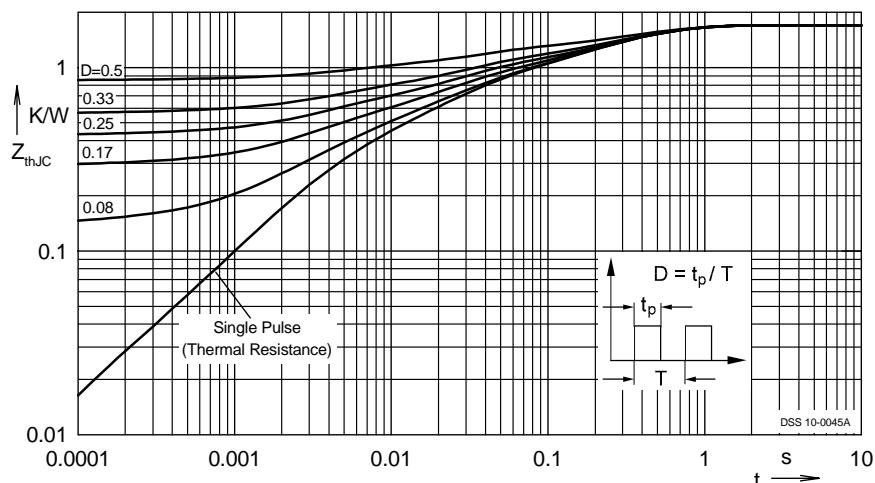


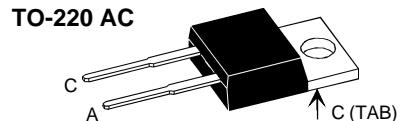
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

I_{FAV} = 10 A
V_{RRM} = 45 V
V_F = 0.40 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSS 10-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS} I _{FAV}	T _C = 135°C; rectangular, d = 0.5	35	A
		10	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	160	A
E _{AS}	I _{AS} = 13 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	24	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.3	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	75	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	5 50	mA mA
V _F	I _F = 10 A; T _{VJ} = 125°C I _F = 10 A; T _{VJ} = 25°C I _F = 20 A; T _{VJ} = 125 °C	0.45 0.51 0.70	V V V
R _{thJC} R _{thCH}		1.7 0.5	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

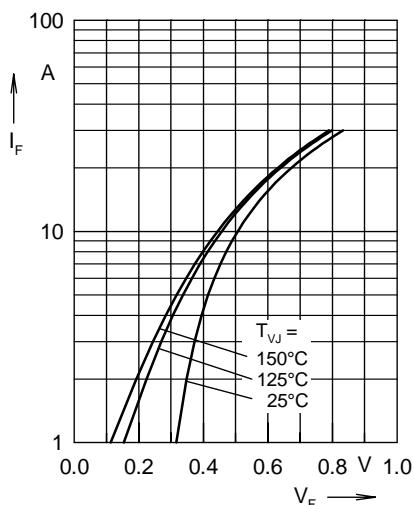


Fig. 1 Maximum forward voltage drop characteristics

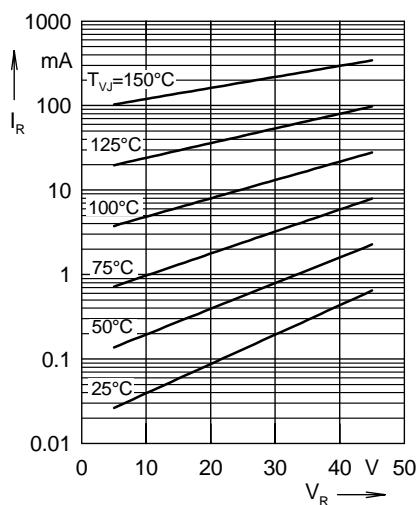


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

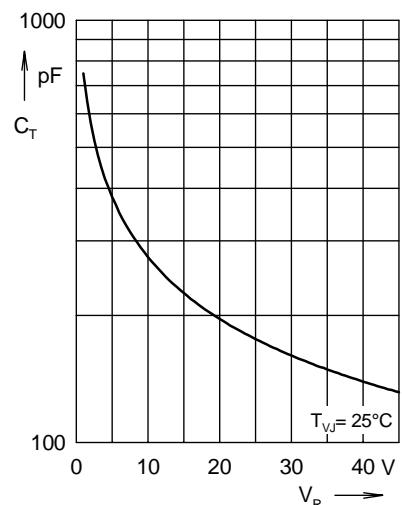


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

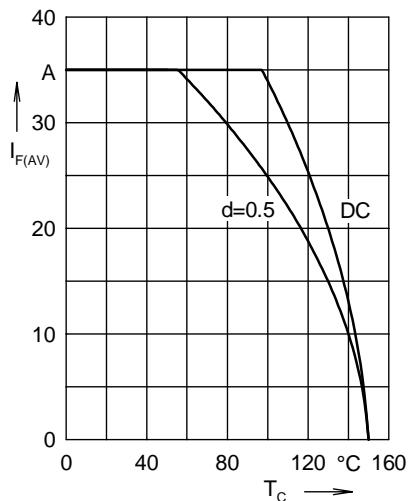


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

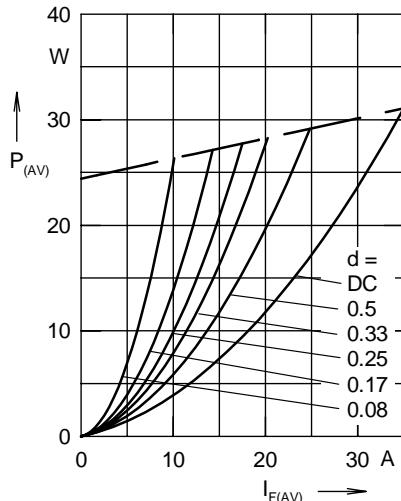


Fig. 5 Forward power loss characteristics

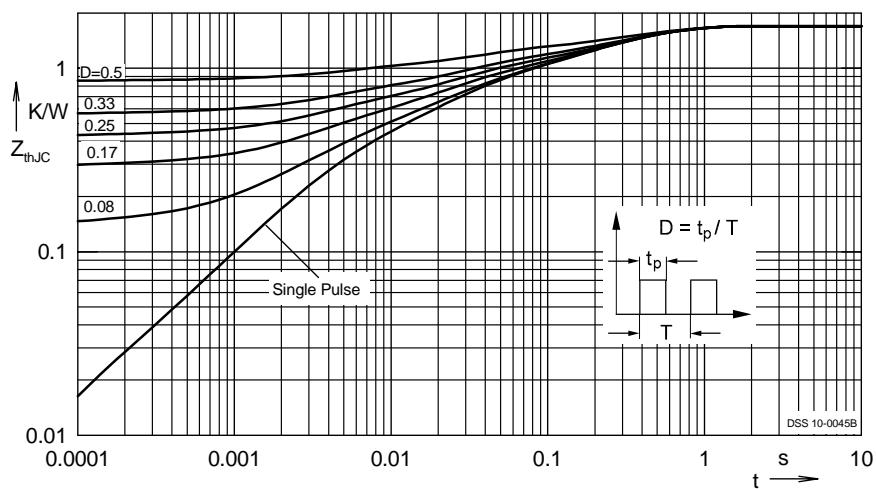


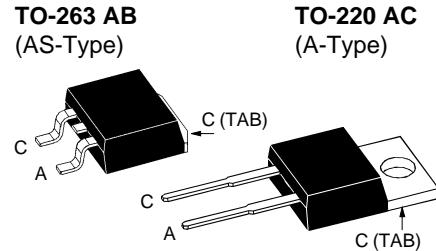
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

$I_{FAV} = 16 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.57 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSS 16-0045A
		DSS 16-0045AS

TO-263 AB
(AS-Type)

A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$	16	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	280	A
E_{AS}	$I_{AS} = 15 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	32	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.5	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	105	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5	mA mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.57 0.67 0.69	V V V
R_{thJC}		1.4	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

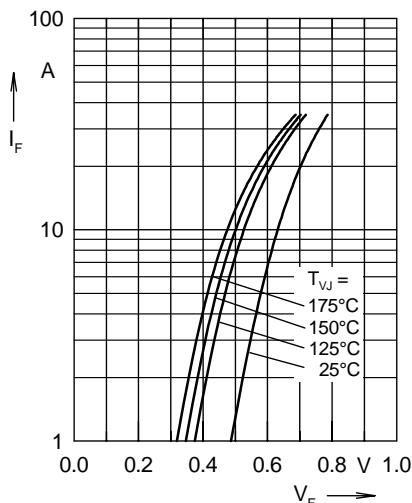


Fig. 1 Maximum forward voltage drop characteristics

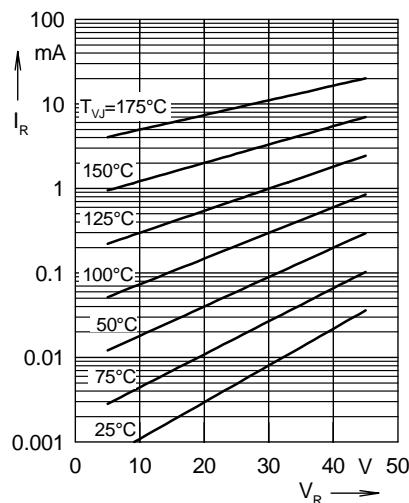


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

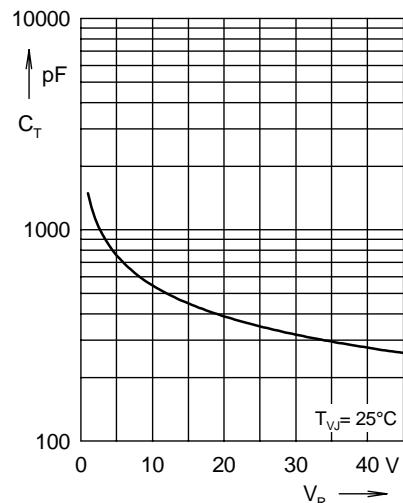


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

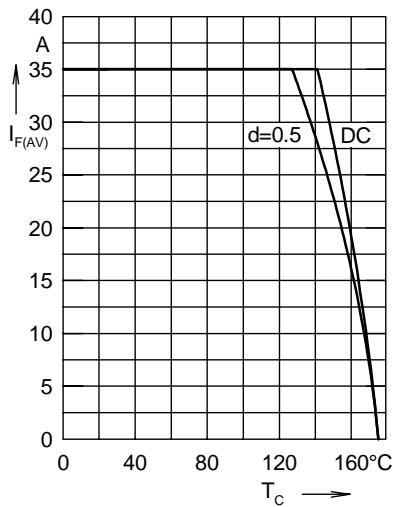


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

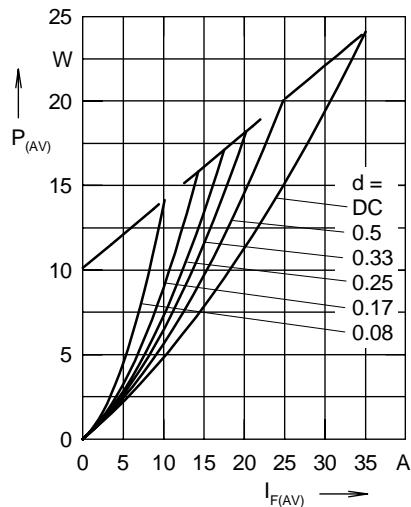


Fig. 5 Forward power loss characteristics

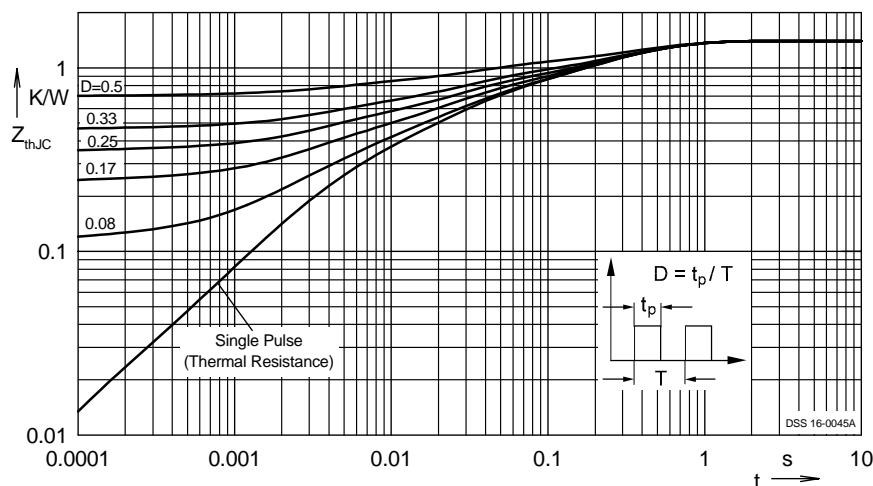


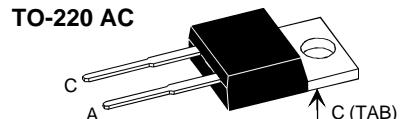
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

$I_{FAV} = 16 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.42 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSS 16-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$	16	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	320	A
E_{AS}	$I_{AS} = 15 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	32	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.5	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	90	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	10	mA
		100	mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.42 0.48 0.62	V
R_{thJC}		1.4	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

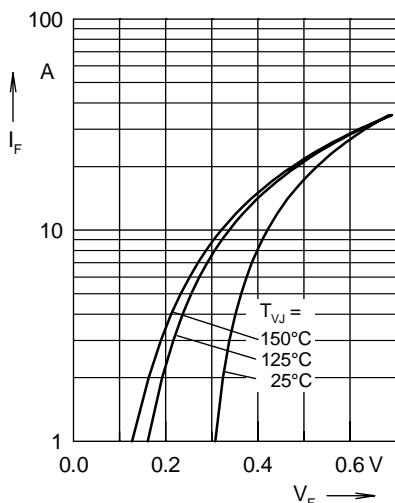


Fig. 1 Maximum forward voltage drop characteristics

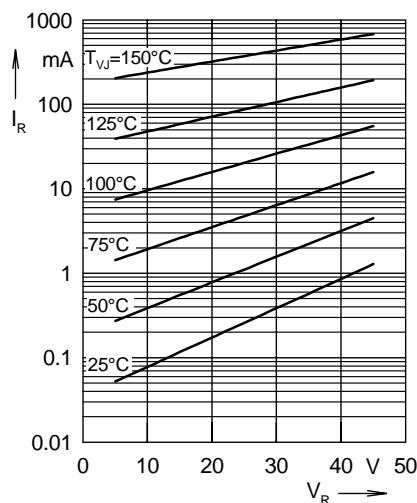


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

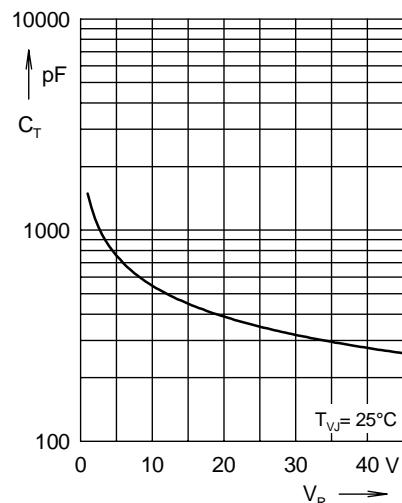


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

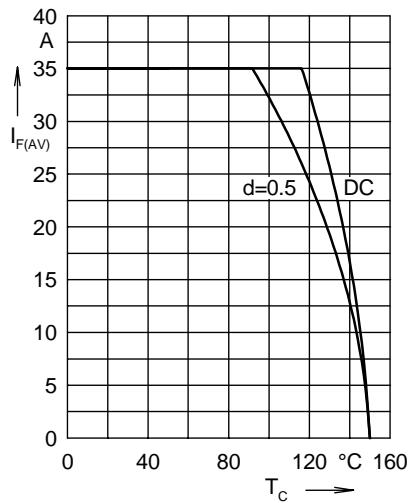


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

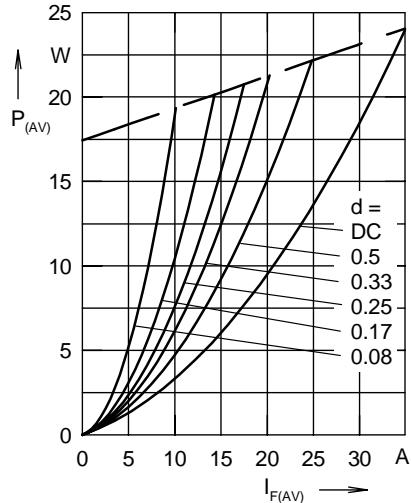


Fig. 5 Forward power loss characteristics

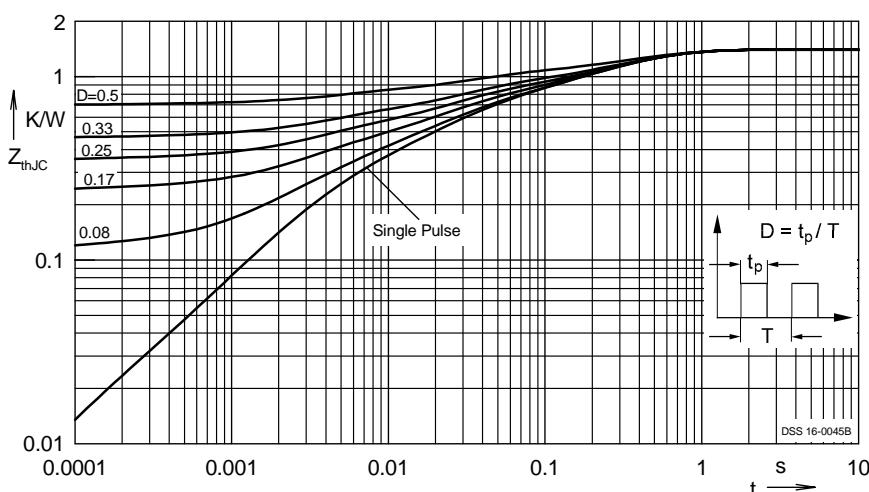


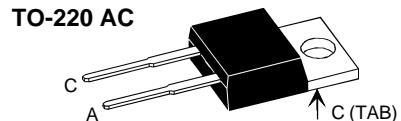
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

I_{FAV} = 25 A
V_{RRM} = 45 V
V_F = 0.59 V

V _{RSM}	V _{RRM}	Type
V	V	
45	45	DSS 25-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5	25	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	550	A
E _{AS}	I _{AS} = 18 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	46	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.8	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	135	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	1 10	mA mA
V _F	I _F = 25 A; T _{VJ} = 125°C I _F = 25 A; T _{VJ} = 25°C I _F = 50 A; T _{VJ} = 125°C	0.59 0.69 0.73	V V V
R _{thJC}		1.1	K/W
R _{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

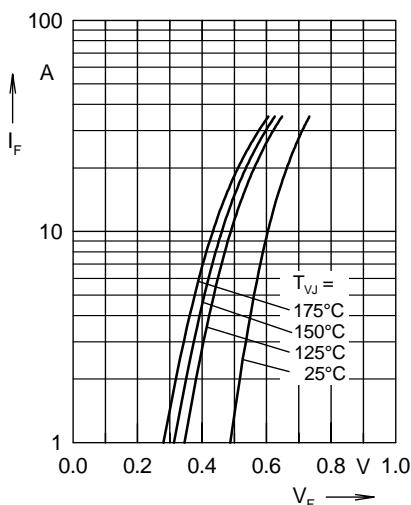


Fig. 1 Maximum forward voltage drop characteristics

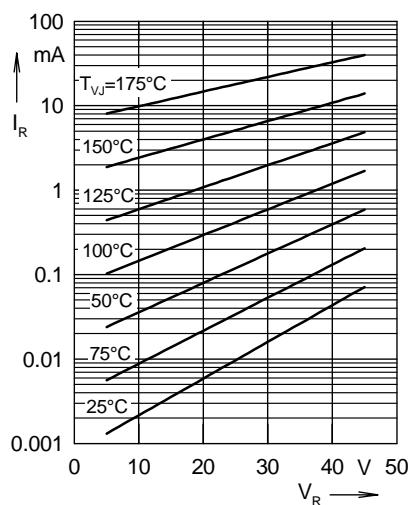


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

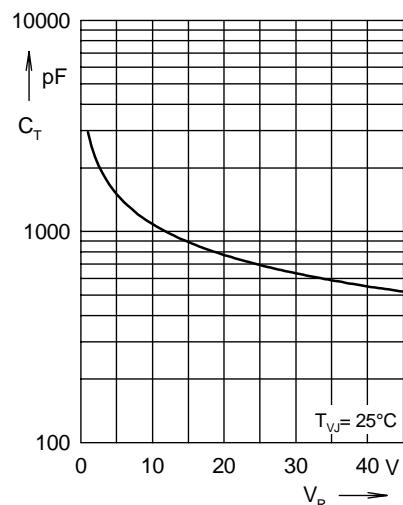


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

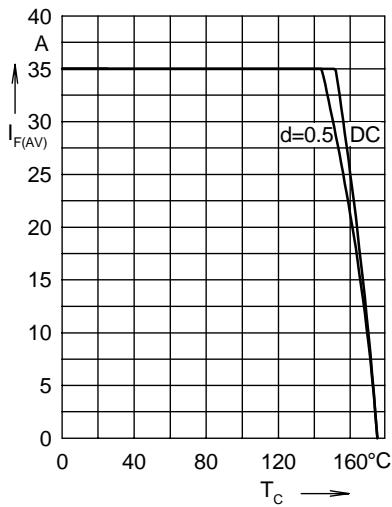


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

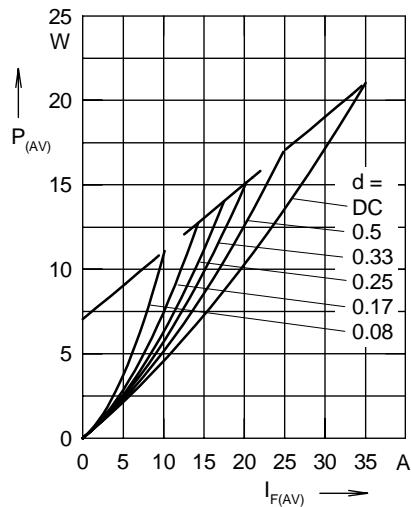


Fig. 5 Forward power loss characteristics

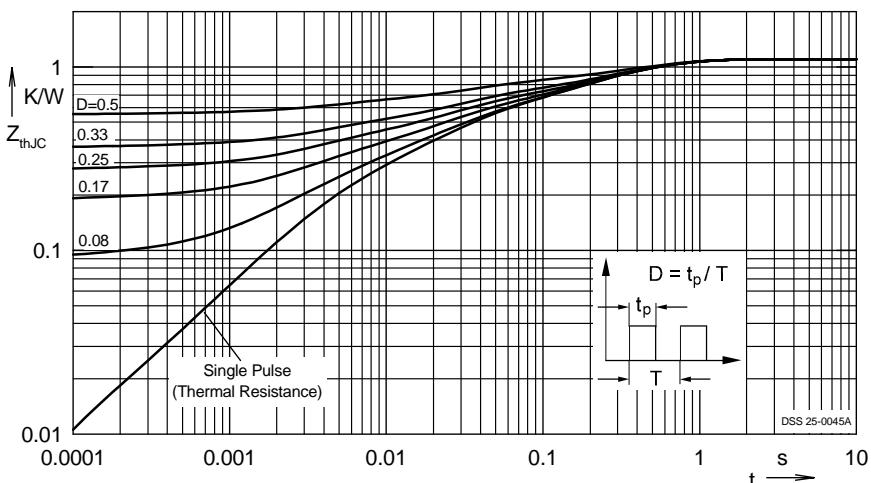


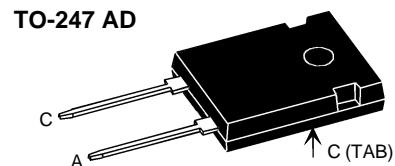
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

$I_{FAV} = 60 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.57 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSS 60-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAV}	$T_C = 100^\circ\text{C}$; rectangular, $d = 0.5$	60	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	900	A
E_{AS}	$I_{AS} = 20 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	57	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	2	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	155	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	10 250	mA mA
V_F	$I_F = 60 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 60 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 120 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.57 0.60 0.93	V V V
R_{thJC} R_{thCH}		0.8 0.25	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

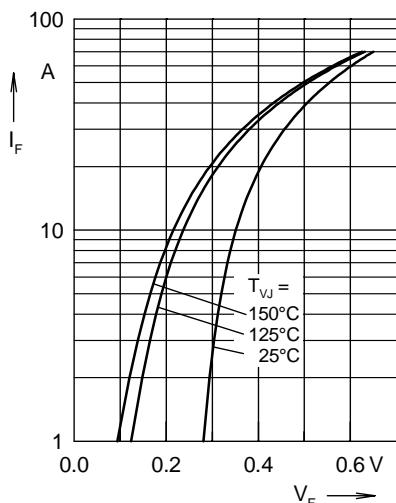


Fig. 1 Maximum forward voltage drop characteristics

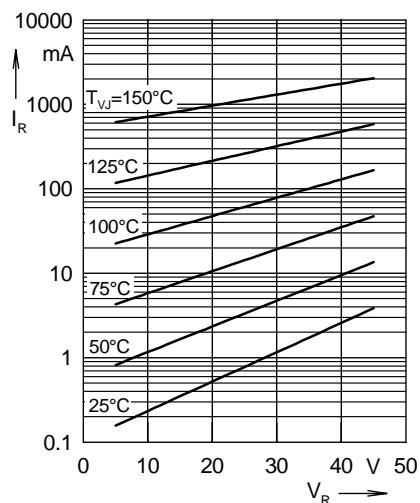


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

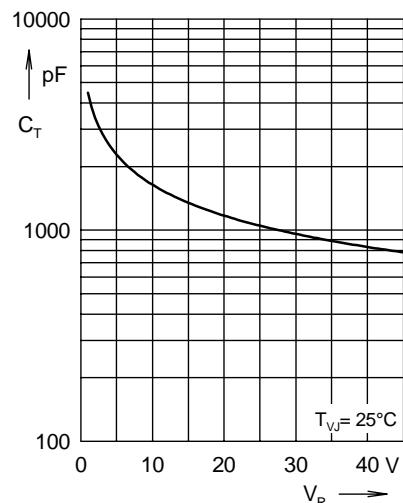


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

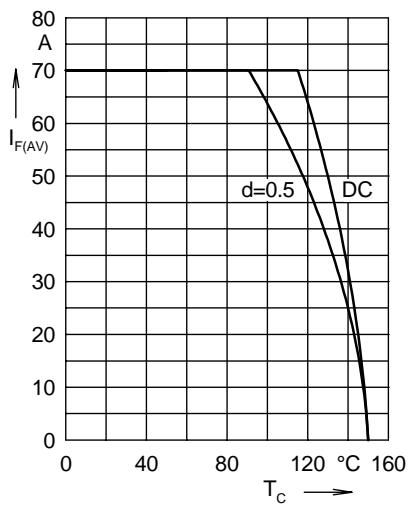


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

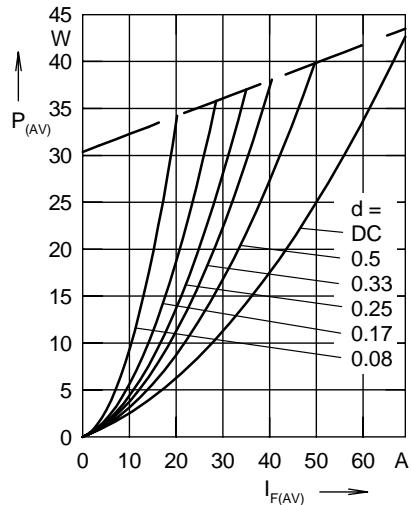


Fig. 5 Forward power loss characteristics

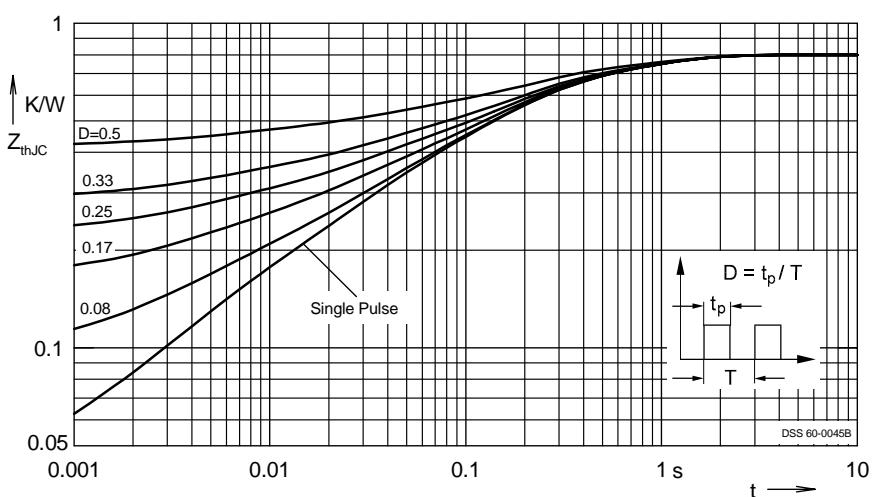


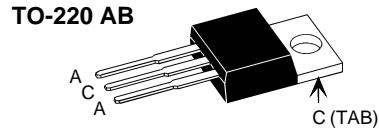
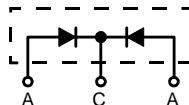
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 10 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.58 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSSK 20-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$	10	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$; per device	20	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	140	A
E_{AS}	$I_{AS} = 13 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	24	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.3	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	90	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.3 2.5	mA mA
V_F	$I_F = 10 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 10 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.58 0.68 0.70	V V V
R_{thJC}		1.7	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

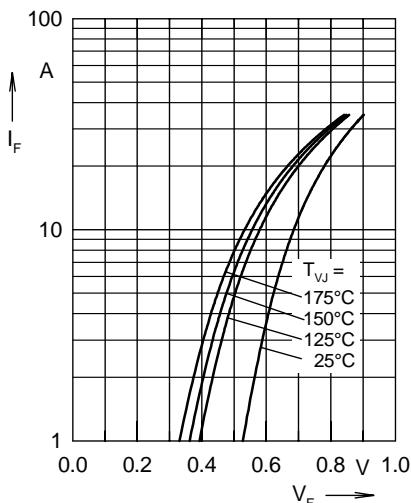


Fig. 1 Maximum forward voltage drop characteristics

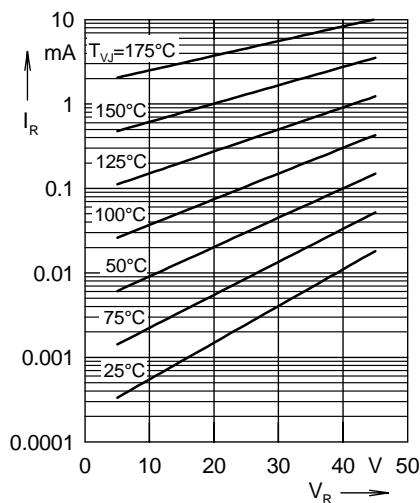


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

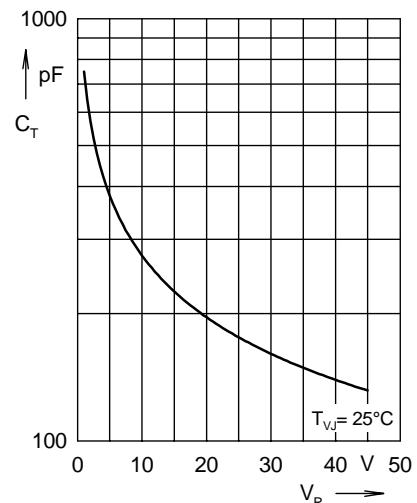


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

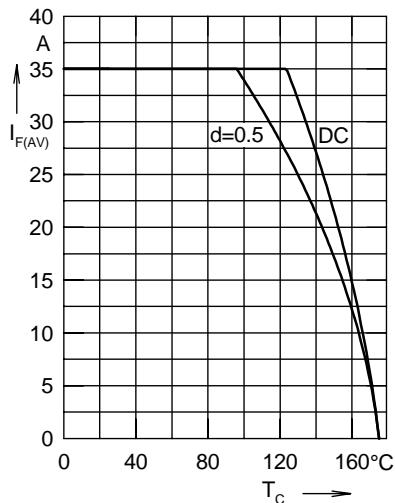


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

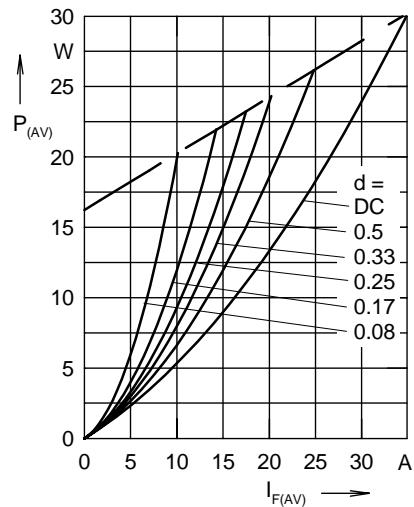


Fig. 5 Forward power loss characteristics

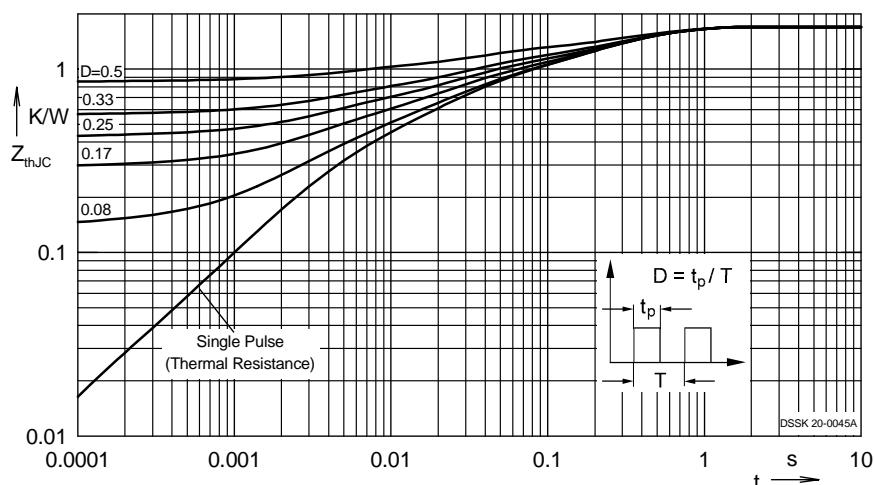


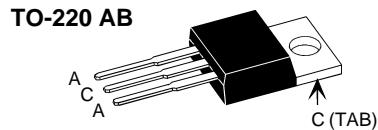
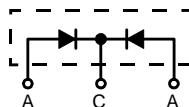
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 10 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.40 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSSK 20-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$	10	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$; per device	20	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	160	A
E_{AS}	$I_{AS} = 13 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	24	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.3	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	75	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	5 50	mA mA
V_F	$I_F = 10 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 10 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.45 0.51 0.70	V V V
R_{thJC} R_{thCH}		1.7 0.5	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

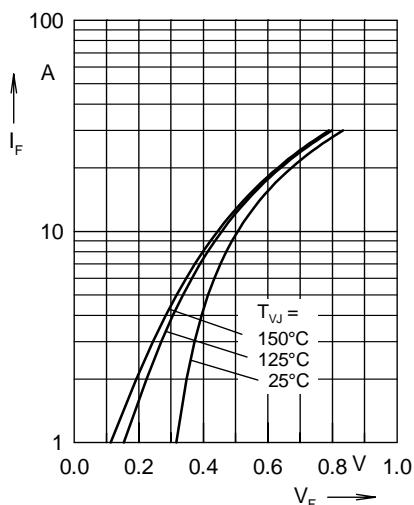


Fig. 1 Maximum forward voltage drop characteristics

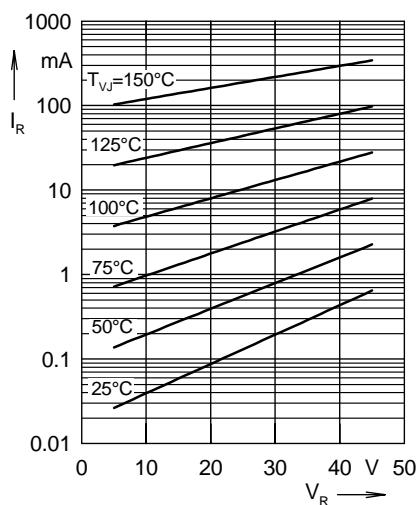


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

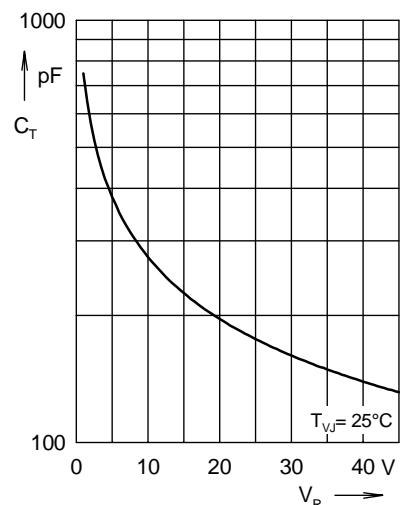


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

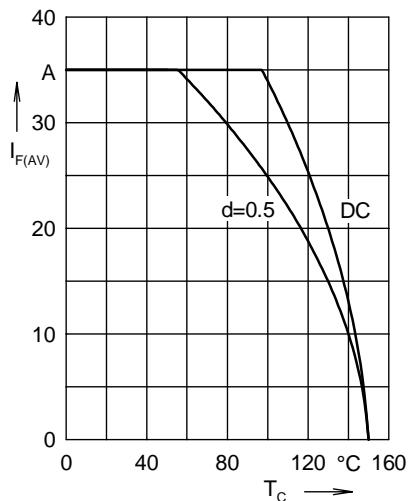


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

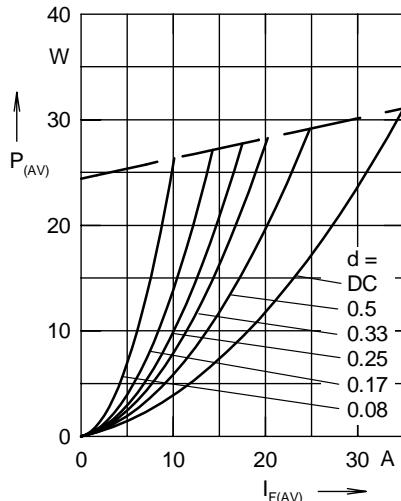


Fig. 5 Forward power loss characteristics

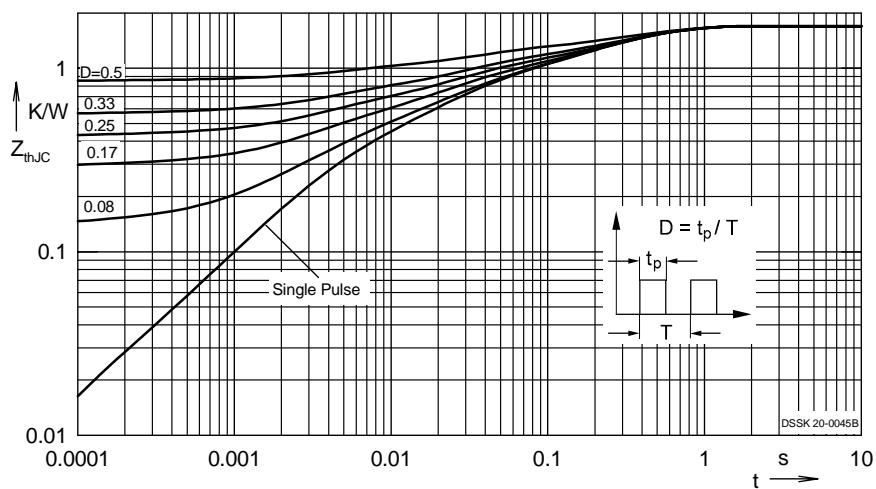


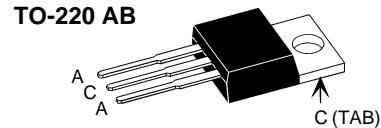
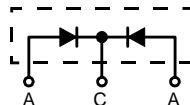
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 14 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.57 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSSK 28-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$	14	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$; per device	28	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	280	A
E_{AS}	$I_{AS} = 15 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	32	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.5	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	105	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5	mA mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.57 0.67 0.69	V V V
R_{thJC}		1.4	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

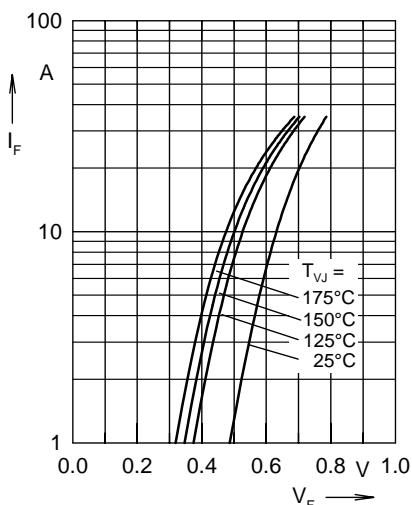


Fig. 1 Maximum forward voltage drop characteristics

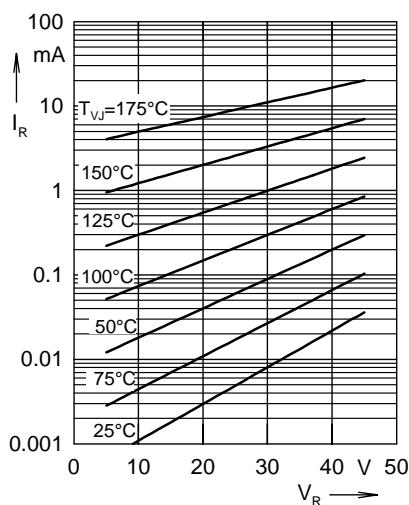


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

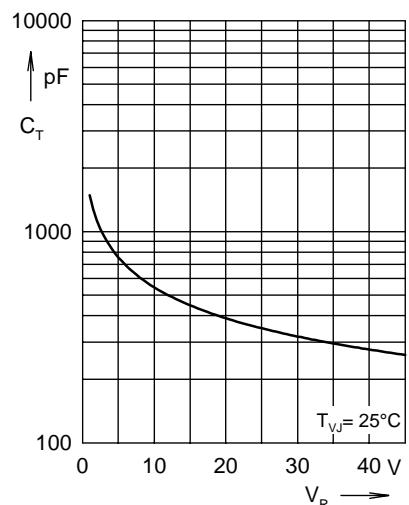


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

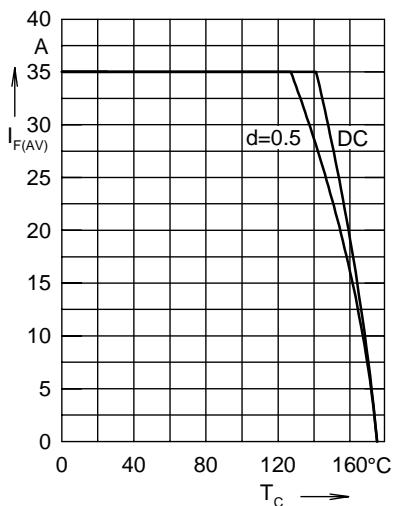


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_c

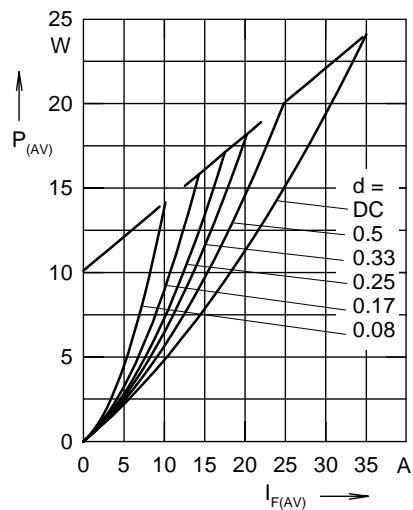


Fig. 5 Forward power loss characteristics

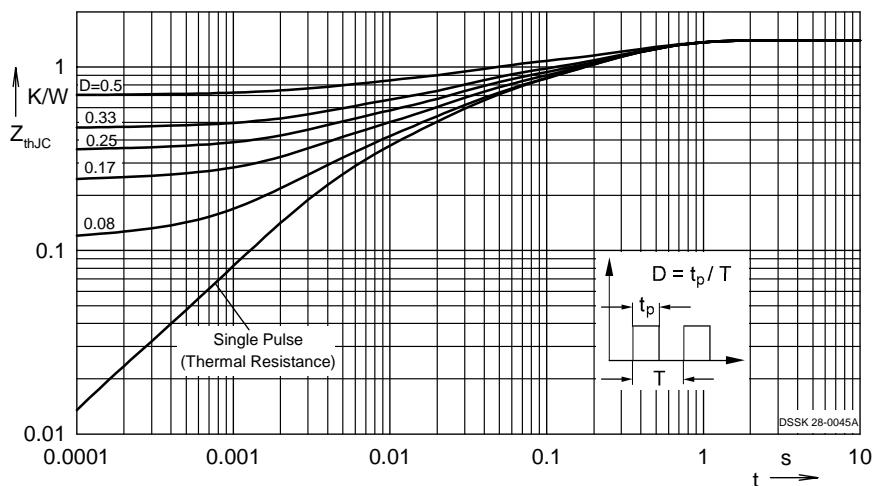


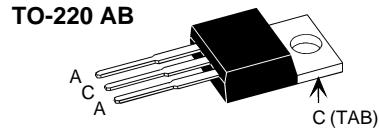
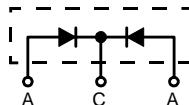
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 14 \text{ A}$
 $V_{RRM} = 45 \text{ V}$
 $V_F = 0.42 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSSK 28-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$	14	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$; per device	28	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	320	A
E_{AS}	$I_{AS} = 15 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	32	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1.5	A
$(dv/dt)_{cr}$		1000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	90	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	10 100	mA mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.42 0.48 0.62	V V V
R_{thJC} R_{thCH}		1.4 0.5	K/W K/W

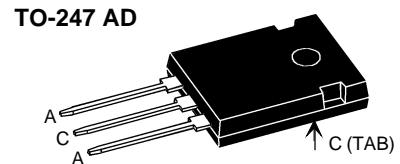
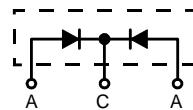
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier with common cathode

I_{FAV} = 2x15 A
V_{RRM} = 45 V
V_F = 0.57 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSSK 30-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		50	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5	15	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5; per device	30	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	280	A
E _{AS}	I _{AS} = 15 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	32	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.5	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	105	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	0.5 5	mA mA
V _F	I _F = 15 A; T _{VJ} = 125°C I _F = 15 A; T _{VJ} = 25°C I _F = 30 A; T _{VJ} = 125°C	0.57 0.66 0.67	V V V
R _{thJC}		1.4	K/W
R _{thCH}		0.25	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

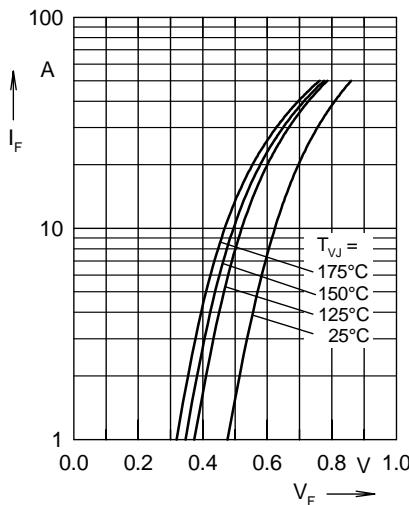


Fig. 1 Maximum forward voltage drop characteristics

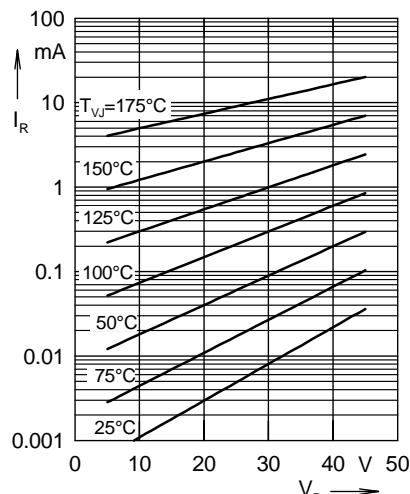


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

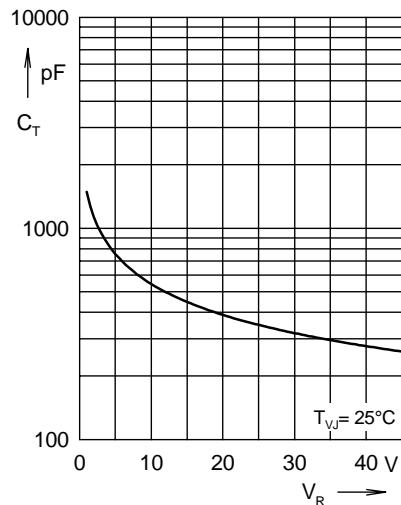


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

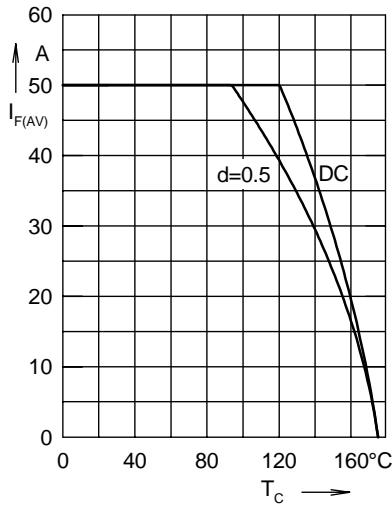


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

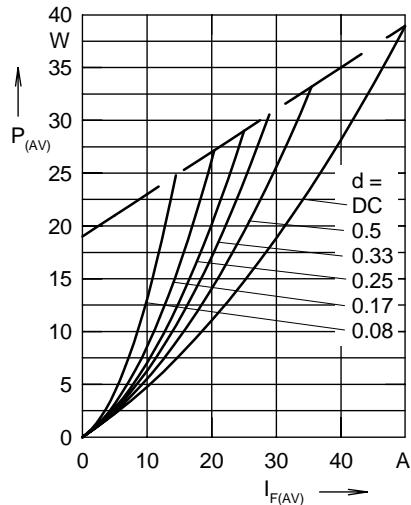


Fig. 5 Forward power loss characteristics

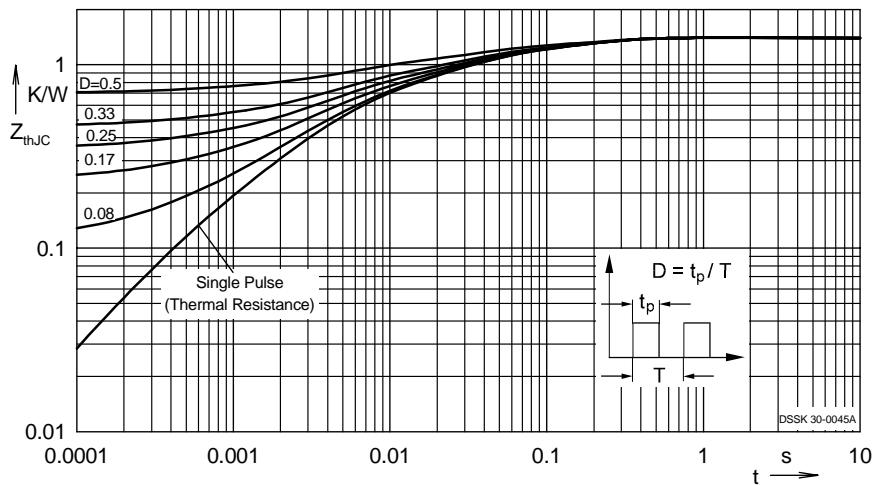


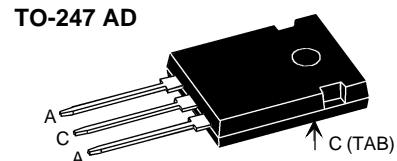
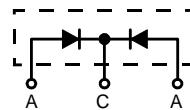
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x15 A
V_{RRM} = 45 V
V_F = 0.41 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSSK 30-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		50	A
I _{FAV}	T _C = 135°C; rectangular, d = 0.5	15	A
I _{FAV}	T _C = 135°C; rectangular, d = 0.5; per device	30	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	320	A
E _{AS}	I _{AS} = 15 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	32	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.5	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	10 100	mA mA
V _F	I _F = 15 A; T _{VJ} = 125°C I _F = 15 A; T _{VJ} = 25°C I _F = 30 A; T _{VJ} = 125°C	0.41 0.47 0.60	V V V
R _{thJC} R _{thCH}		0.25	1.4 K/W K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

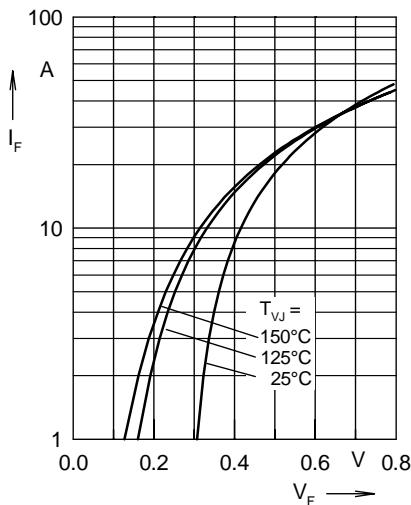


Fig. 1 Maximum forward voltage drop characteristics

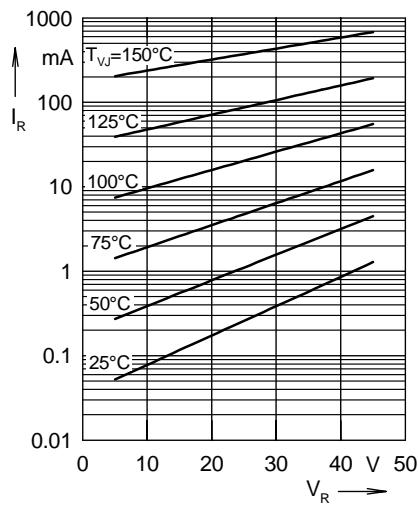


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

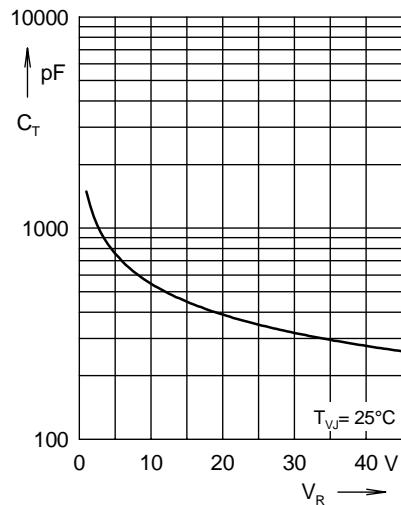


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

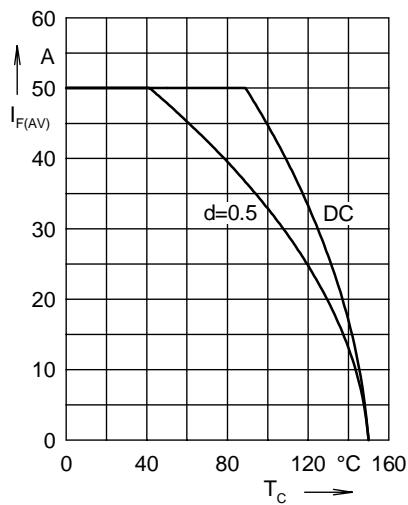


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

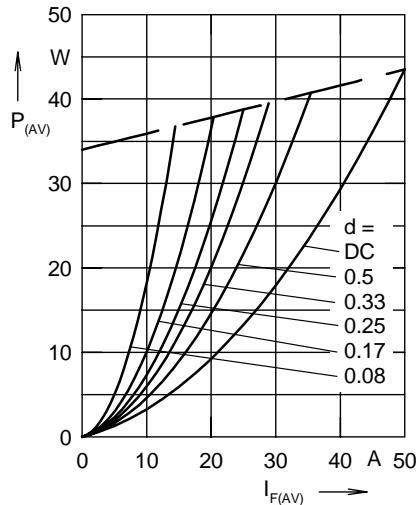


Fig. 5 Forward power loss characteristics

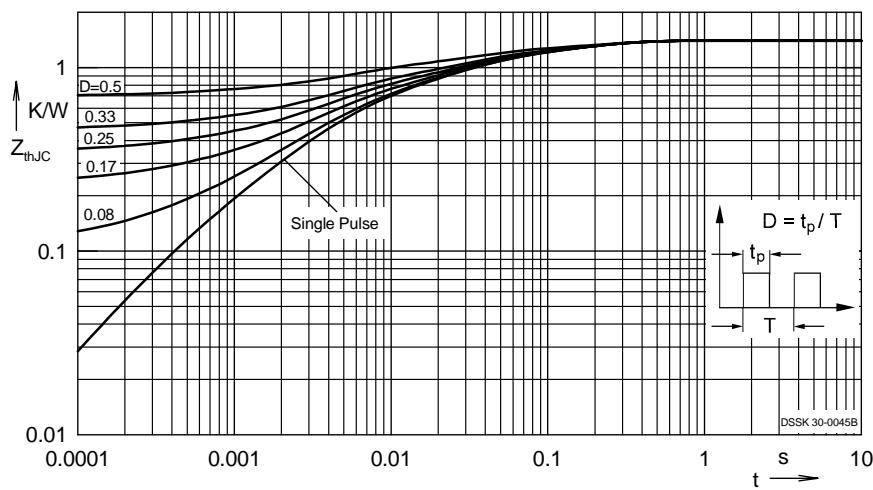


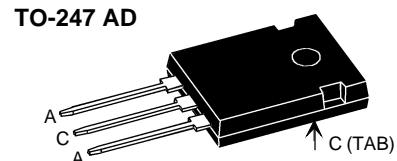
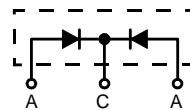
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x30 A
V_{RRM} = 45 V
V_F = 0.60 V

V _{RSM}	V _{RRM}	Type
V	V	
45	45	DSSK 60-0045A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5	30	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5; per device	60	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	550	A
E _{AS}	I _{AS} = 18 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	46	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.8	A
(dV/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	135	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	1	mA
		10	mA
V _F	I _F = 30 A; T _{VJ} = 125°C I _F = 30 A; T _{VJ} = 25°C I _F = 60 A; T _{VJ} = 125°C	0.60 0.69 0.74	V
R _{thJC}		1.1	K/W
R _{thCH}		0.25	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

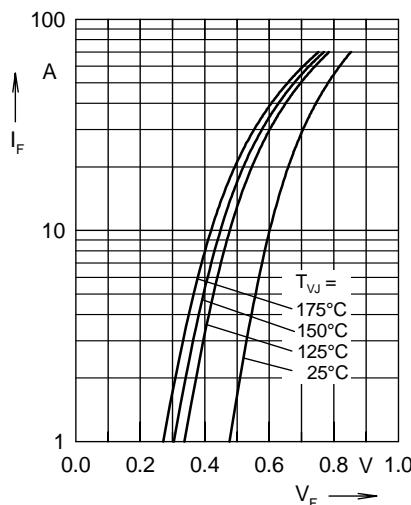


Fig. 1 Maximum forward voltage drop characteristics

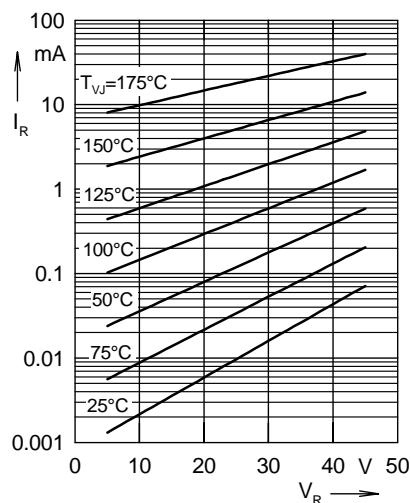


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

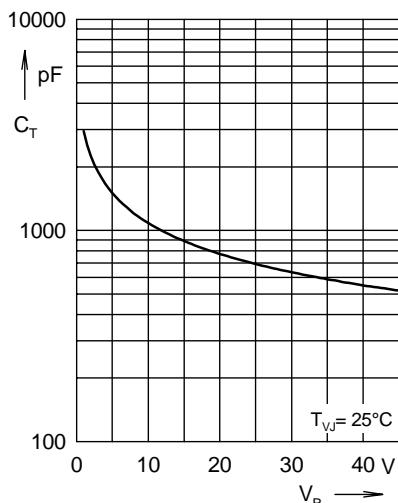


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

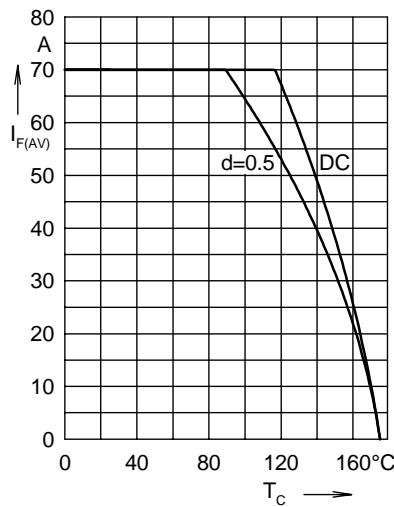


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

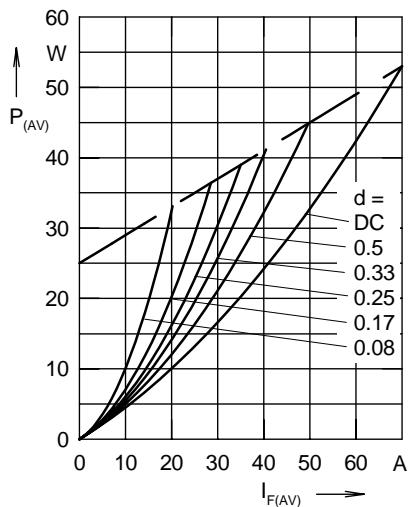


Fig. 5 Forward power loss characteristics

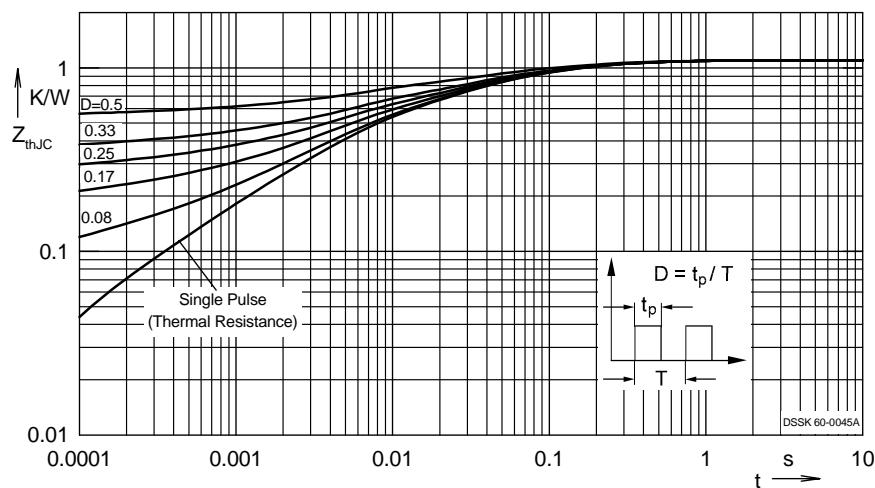


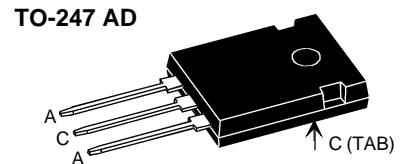
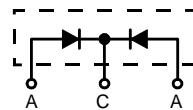
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x30 A
V_{RRM} = 45 V
V_F = 0.44 V

V _{RSM}	V _{RRM}	Type
V	V	
45	45	DSSK 60-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 120°C; rectangular, d = 0.5	30	A
I _{FAV}	T _C = 120°C; rectangular, d = 0.5; per device	60	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	640	A
E _{AS}	I _{AS} = 18 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	46	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.8	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	115	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	20	mA
		200	mA
V _F	I _F = 30 A; T _{VJ} = 125°C I _F = 30 A; T _{VJ} = 25°C I _F = 60 A; T _{VJ} = 125°C	0.44 0.50 0.68	V
R _{thJC}		1.1	K/W
R _{thCH}		0.25	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

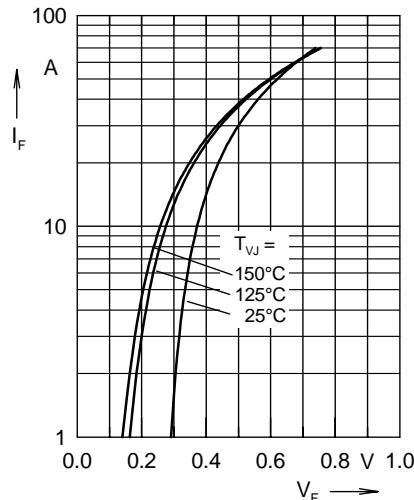


Fig. 1 Maximum forward voltage drop characteristics

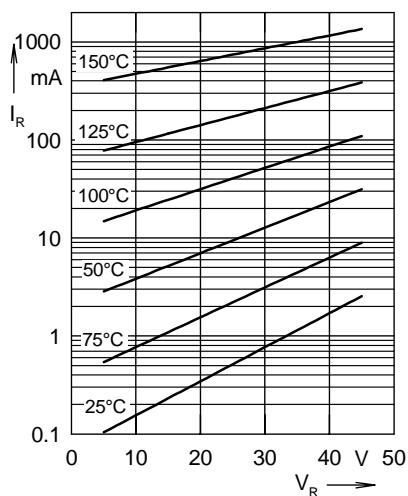


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

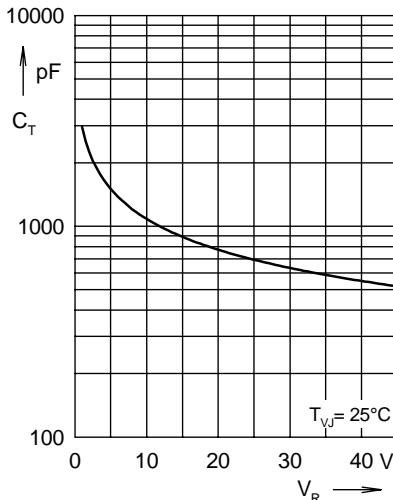


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

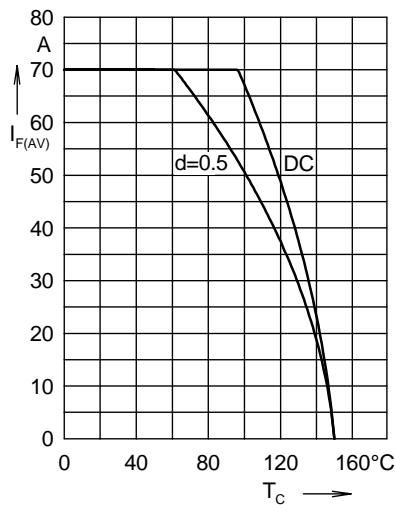


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

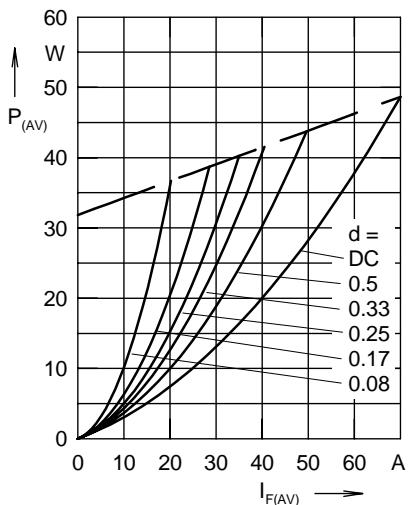


Fig. 5 Forward power loss characteristics

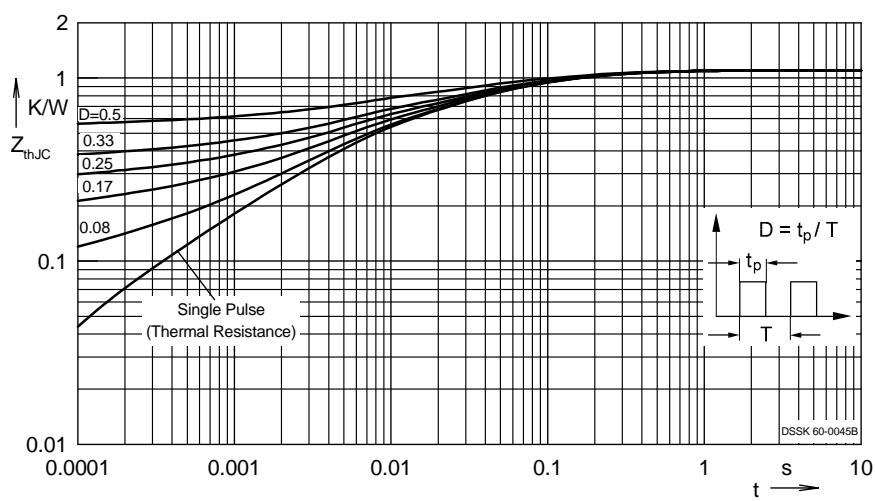


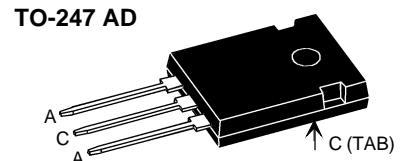
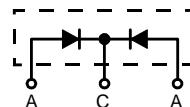
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x40 A
V_{RRM} = 45 V
V_F = 0.45 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSSK 80-0045B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 125°C; rectangular, d = 0.5	40	A
I _{FAV}	T _C = 125°C; rectangular, d = 0.5; per device	80	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	900	A
E _{AS}	I _{AS} = 20 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	57	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	2	A
(dV/dt) _{cr}		1000	V/µs
T _{VJ}		-55...+150	°C
T _{VJM}		150	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	155	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	10 250	mA mA
V _F	I _F = 40 A; T _{VJ} = 125°C I _F = 40 A; T _{VJ} = 25°C I _F = 80 A; T _{VJ} = 125°C	0.45 0.51 0.69	V V V
R _{thJC} R _{thCH}		0.25	0.8 K/W K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

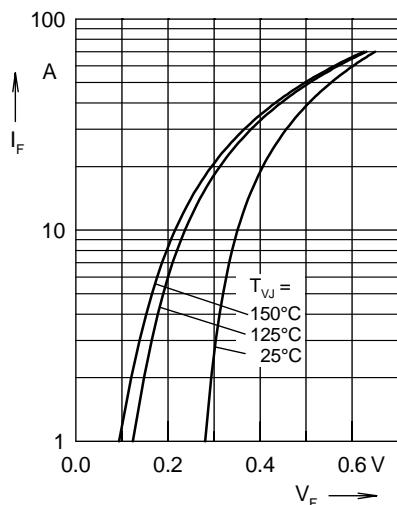


Fig. 1 Maximum forward voltage drop characteristics

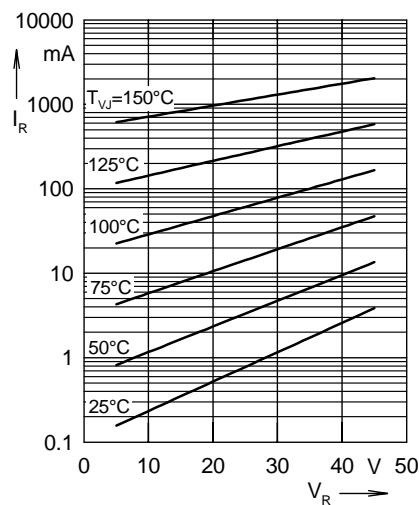


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

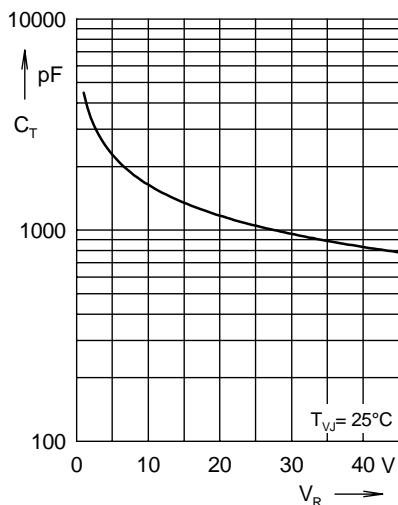


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

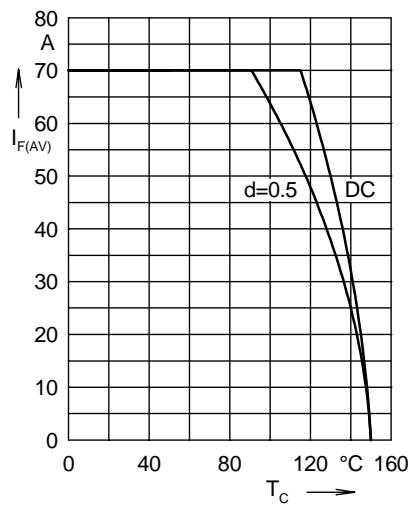


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

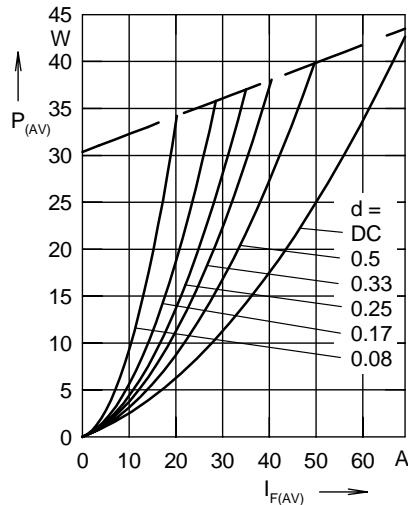


Fig. 5 Forward power loss characteristics

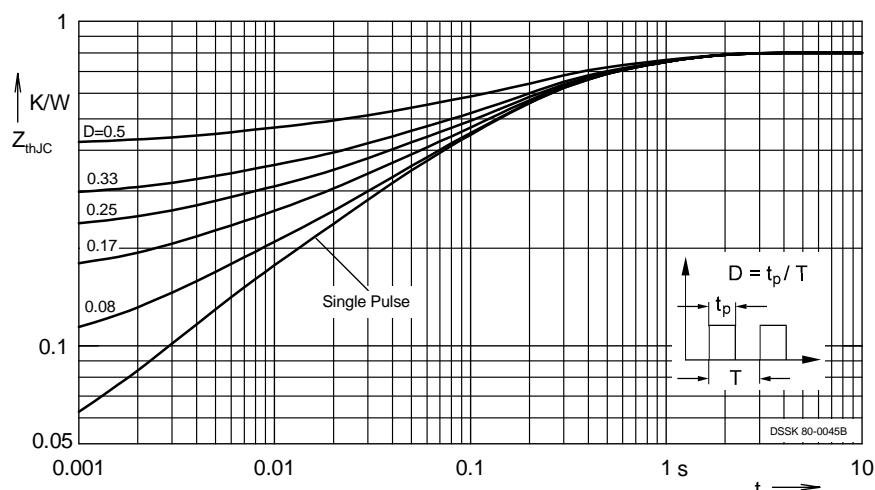


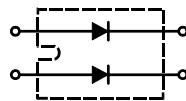
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

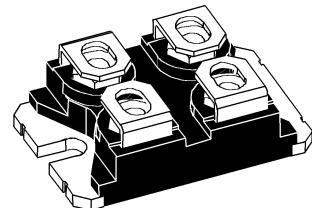
Power Schottky Rectifier

I_{FAV} = 2x60 A
V_{RRM} = 45 V
V_F = 0.66 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSS 2x61-0045A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		100	A
I _{FAVM}	T _C = 105°C; rectangular, d = 0.5	60	A
I _{FAVM}	T _C = 105°C; rectangular, d = 0.5; per device	120	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	800	A
E _{AS}	I _{AS} = 20 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	57	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	2	A
(dV/dt) _{cr}		1000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	150	W
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	2 20	mA mA
V _F	I _F = 60 A; T _{VJ} = 125°C I _F = 60 A; T _{VJ} = 25°C I _F = 120 A; T _{VJ} = 125°C	0.66 0.74 0.86	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

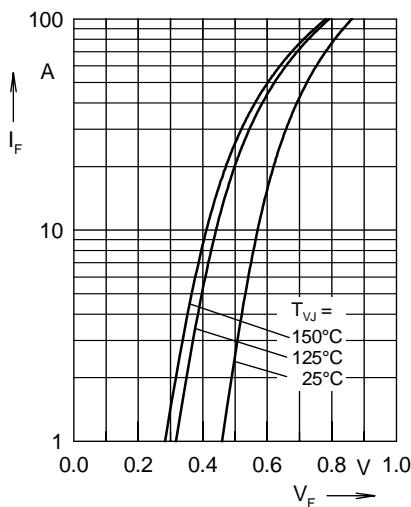


Fig. 1 Maximum forward voltage drop characteristics

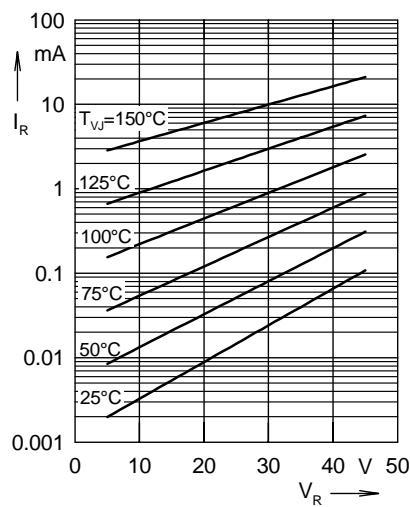


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

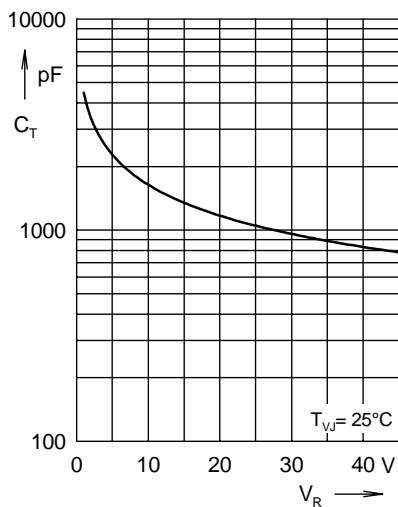


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

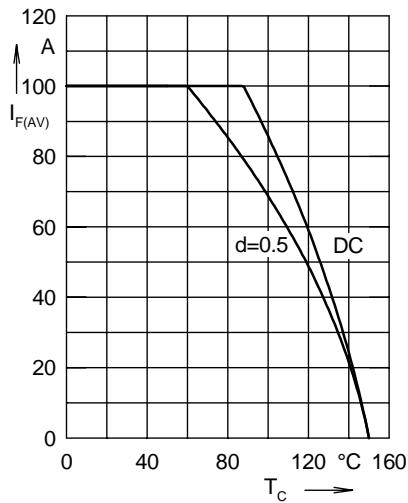


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

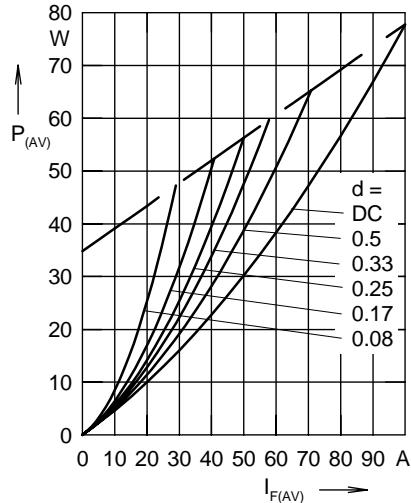


Fig. 5 Forward power loss characteristics

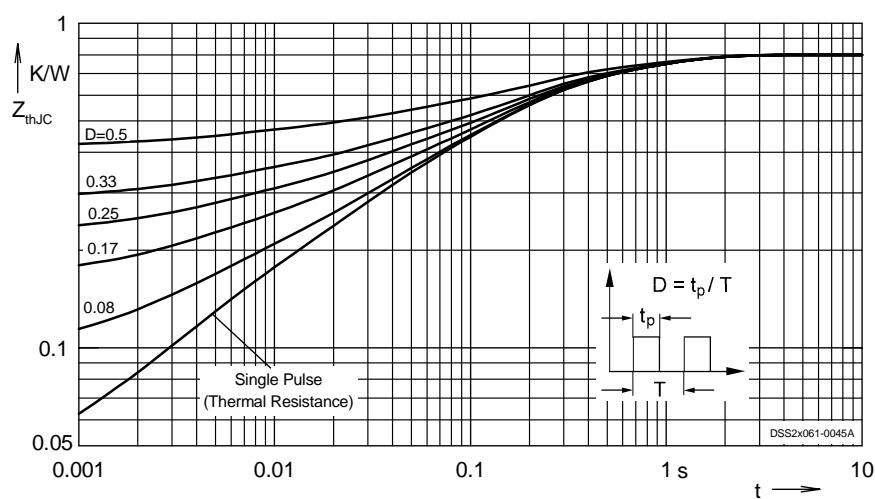


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

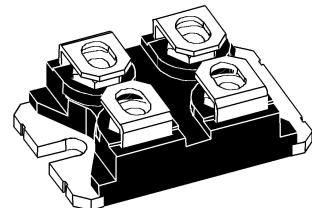
Power Schottky Rectifier

I_{FAV} = 2x80 A
V_{RRM} = 45 V
V_F = 0.64 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSS 2x81-0045B



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		100	A
I _{FAVM}	T _C = 75°C; rectangular, d = 0.5	80	A
I _{FAVM}	T _C = 75°C; rectangular, d = 0.5; per device	160	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	900	A
E _{AS}	I _{AS} = 20 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	57	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	2	A
(dV/dt) _{cr}		1000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	150	W
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	60 250	mA mA
V _F	I _F = 80 A; T _{VJ} = 125°C I _F = 80 A; T _{VJ} = 25°C I _F = 160 A; T _{VJ} = 125°C	0.64 0.66 1.07	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

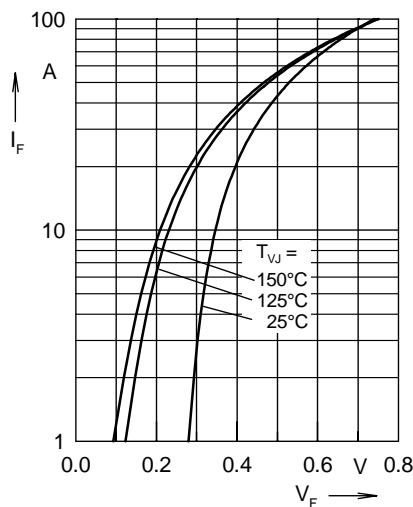


Fig. 1 Maximum forward voltage drop characteristics

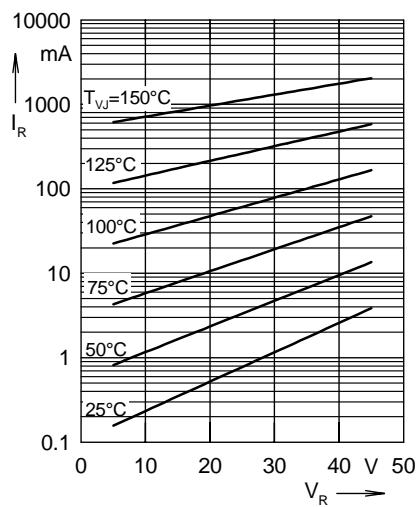


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

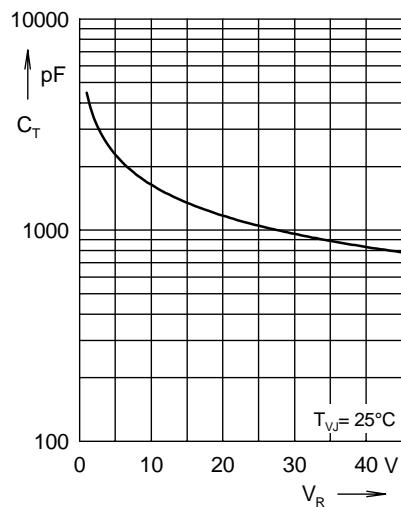


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

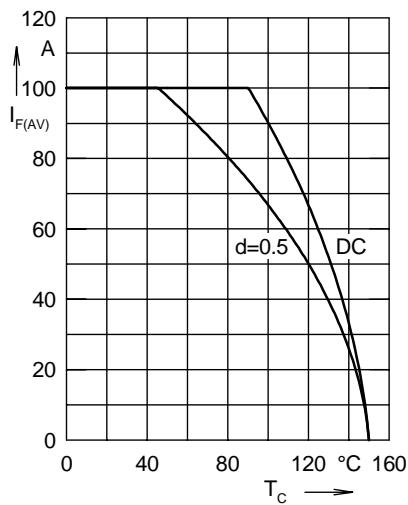


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

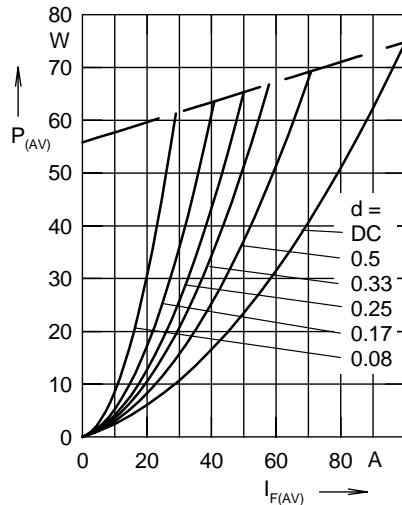


Fig. 5 Forward power loss characteristics

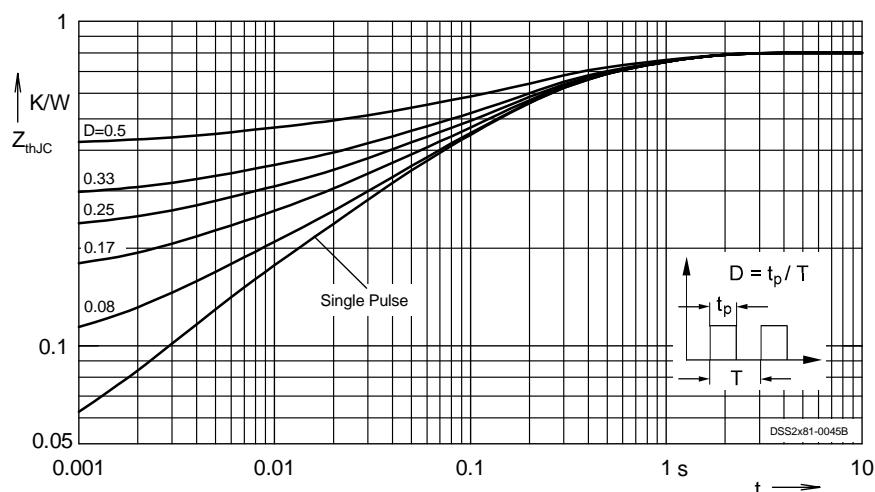


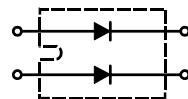
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

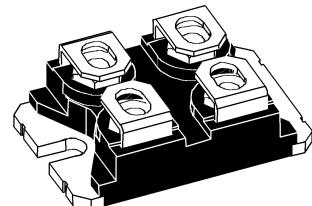
Power Schottky Rectifier

I_{FAV} = 2x120 A
V_{RRM} = 45 V
V_F = 0.59 V

V _{RSM} V	V _{RRM} V	Type
45	45	DSS 2x121-0045B



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings		
I _{FRMS}		150	A	
I _{FAVM}	T _C = 100°C; rectangular, d = 0.5	120	A	
I _{FAVM}	T _C = 100°C; rectangular, d = 0.5; per device	240	A	
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	1800	A	
E _{AS}	I _{AS} = 28 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	112	mJ	
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	2.8	A	
(dV/dt) _{cr}		1000	V/µs	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+150	°C	
P _{tot}	T _C = 25°C	310	W	
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~	
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.	
Weight	typical	30	g	

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	120 500	mA mA
V _F	I _F = 120 A; T _{VJ} = 125°C I _F = 120 A; T _{VJ} = 25°C I _F = 240 A; T _{VJ} = 125°C	0.59 0.62 0.97	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

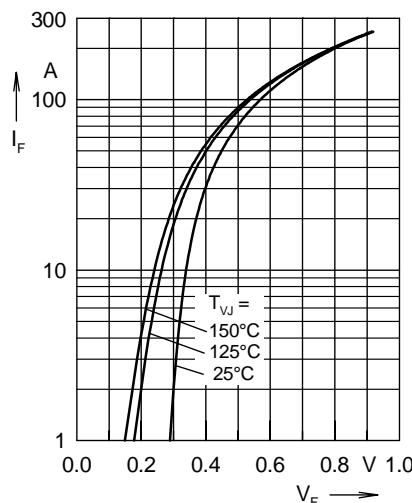


Fig. 1 Maximum forward voltage drop characteristics

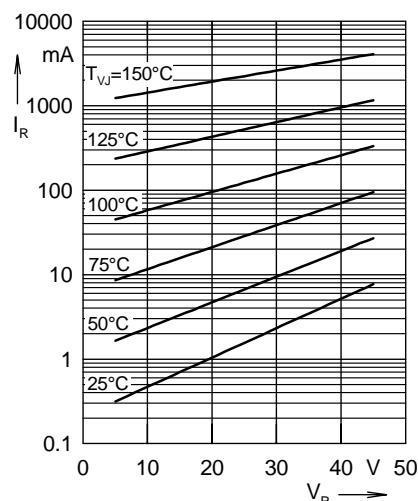


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

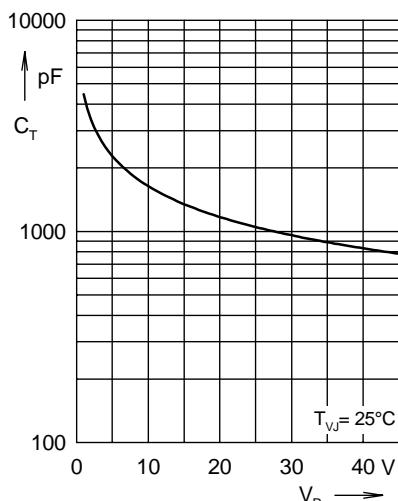


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

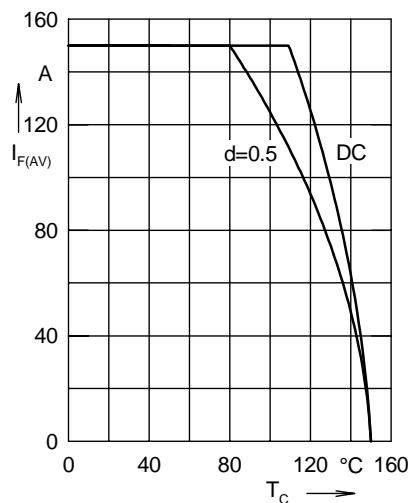


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

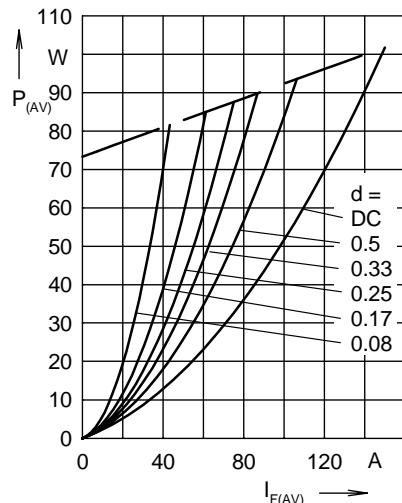


Fig. 5 Forward power loss characteristics

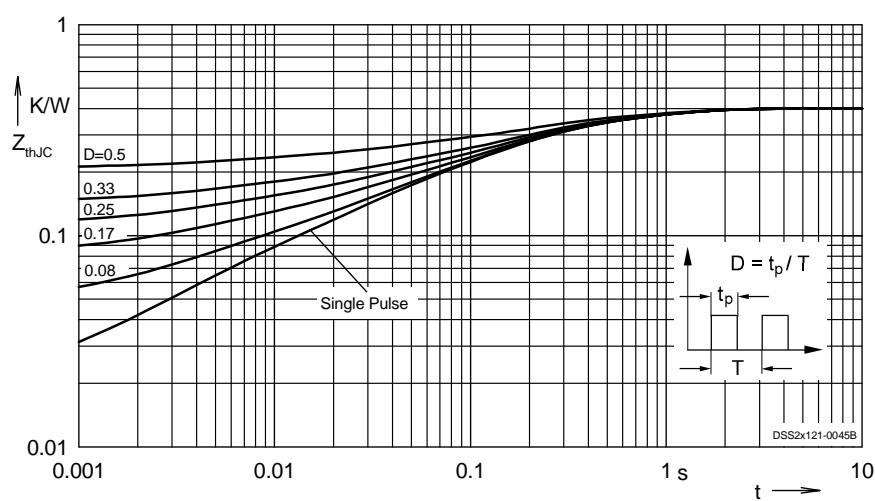


Fig. 6 Transient thermal impedance junction to case at various duty cycles

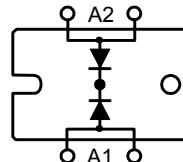
Note: All curves are per diode

Power Schottky Rectifier

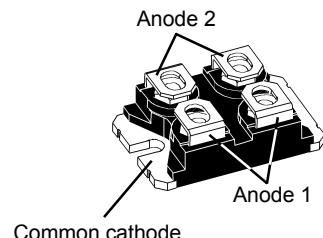
Non isolated

I_{FAVM} = 2x160 A
V_{RRM} = 45 V
V_F = 0.73 V

V _{RSM}	V _{RRM}	Type
V	V	
45	45	DSS 2x160-0045A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		200	A
I _{FAVM}	T _C = 100°C; rectangular, d = 0.5	160	A
I _{FAVM}	T _C = 100°C; rectangular, d = 0.5; per device	320	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	1600	A
E _{AS}	I _{AS} = 28 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	112	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	2.8	A
(dv/dt) _{cr}		1000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	410	W
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	4 40	mA mA
V _F	I _F = 160 A; T _{VJ} = 125°C T _{VJ} = 25°C I _F = 320 A; T _{VJ} = 125°C	0.73 0.80 0.99	V V V
R _{thJC} R _{thCH}		0.15	0.3 K/W K/W

Features

- International standard package miniBLOC
- Epoxy meets UL 94V-0
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

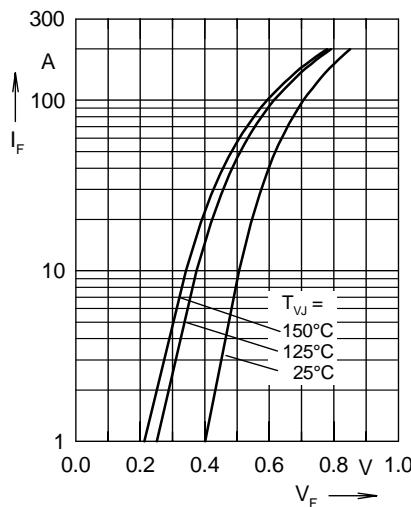


Fig. 1 Maximum forward voltage drop characteristics

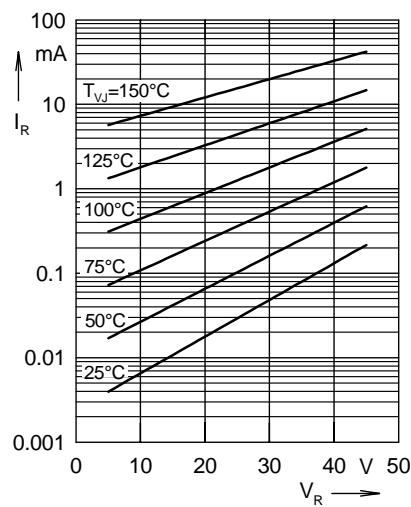


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

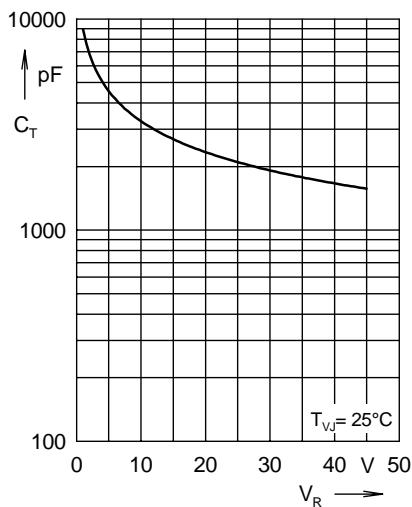


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

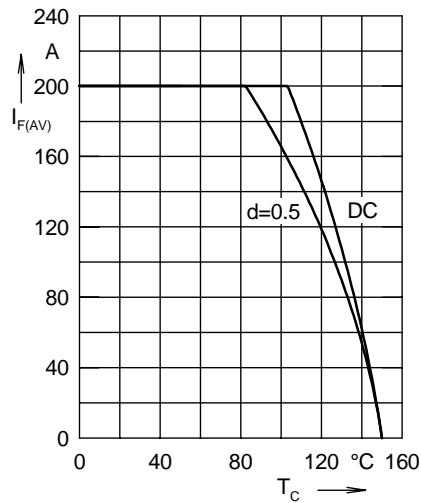


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

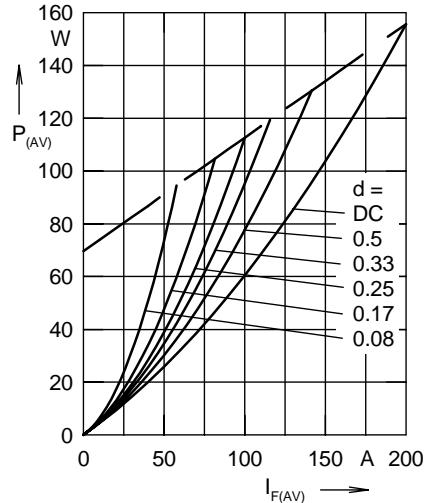


Fig. 5 Forward power loss characteristics

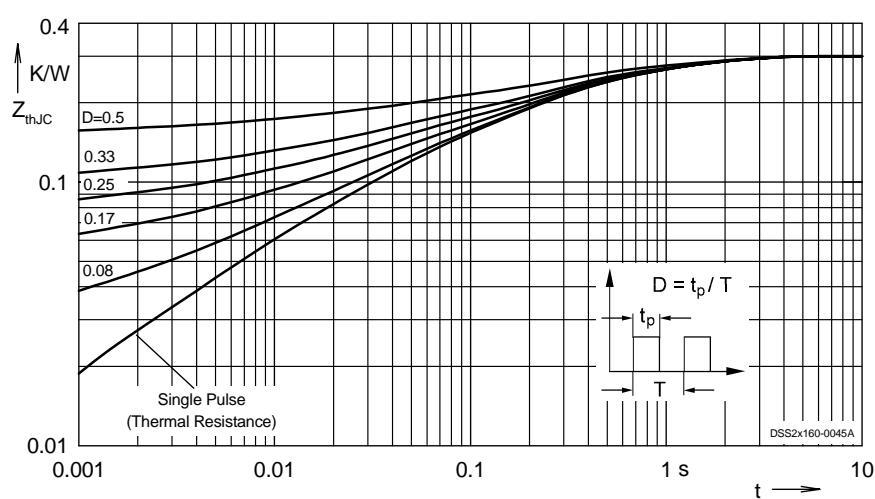


Fig. 6 Transient thermal impedance junction to case at various duty cycles

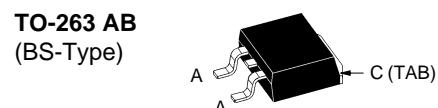
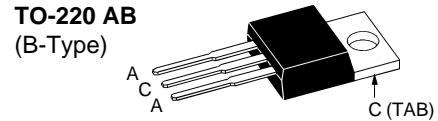
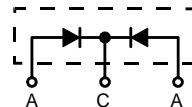
Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 15 \text{ A}$
 $V_{RRM} = 60 \text{ V}$
 $V_F = 0.52 \text{ V}$

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
60	60	DSSK 28-006B
60	60	DSSK 28-006BS



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$	15	A
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$; per device	30	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	320	A
E_{AS}	$I_{AS} = \text{tbd}$ A; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	V/ μ s
T_{VJ}		-55...+150	°C
T_{VJM}		150	°C
T_{stg}		-55...+150	°C
P_{tot}	$T_C = 25^\circ\text{C}$	115	W
M_d	mounting torque (Version B only)	0.4...0.6	Nm
Weight	typical	2	g

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$; $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$; $V_R = V_{RRM}$	20 50	mA mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.52 0.56 0.69	V V V
R_{thJC} R_{thCH}	(Version B only)	0.5	1.1 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%

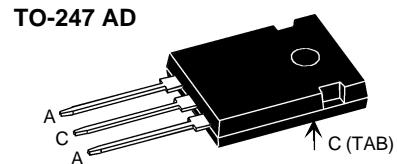
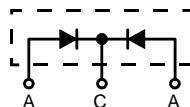
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 20 \text{ A}$
 $V_{RRM} = 60 \text{ V}$
 $V_F = 0.50 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
60	60	DSSK 40-006B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$	20	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$; per device	40	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	350	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	150	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	20 175	mA mA
V_F	$I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 40 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.50 0.53 0.60	V V V
R_{thJC} R_{thCH}		0.25	1.1 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

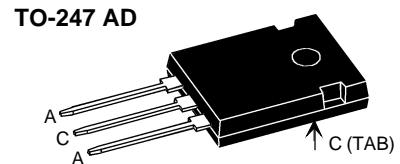
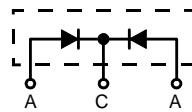
IXYS reserves the right to change limits, Conditions and dimensions.

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Power Schottky Rectifier with common cathode

I_{FAV} = 2x40 A
V_{RRM} = 60 V
V_F = 0.51 V

V _{RSM}	V _{RRM}	Type
V	V	
60	60	DSSK 80-006B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings		
I _{FRMS}		70		A
I _{FAV}	T _C = 120°C; rectangular, d = 0.5	40		A
I _{FAV}	T _C = 120°C; rectangular, d = 0.5; per device	80		A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	900		A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ	
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f = 10 kHz; repetitive	tbd		A
(dv/dt) _{cr}		tbd	V/µs	
T _{VJ}		-55...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-55...+150	°C	
P _{tot}	T _C = 25°C	155		W
M _d	mounting torque	0.8...1.2	Nm	
Weight	typical	6		g

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	40 200	mA mA
V _F	I _F = 40 A; T _{VJ} = 125°C I _F = 40 A; T _{VJ} = 25°C I _F = 80 A; T _{VJ} = 125°C	0.51 0.55 0.74	V V V
R _{thJC} R _{thCH}		0.25	0.8 K/W K/W

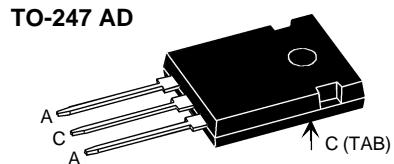
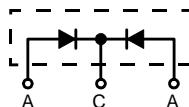
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 20 \text{ A}$
 $V_{RRM} = 80 \text{ V}$
 $V_F = 0.57 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
80	80	DSSK 40-008B



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$	20	A
I_{FAV}	$T_C = 130^\circ\text{C}$; rectangular, $d = 0.5$; per device	40	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	660	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		tbd	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	115	W
M_d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ\text{C}$ $V_R = V_{RRM}$	20 150	mA mA
V_F	$I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 40 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.57 0.62 0.67	V V V
R_{thJC}		1.1	K/W
R_{thCH}		0.25	K/W

Dimensions see pages D2 - 87-88

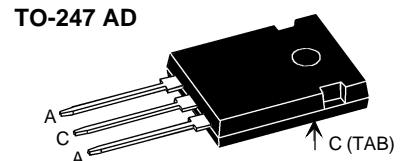
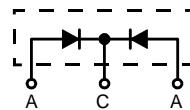
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier with common cathode

I_{FAV} = 2x35 A
V_{RRM} = 80 V
V_F = 0.66 V

V _{RSM}	V _{RRM}	Type
V	V	
80	80	DSSK 70-008A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5	35	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5; per device	70	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	700	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dV/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	190	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	4	mA
		10	mA
V _F	I _F = 35 A; T _{VJ} = 125°C I _F = 35 A; T _{VJ} = 25°C I _F = 70 A; T _{VJ} = 125°C	0.66 0.77 0.79	V
R _{thJC}		0.8	K/W
R _{thCH}		0.25	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

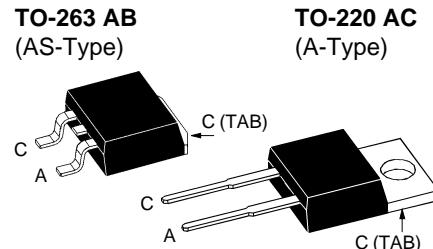
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier

$I_{FAV} = 10 \text{ A}$
 $V_{RRM} = 100 \text{ V}$
 $V_F = 0.65 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
100	100	DSS 10-01A DSS 10-01AS

TO-263 AB
(AS-Type)

A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$	10	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	120	A
E_{AS}	$I_{AS} = 8 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	7	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	0.8	A
$(dv/dt)_{cr}$		5000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	90	W
M_d	mounting torque (A-Type only)	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.3 2.5	mA mA
V_F	$I_F = 10 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 10 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.65 0.80 0.77	V V V
R_{thJC} R_{thCH}		1.7 0.5	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

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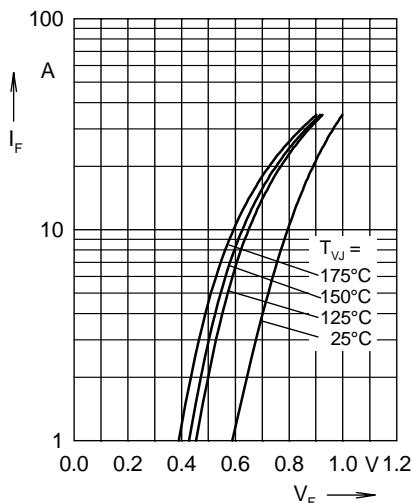


Fig. 1 Maximum forward voltage drop characteristics

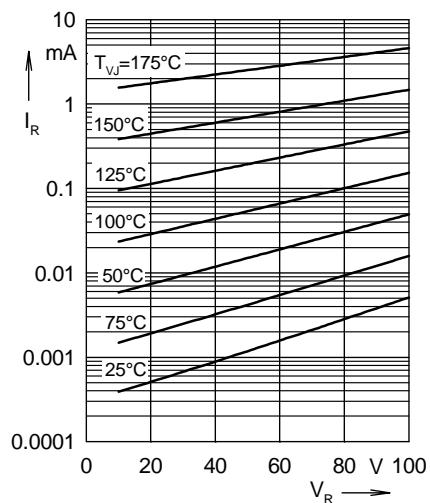


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

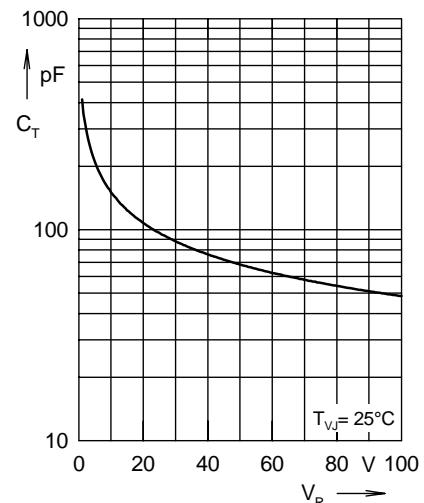


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

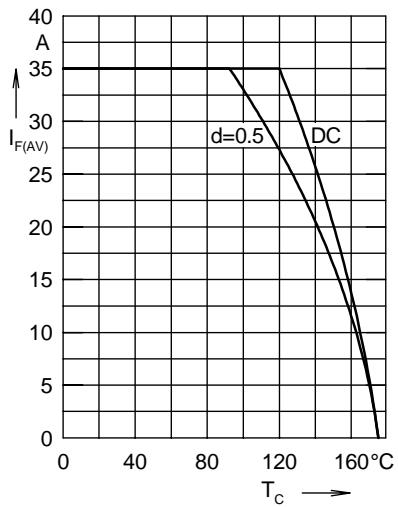


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

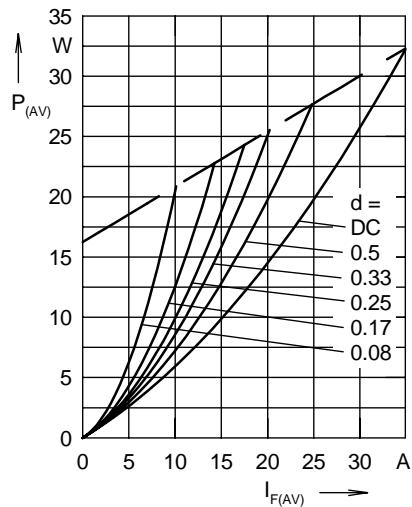


Fig. 5 Forward power loss characteristics

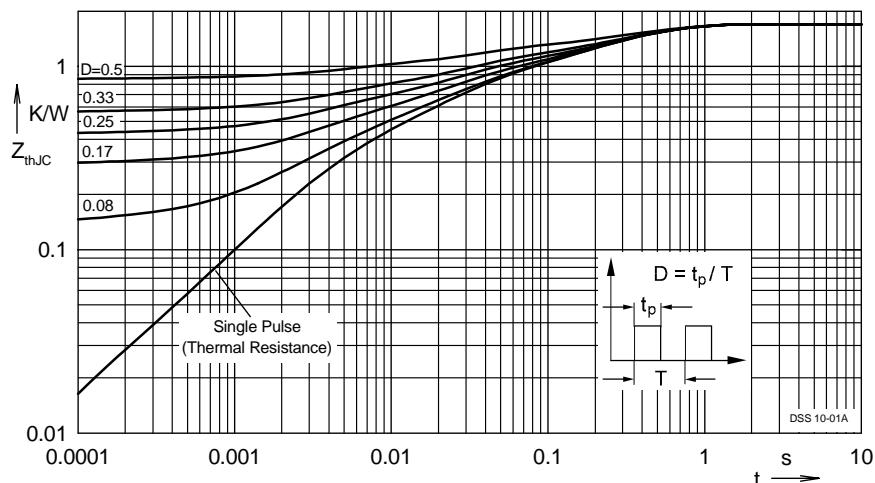


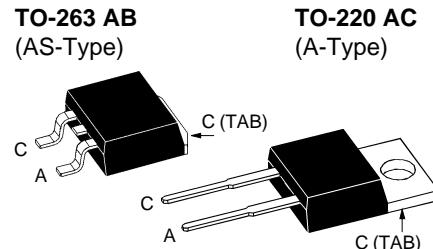
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier

$I_{FAV} = 16 \text{ A}$
 $V_{RRM} = 100 \text{ V}$
 $V_F = 0.64 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
100	100	DSS 16-01A
		DSS 16-01AS

TO-263 AB
(AS-Type)

A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 155^\circ\text{C}$; rectangular, $d = 0.5$	16	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sinev	230	A
E_{AS}	$I_{AS} = 9.5 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	10	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1	A
$(dv/dt)_{cr}$		5000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	105	W
M_d	mounting torque (A-Type only)	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5	mA mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.64 0.79 0.76	V V V
R_{thJC}		1.4	K/W
R_{thCH}		0.5	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

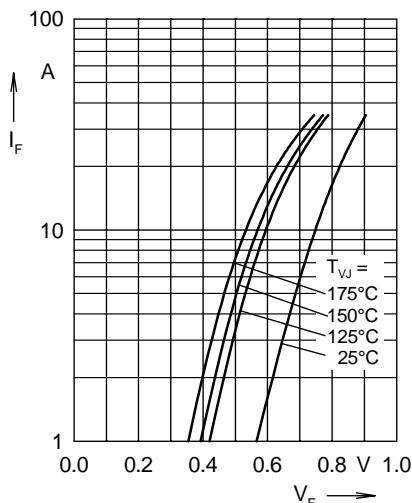


Fig. 1 Maximum forward voltage drop characteristics

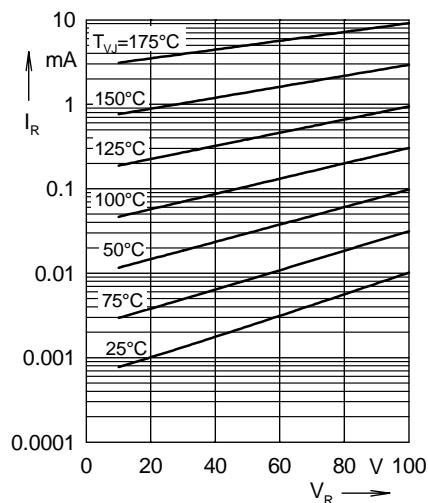


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

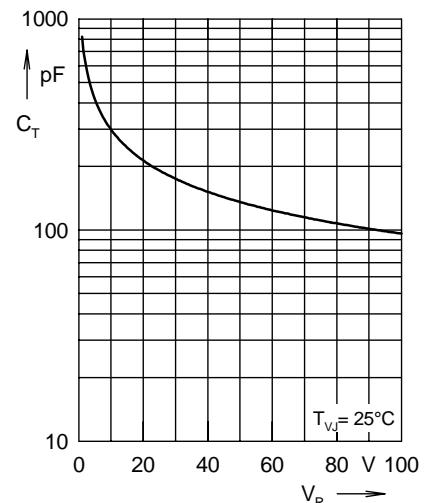


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

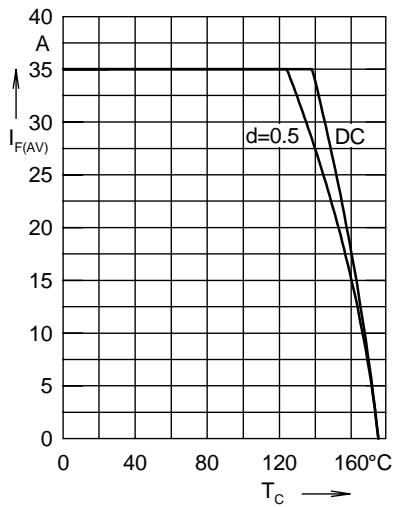


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

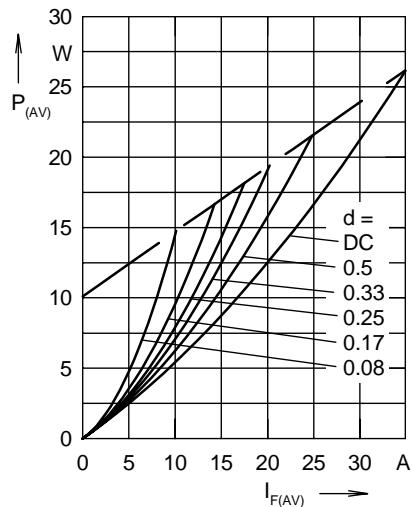


Fig. 5 Forward power loss characteristics

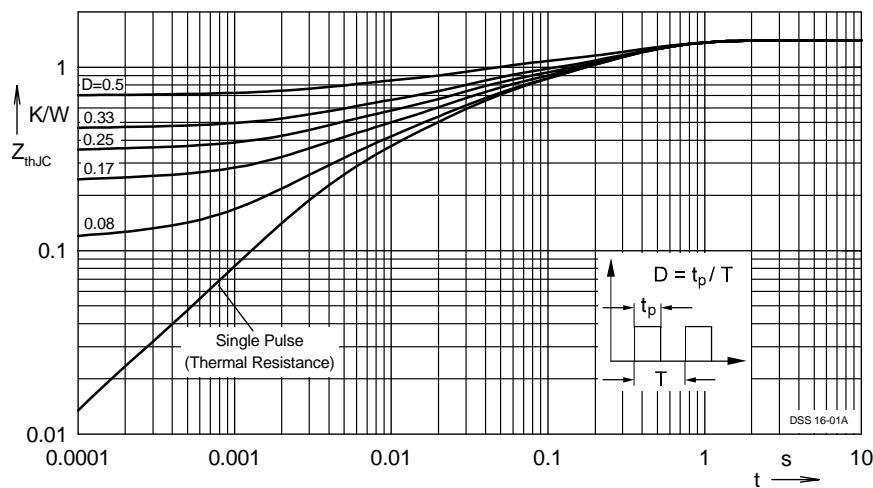


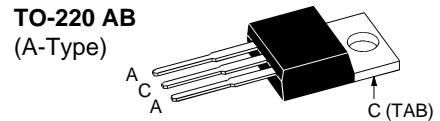
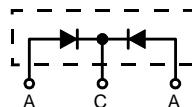
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

Preliminary Data

V_{RSM}	V_{RRM}	Type
V	V	
100	100	DSSK 16-01A
100	100	DSSK 16-01AS



A = Anode, C = Cathode , TAB = Cathode

Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_c = 165^\circ\text{C}$; rectangular, $d = 0.5$	8	A
I_{FAV}	$T_c = 165^\circ\text{C}$; rectangular, $d = 0.5$; per device	16	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	120	A
E_{AS}	$I_{AS} = 8 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	7	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	0.8	A
$(dv/dt)_{cr}$		5000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_c = 25^\circ\text{C}$	90	W
M_d	mounting torque (Version A only)	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.3 2.5	mA mA
V_F	$I_F = 10 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 10 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.65 0.80 0.77	V V V
R_{thJC} R_{thCH}	(Version A only)	0.5	1.7 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

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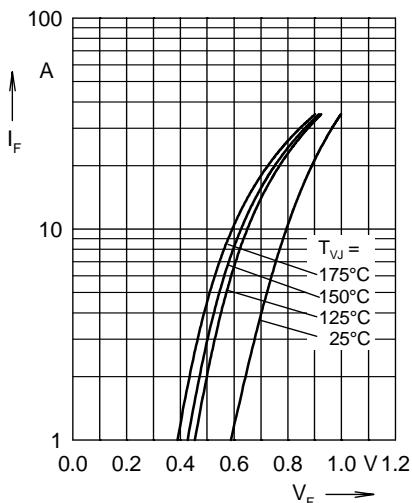


Fig. 1 Maximum forward voltage drop characteristics

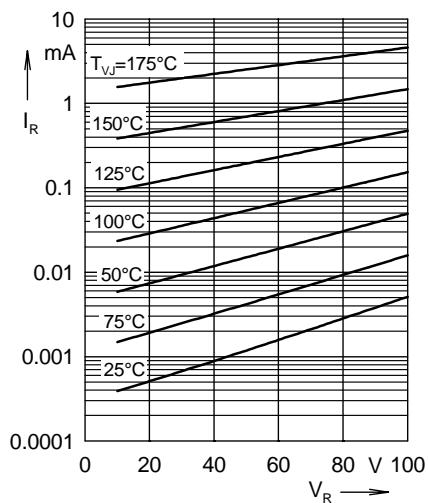


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

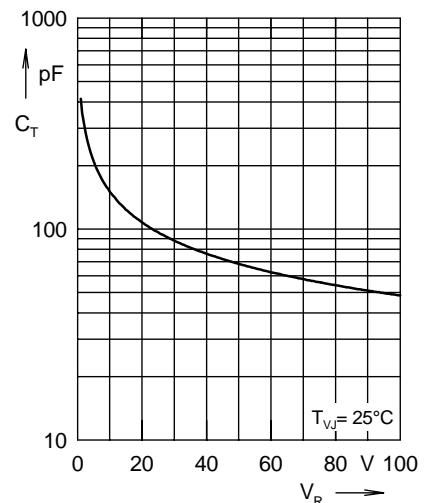


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

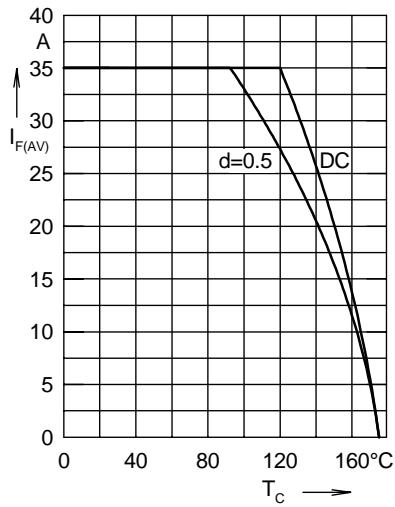


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

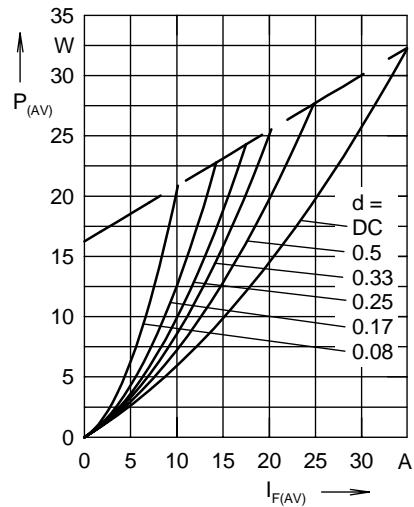


Fig. 5 Forward power loss characteristics

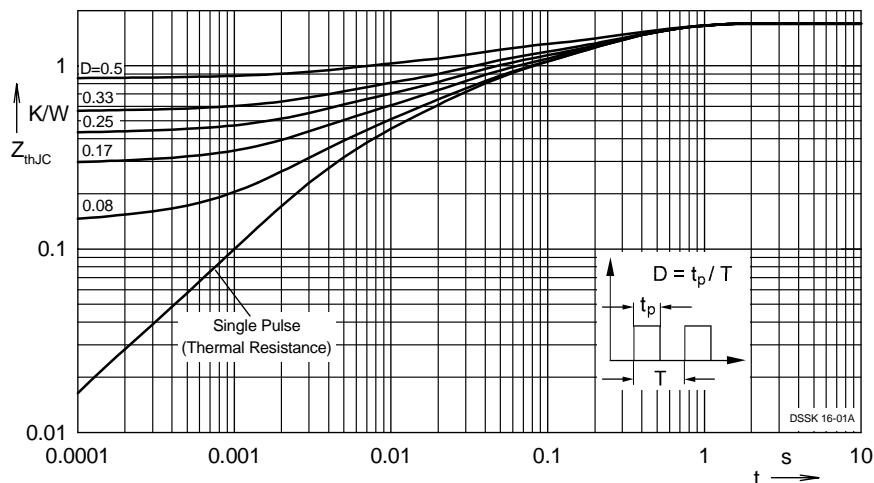


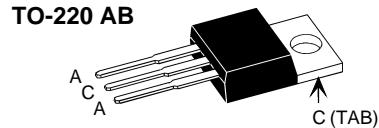
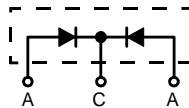
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per Diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 15 \text{ A}$
 $V_{RRM} = 100 \text{ V}$
 $V_F = 0.64 \text{ V}$

V_{RSM}	V_{RRM}	Type
V	V	
100	100	DSSK 28-01A DSSK 28-01AS



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_C = 155^\circ\text{C}$; rectangular, $d = 0.5$	2x15	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sinev	230	A
E_{AS}	$I_{AS} = 9.5 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	10	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	1	A
$(dv/dt)_{cr}$		5000	$\text{V}/\mu\text{s}$
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	105	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$\textcircled{1}$ $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5	mA mA
V_F	$I_F = 15 \text{ A}$; $I_F = 15 \text{ A}$; $I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.64 0.79 0.76	V V V
R_{thJC}		1.4	K/W
R_{thCH}		0.5	K/W

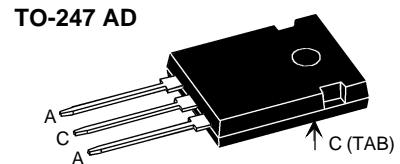
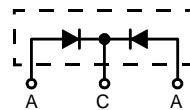
Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

Power Schottky Rectifier with common cathode

I_{FAV} = 2x15 A
V_{RRM} = 100 V
V_F = 0.64 V

V _{RSM} V	V _{RRM} V	Type
100	100	DSSK 30-01A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		50	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5	15	A
I _{FAV}	T _C = 160°C; rectangular, d = 0.5; per device	30	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	230	A
E _{AS}	I _{AS} = 9.5 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	10	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1	A
(dv/dt) _{cr}		5000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	105	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	0.5 5	mA mA
V _F	I _F = 15 A; T _{VJ} = 125°C I _F = 15 A; T _{VJ} = 25°C I _F = 30 A; T _{VJ} = 125°C	0.64 0.78 0.74	V V V
R _{thJC}		1.4	K/W
R _{thCH}		0.25	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

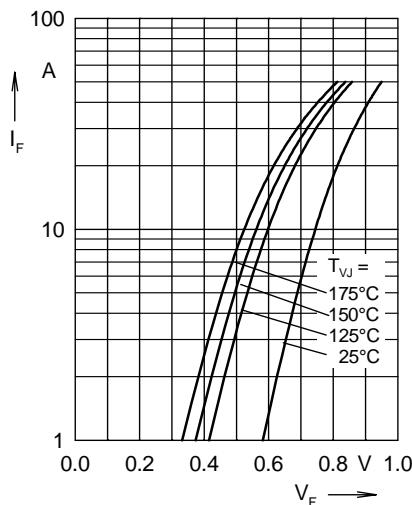


Fig. 1 Maximum forward voltage drop characteristics

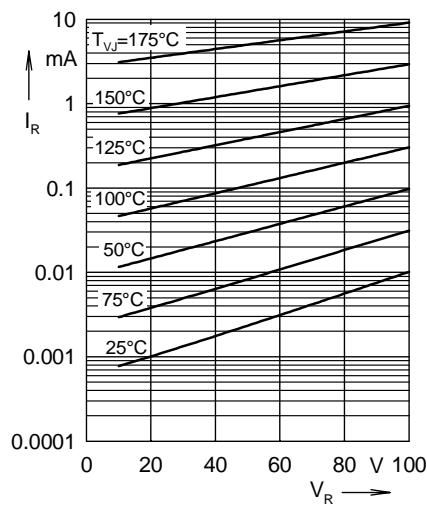


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

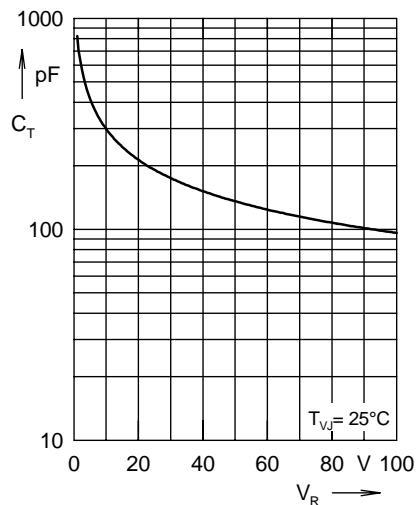


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

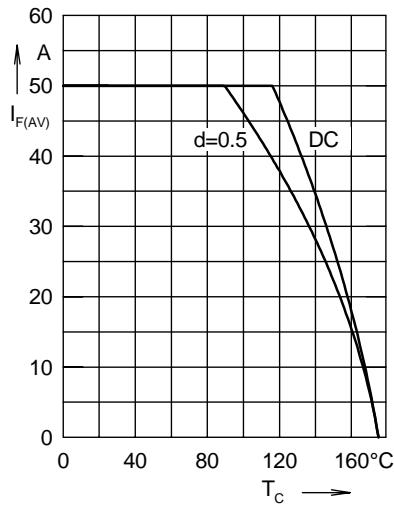


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

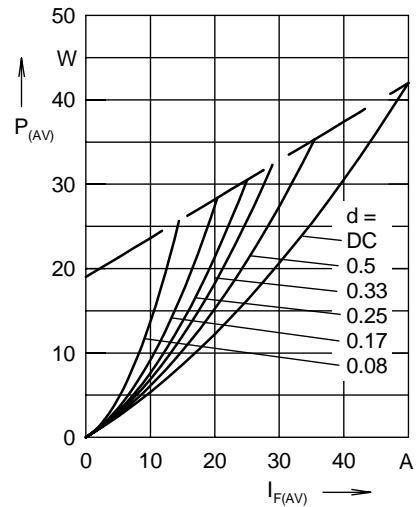


Fig. 5 Forward power loss characteristics

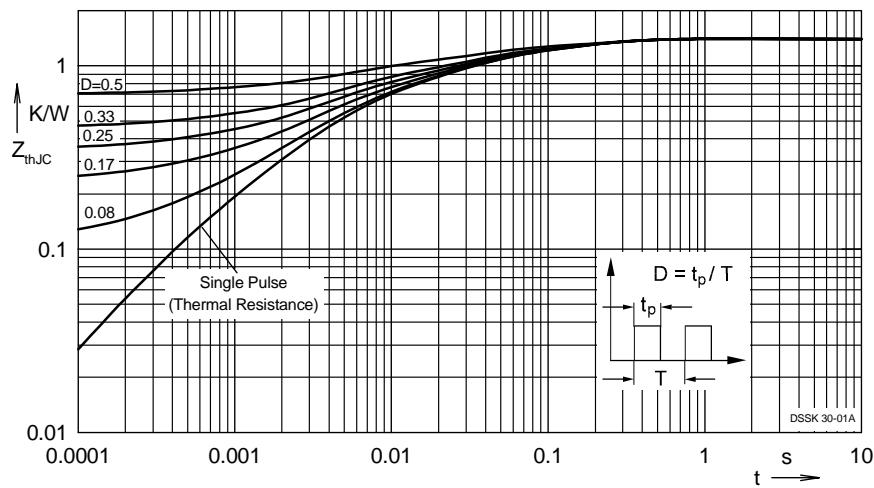


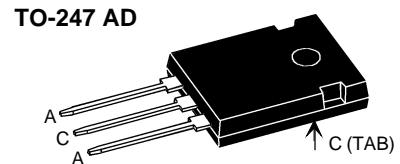
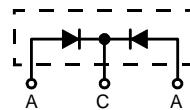
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x25 A
V_{RRM} = 100 V
V_F = 0.65 V

V _{RSM} V	V _{RRM} V	Type
100	100	DSSK 50-01A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5	25	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5; per device	50	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	450	A
E _{AS}	I _{AS} = 11 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	13	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.1	A
(dv/dt) _{cr}		5000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	135	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	1 10	mA mA
V _F	I _F = 25 A; T _{VJ} = 125°C I _F = 25 A; T _{VJ} = 25°C I _F = 50 A; T _{VJ} = 125°C	0.65 0.80 0.77	V V V
R _{thJC} R _{thCH}		0.25	1.1 K/W K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

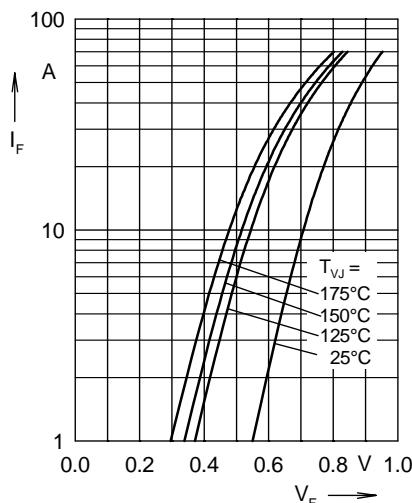


Fig. 1 Maximum forward voltage drop characteristics

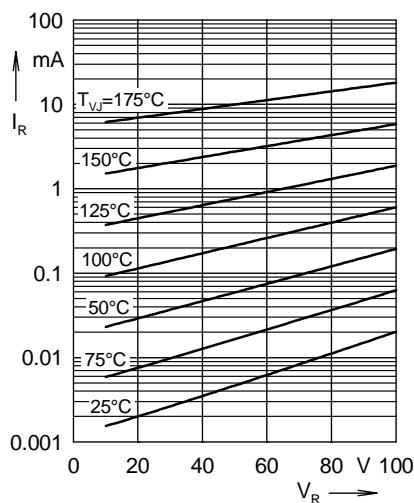


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

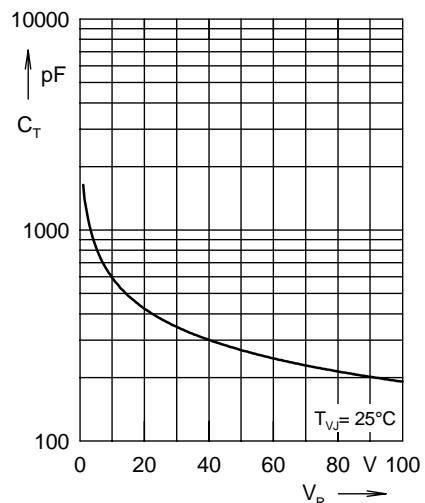


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

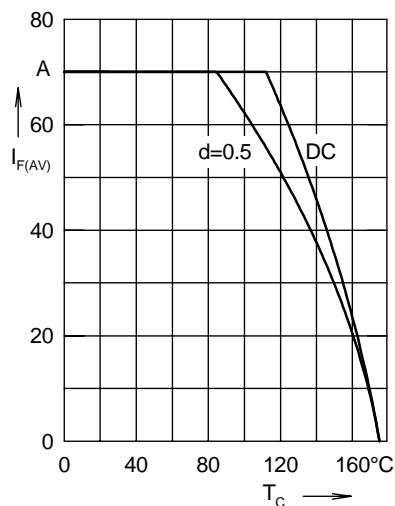


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

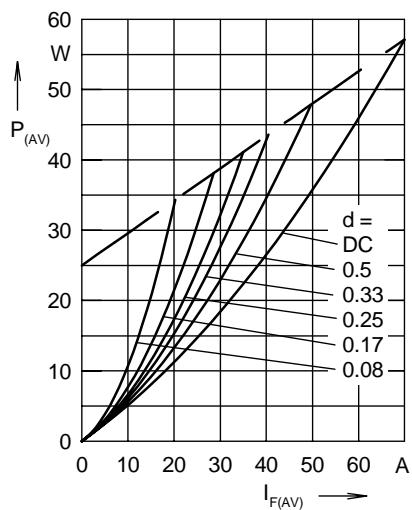


Fig. 5 Forward power loss characteristics

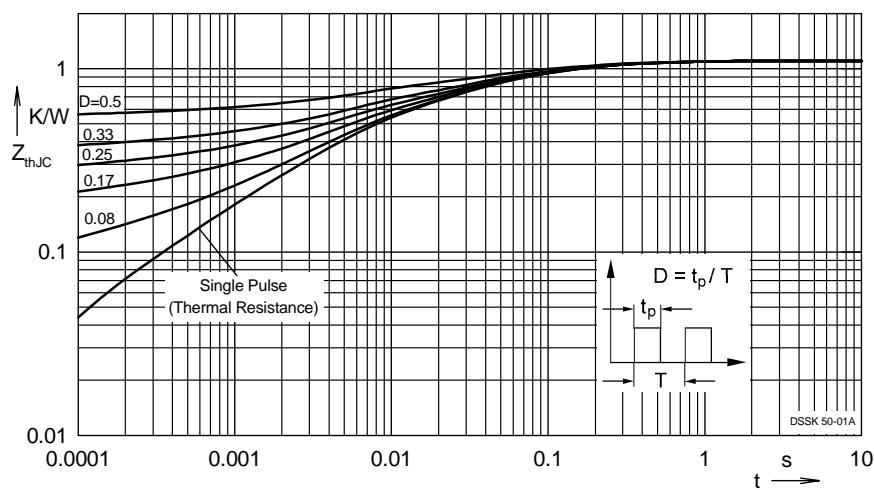


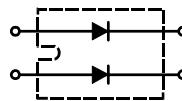
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

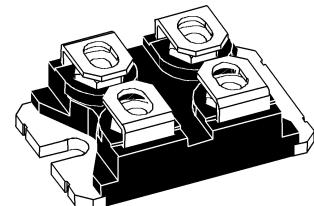
Power Schottky Rectifier

I_{FAV} = 2x40 A
V_{RRM} = 100 V
V_F = 0.70 V

V _{RSM} V	V _{RRM} V	Type
100	100	DSS 2x41-01A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAVM}	T _C = 110°C; rectangular, d = 0.5	40	A
I _{FAVM}	T _C = 110°C; rectangular, d = 0.5; per device	80	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	450	A
E _{AS}	I _{AS} = 11 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	13	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.1	A
(dV/dt) _{cr}		5000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	115	W
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	1 10	mA mA
V _F	I _F = 40 A; T _{VJ} = 125°C I _F = 40 A; T _{VJ} = 25°C I _F = 80 A; T _{VJ} = 125°C	0.70 0.83 0.86	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

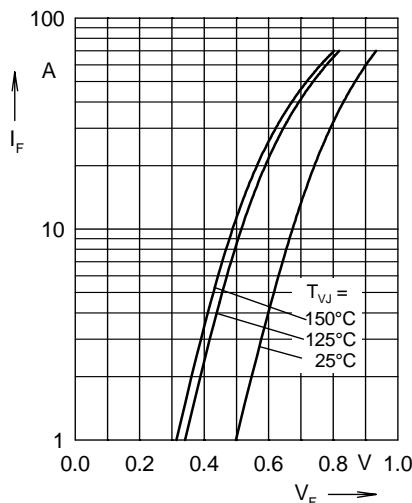


Fig. 1 Maximum forward voltage drop characteristics

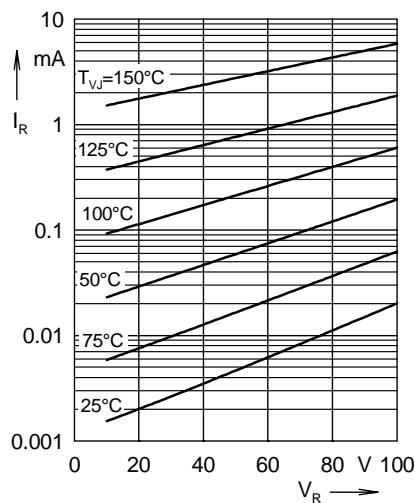


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

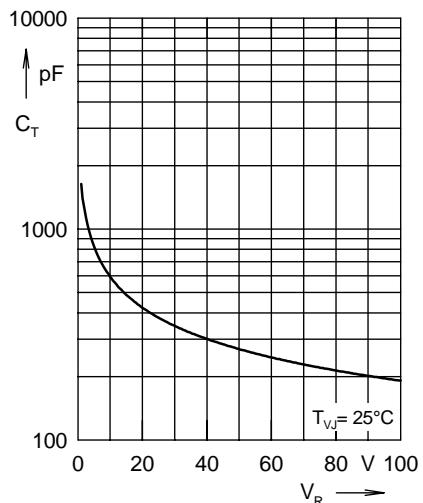


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

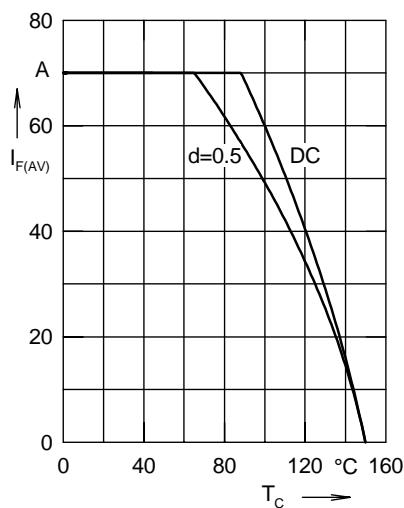


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

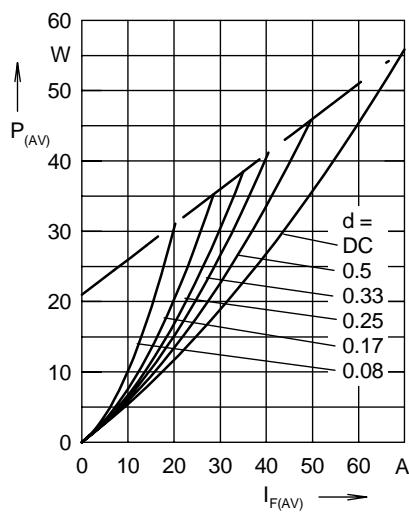


Fig. 5 Forward power loss characteristics

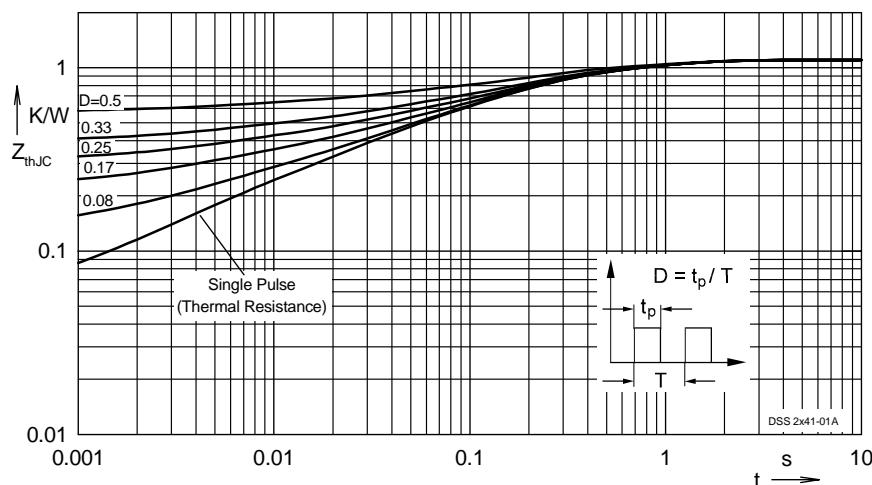


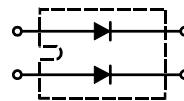
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

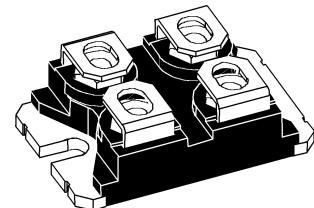
Power Schottky Rectifier

I_{FAV} = 2x60 A
V_{RRM} = 100 V
V_F = 0.73 V

V _{RSM} V	V _{RRM} V	Type
100	100	DSS 2x61-01A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings		
I _{FRMS}		100	A	
I _{FAVM}	T _C = 105°C; rectangular, d = 0.5	60	A	
I _{FAVM}	T _C = 105°C; rectangular, d = 0.5; per device	120	A	
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	700	A	
E _{AS}	I _{AS} = 12 A; L = 180 µH; TVJ = 25°C; non repetitive	16	mJ	
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.2	A	
(dV/dt) _{cr}		5000	V/µs	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+150	°C	
P _{tot}	T _C = 25°C	150	W	
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~	
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.	
Weight	typical	30	g	

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	2 20	mA mA
V _F	I _F = 60 A; T _{VJ} = 125°C I _F = 60 A; T _{VJ} = 25°C I _F = 120 A; T _{VJ} = 125°C	0.73 0.86 0.93	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

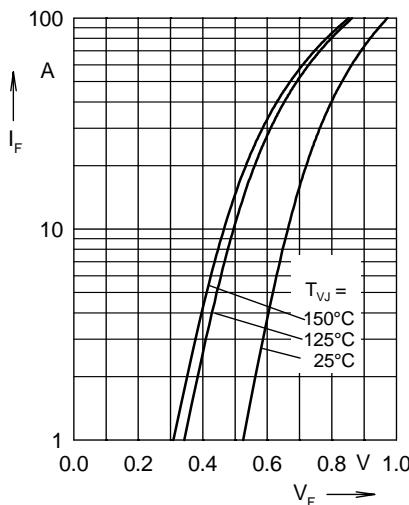


Fig. 1 Maximum forward voltage drop characteristics

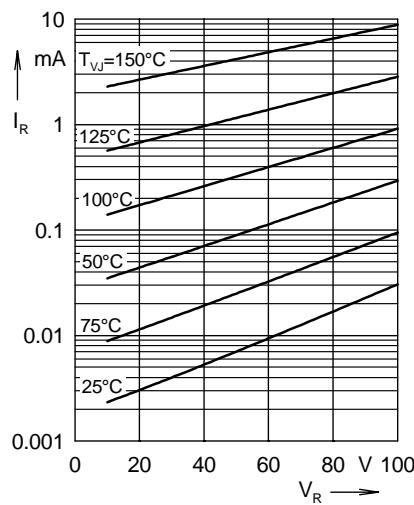


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

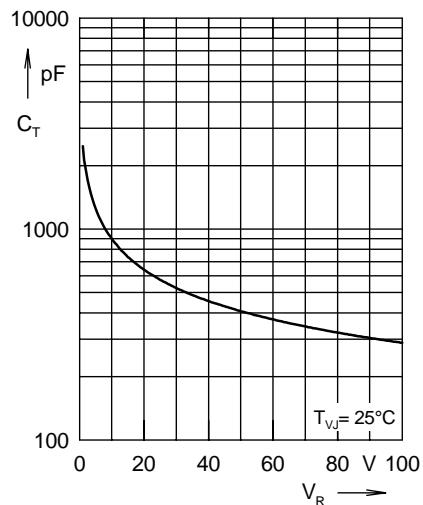


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

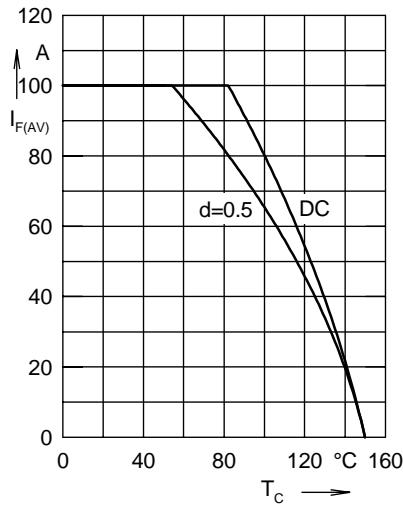


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

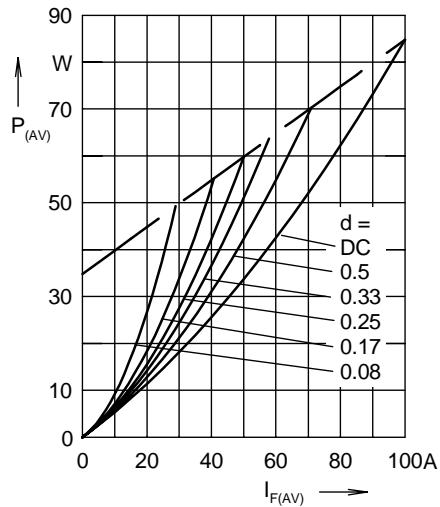


Fig. 5 Forward power loss characteristics

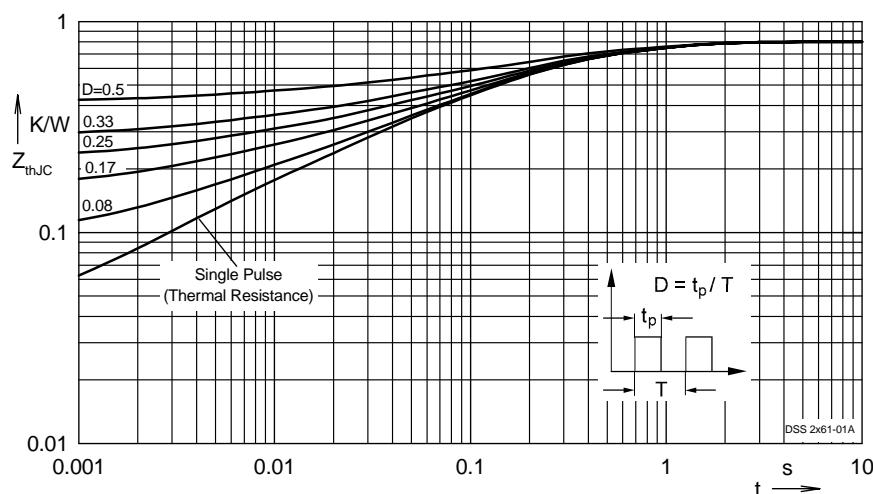


Fig. 6 Transient thermal impedance junction to case at various duty cycles

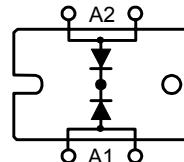
Note: All curves are per diode

Power Schottky Rectifier

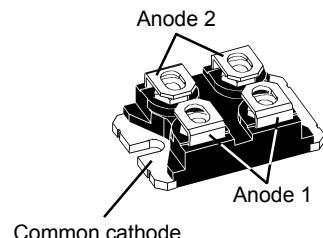
Non isolated

I_{FAVM} = 2x160 A
V_{RRM} = 100 V
V_F = 0.80 V

V _{RSM}	V _{RRM}	Type
V	V	
100	100	DSS 2x160-01A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		200	A
I _{FAVM}	T _C = 95°C; rectangular, d = 0.5	160	A
I _{FAVM}	T _C = 95°C; rectangular, d = 0.5; per device	320	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	1400	A
E _{AS}	I _{AS} = 17 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	31	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1.7	A
(dv/dt) _{cr}		5000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	410	W
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	4 40	mA mA
V _F	I _F = 160 A; T _{VJ} = 125°C T _{VJ} = 25°C I _F = 320 A; T _{VJ} = 125°C	0.80 0.92 1.06	V V V
R _{thJC}		0.30	K/W
R _{thCH}		0.15	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

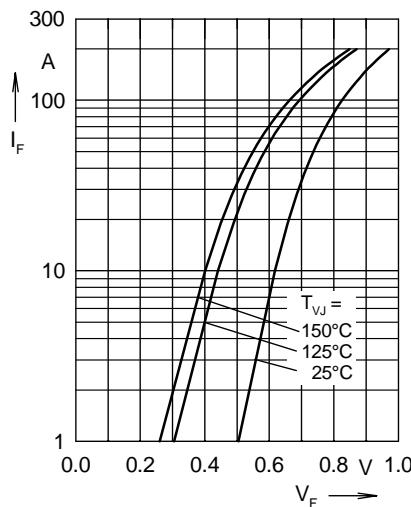


Fig. 1 Maximum forward voltage drop characteristics

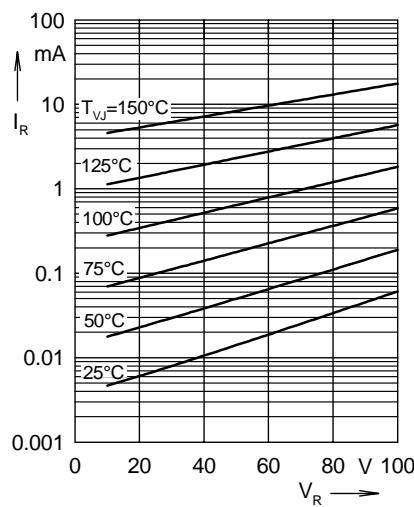


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

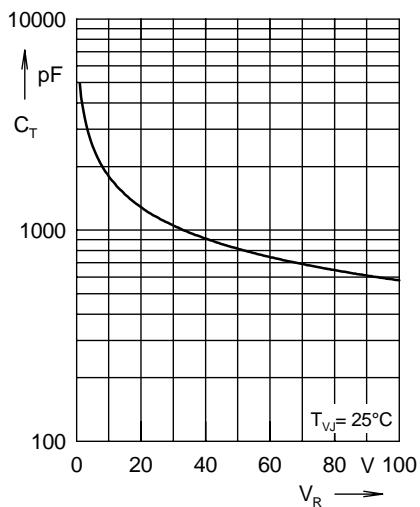


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

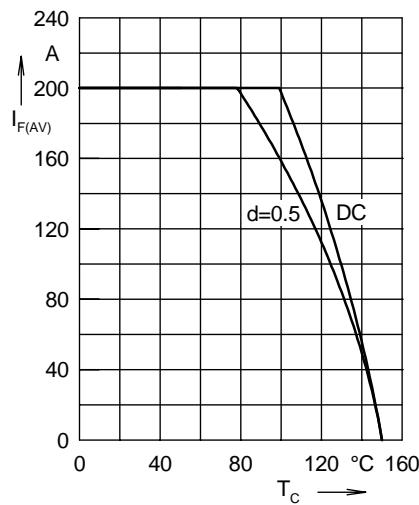


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

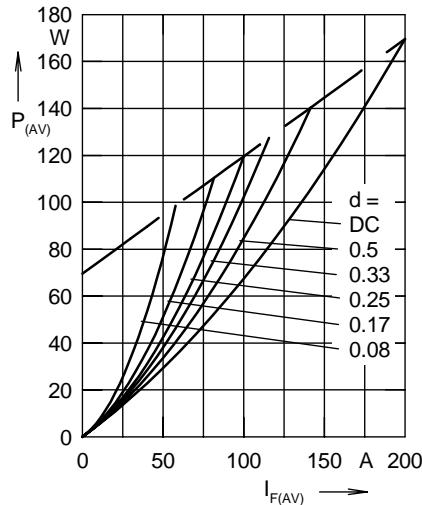


Fig. 5 Forward power loss characteristics

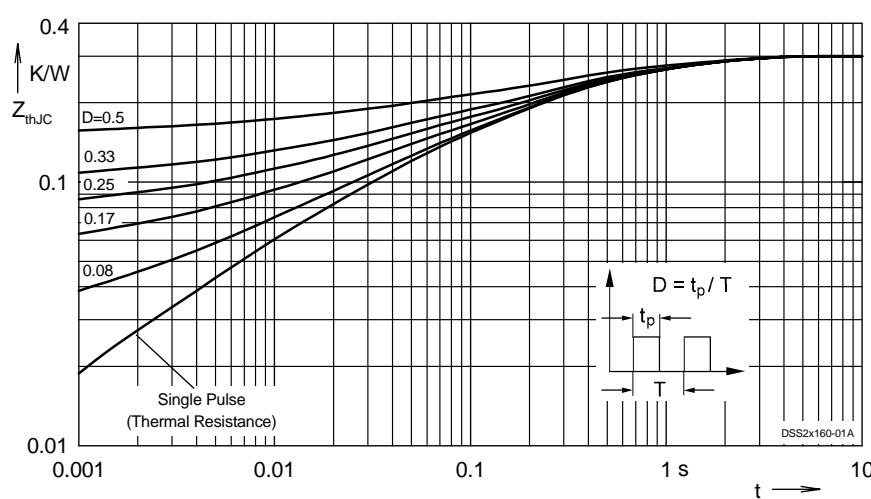


Fig. 6 Transient thermal impedance junction to case at various duty cycles

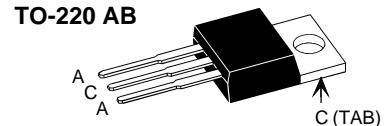
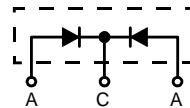
Note: All curves are per diode

Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 10 \text{ A}$
 $V_{RRM} = 130 \text{ V}$
 $V_F = 0.65 \text{ V}$

Preliminary Data

V_{RSM} V	V_{RRM} V	Type
130	130	DSSK 20-013A
150	150	DSSK 20-015A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAV}	$T_c = 165^\circ\text{C}$; rectangular, $d = 0.5$	10	A
I_{FAV}	$T_c = 165^\circ\text{C}$; rectangular, $d = 0.5$; per device	20	A
I_{FSM}	$T_{vj} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	200	A
E_{AS}	$I_{AS} = \text{tbd A}$; $L = 180 \mu\text{H}$; $T_{vj} = 25^\circ\text{C}$; non repetitive	tbd	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$; repetitive	tbd	A
$(dv/dt)_{cr}$		18000	$\text{V}/\mu\text{s}$
T_{vj}		-55...+175	$^\circ\text{C}$
T_{vjm}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_c = 25^\circ\text{C}$	105	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{vj} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{vj} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5.0	mA
V_F	$I_F = 10 \text{ A}$; $T_{vj} = 125^\circ\text{C}$ $I_F = 10 \text{ A}$; $T_{vj} = 25^\circ\text{C}$ $I_F = 20 \text{ A}$; $T_{vj} = 125^\circ\text{C}$	0.65 0.79 0.72	V
R_{thJC} R_{thCH}		0.5	1.4 K/W K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

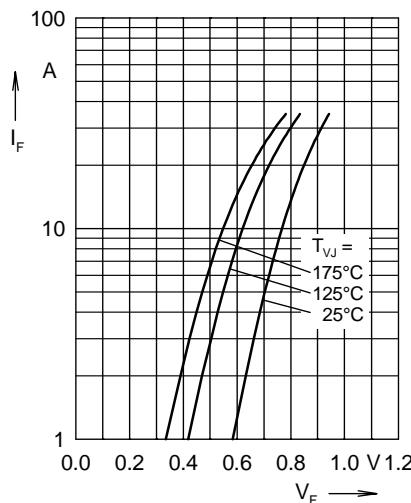


Fig. 1 Maximum forward voltage drop characteristics

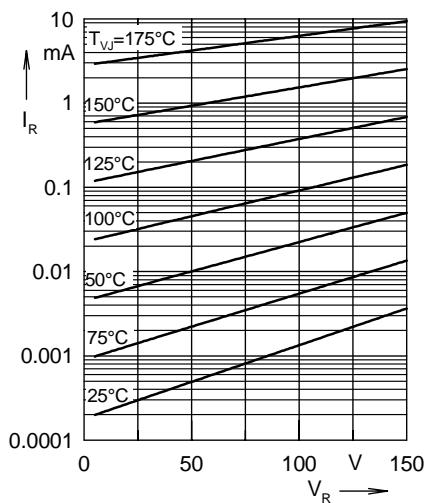


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

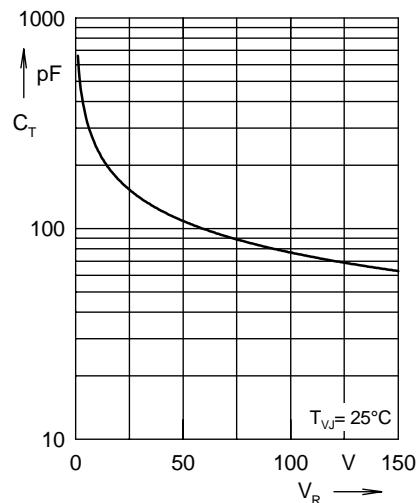


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

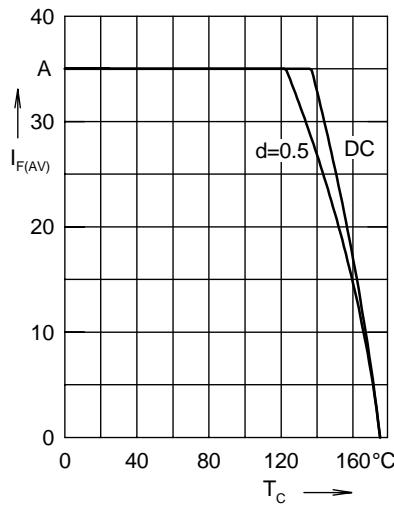


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

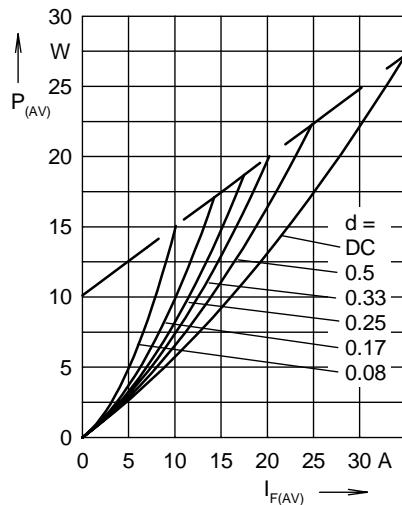


Fig. 5 Forward power loss characteristics

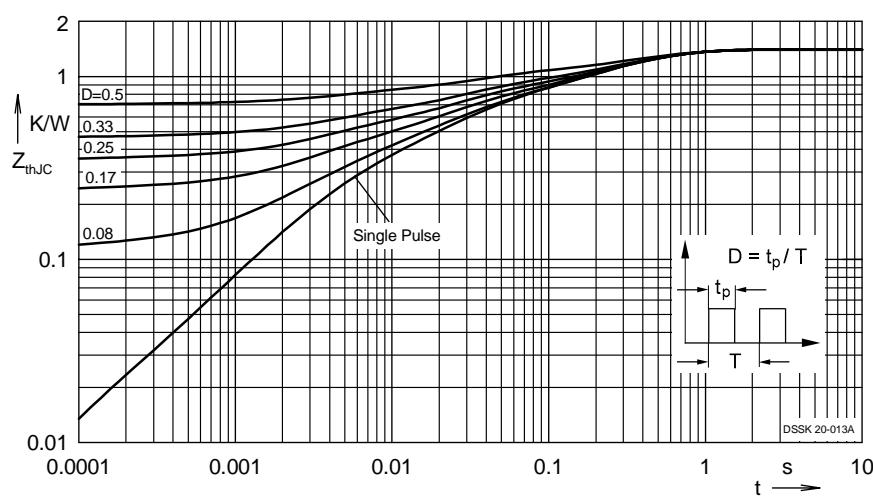


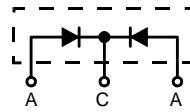
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Power Schottky Rectifier with common cathode

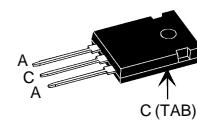
I_{FAV} = 2x30 A
V_{RRM} = 130 / 150 V
V_F = 0.69 V

Preliminary Data

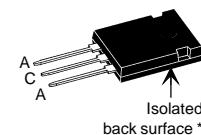
V _{RSM} V	V _{RRM} V	Type
130	130	DSSK 60-013A
150	150	DSSK 60-015A
150	150	DSSK 60-015AR



TO-247 AD
Version A



ISOPLUS 247™
Version AR



* Patent pending

C = Cathode, A = Anode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5	30	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5; per device	60	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	600	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dv/dt) _{cr}		18000	V/ms
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	190	W
M _d	Version A: mounting torque M3	0.8...1.2	Nm
F _c	Version AR: mounting force with clip	20...120	N
V _{ISOL} *	50/60 Hz, RMS, t = 1 minute, leads-to-tab	2500	V~
Weight	typical	6	g

* Version AR only

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	2	mA
		20	mA
V _F	I _F = 30 A; T _{VJ} = 125°C I _F = 30 A; T _{VJ} = 25°C I _F = 60 A; T _{VJ} = 125°C	0.69 0.83 0.80	V
R _{thJC}		0.25	K/W
R _{thCH}			K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

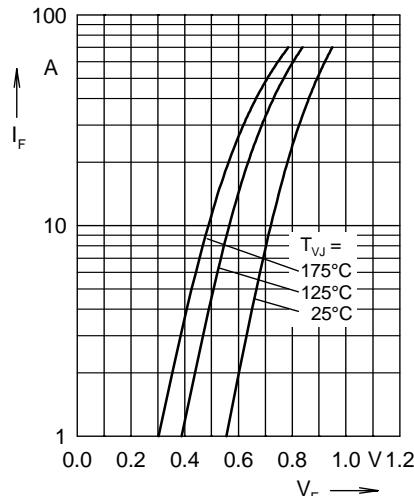


Fig. 1 Maximum forward voltage drop characteristics

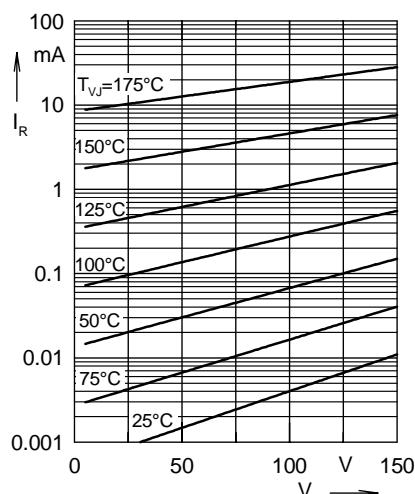


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

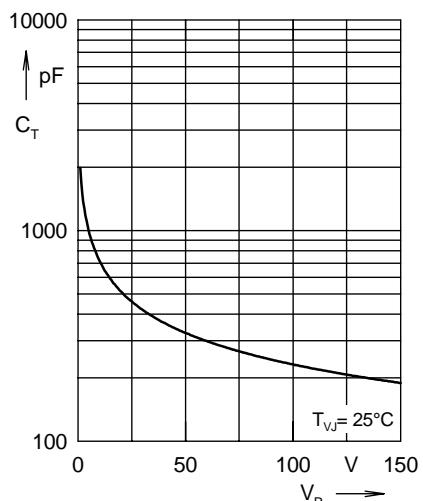


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

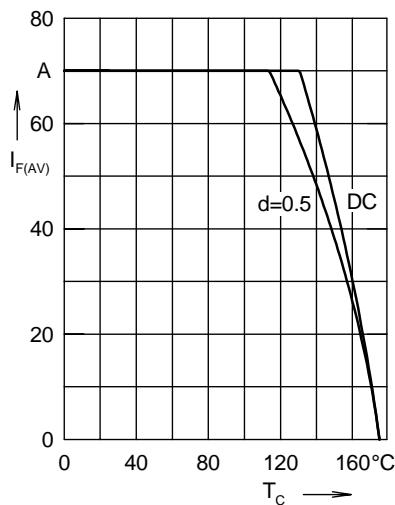


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

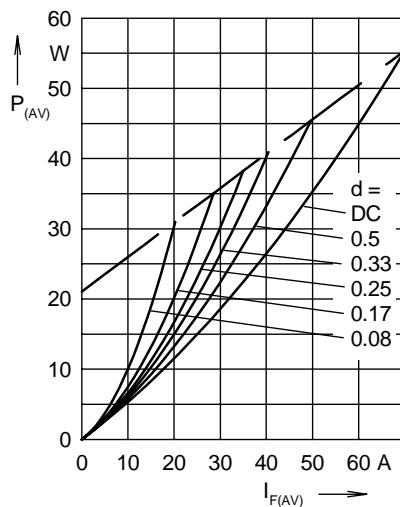


Fig. 5 Forward power loss characteristics

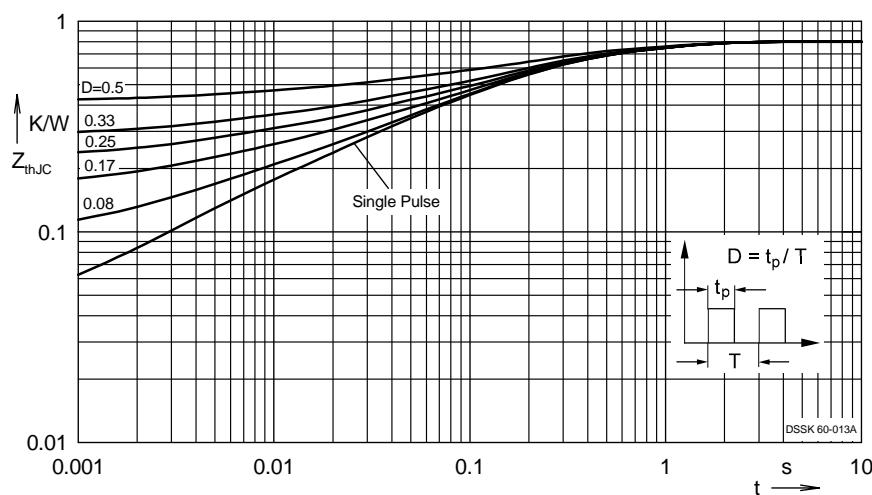


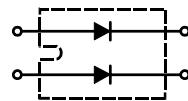
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Power Schottky Rectifier

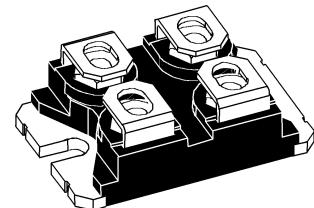
I_{FAV} = 2x100 A
V_{RRM} = 150 V
V_F = 0.78 V

Preliminary Data

V _{RSM} V	V _{RRM} V	Type
150	150	DSS 2x101-015A



miniBLOC, SOT-227 B



Symbol	Conditions	Maximum Ratings	
I _{FRMS}		150	A
I _{FAVM}	T _C = 110°C; rectangular, d = 0.5	100	A
I _{FAVM}	T _C = 110°C; rectangular, d = 0.5; per device	200	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	1200	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dV/dt) _{cr}		18000	V/µs
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	310	W
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~
M _d	mounting torque (M4) terminal connection torque (M4)	1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in. Nm/lb.in.
Weight	typical	30	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	4 40	mA mA
V _F	I _F = 100 A; T _{VJ} = 125°C I _F = 100 A; T _{VJ} = 25°C I _F = 200 A; T _{VJ} = 125°C	0.78 0.90 0.99	V V V
R _{thJC} R _{thCH}		0.1	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

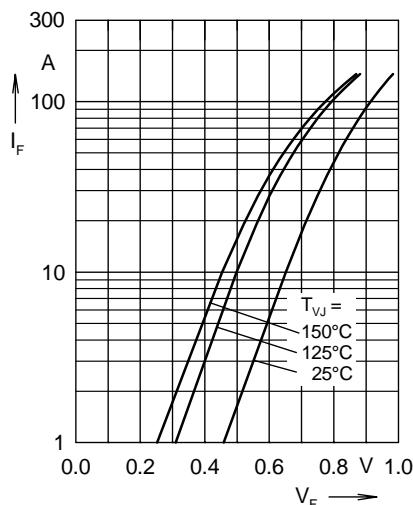


Fig. 1 Maximum forward voltage drop characteristics

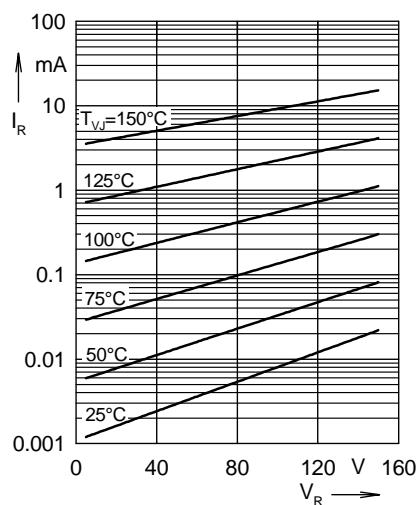


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

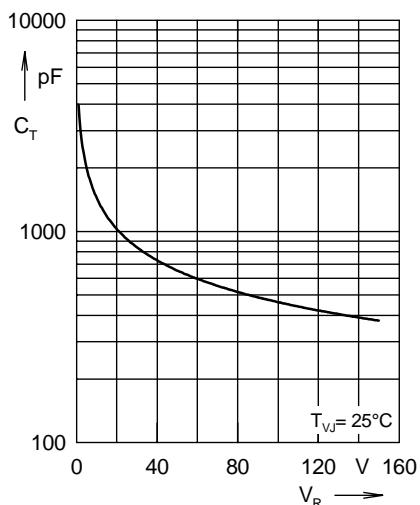


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

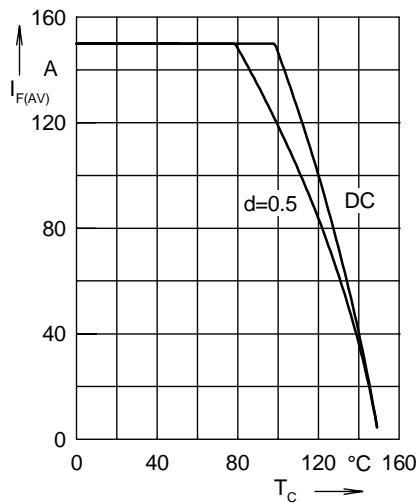


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

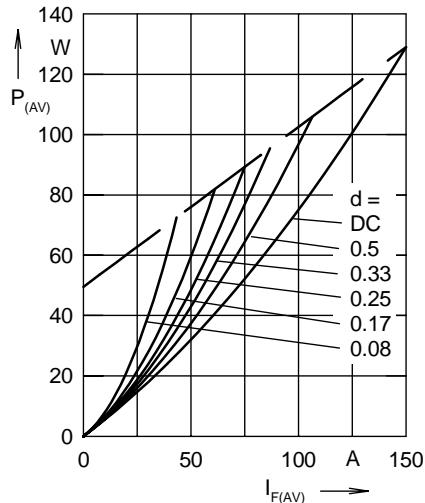


Fig. 5 Forward power loss characteristics

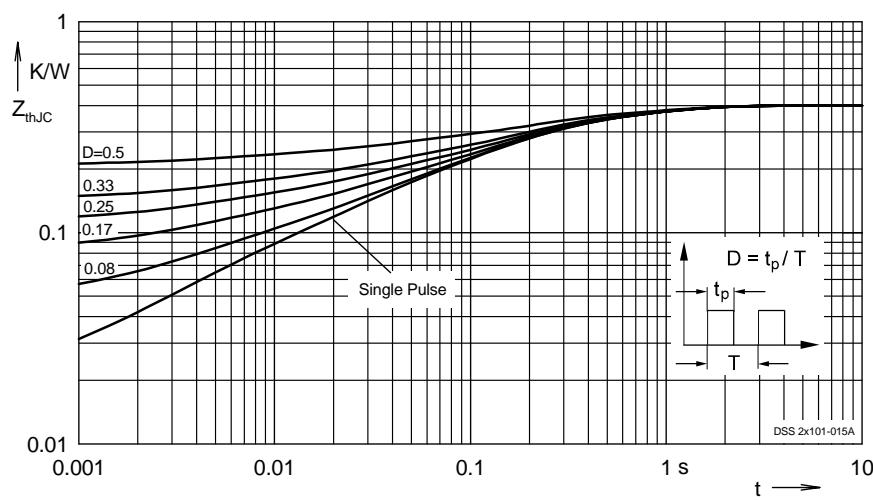


Fig. 6 Transient thermal impedance junction to case at various duty cycles

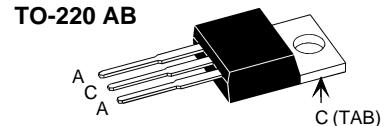
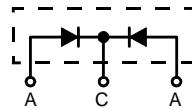
Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x5 A
V_{RRM} = 180 V
V_F = 0.62 V

Preliminary Data

V _{RSM}	V _{RRM}	Type
V	V	
180	180	DSSK 10-018A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAV}	T _C = 165°C; rectangular, d = 0.5	5	A
I _{FAV}	T _C = 165°C; rectangular, d = 0.5; per device	10	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	120	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dv/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R	① T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	0.3 2.5	mA mA
V _F	I _F = 5 A; T _{VJ} = 125°C I _F = 5 A; T _{VJ} = 25°C I _F = 10 A; T _{VJ} = 125°C	0.62 0.78 0.68	V V V
R _{thJC}		1.7	K/W
R _{thCH}		0.5	K/W

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM}-values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see pages D2 - 87-88

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

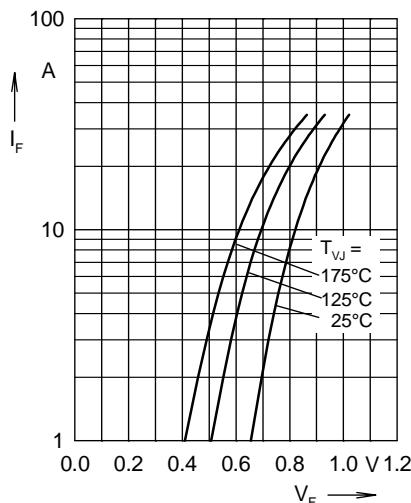


Fig. 1 Maximum forward voltage drop characteristics

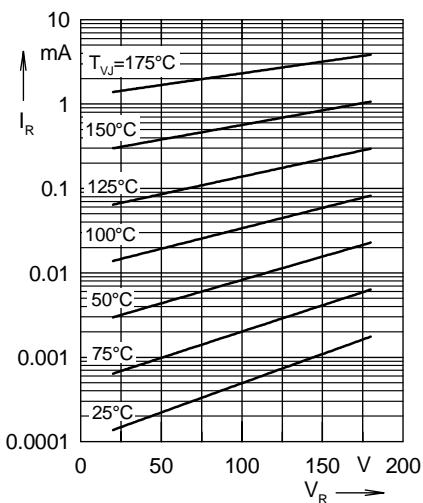


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

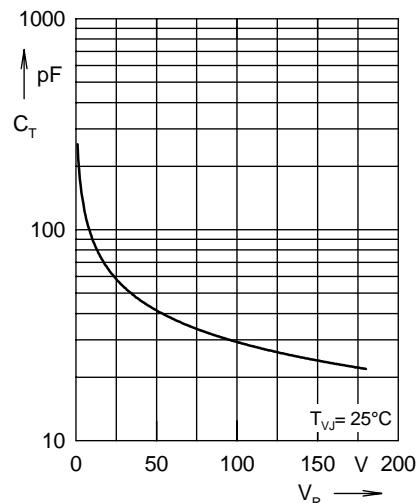


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

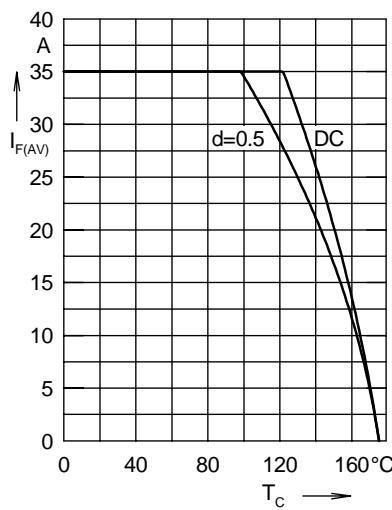


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

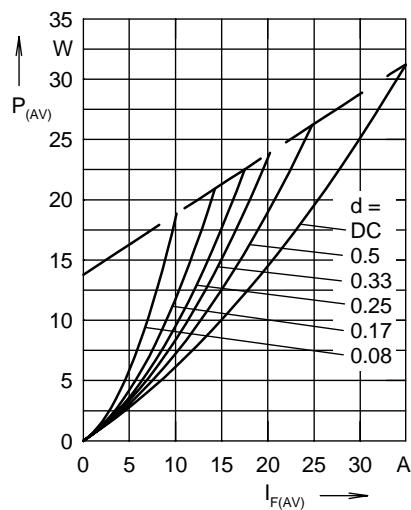


Fig. 5 Forward power loss characteristics

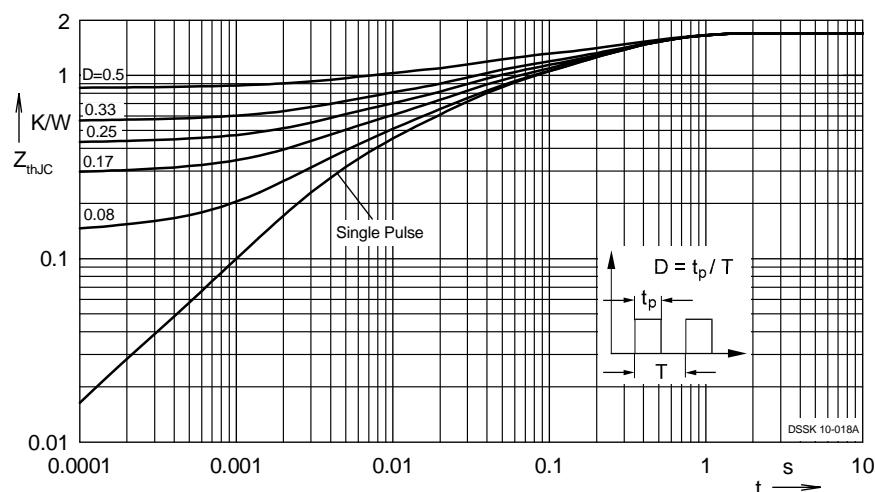


Fig. 6 Transient thermal impedance junction to case at various duty cycles

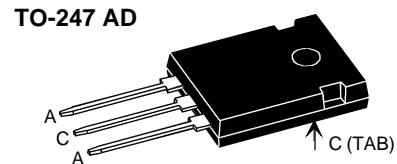
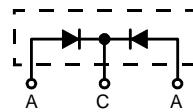
Note: All curves are per diode

Power Schottky Rectifier with common cathode

I_{FAV} = 2x15 A
V_{RRM} = 180 V
V_F = 0.72 V

Preliminary Data

V _{RSM} V	V _{RRM} V	Type
180	180	DSSK 30-018A



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		50	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5	15	A
I _{FAV}	T _C = 150°C; rectangular, d = 0.5; per device	30	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	120	A
E _{AS}	I _{AS} = tbd A; L = 180 µH; T _{VJ} = 25°C; non repetitive	tbd	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	tbd	A
(dV/dt) _{cr}		tbd	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	90	W
M _d	mounting torque	0.8...1.2	Nm
Weight	typical	6	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 100°C V _R = V _{RRM}	0.3 2.5	mA mA
V _F	I _F = 15 A; T _{VJ} = 125°C I _F = 15 A; T _{VJ} = 25°C I _F = 30 A; T _{VJ} = 125°C	0.72 0.86 0.87	V V V
R _{thJC} R _{thCH}		1.7 0.25	K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

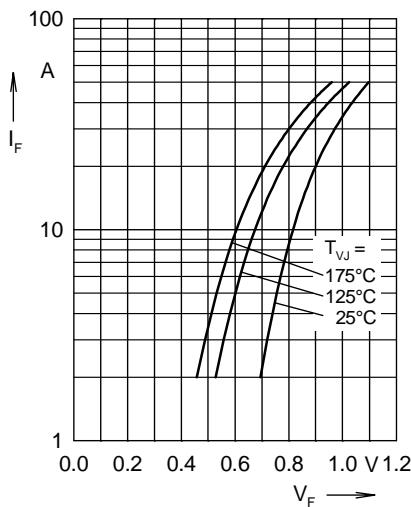


Fig. 1 Maximum forward voltage drop characteristics

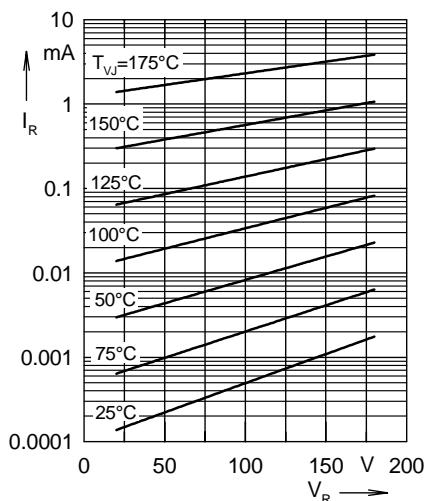


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

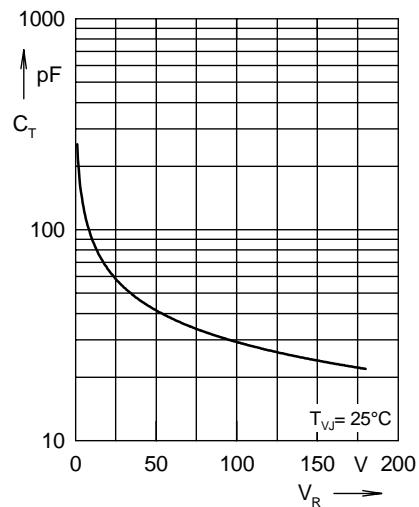


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

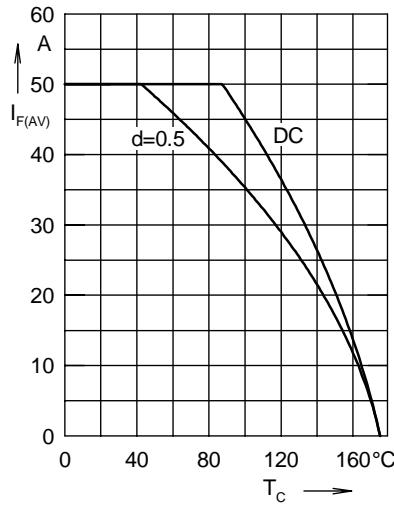


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

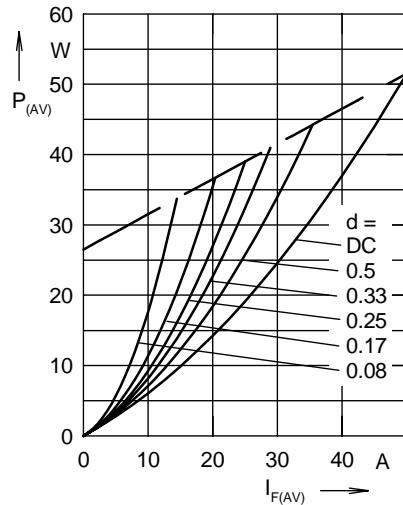


Fig. 5 Forward power loss characteristics

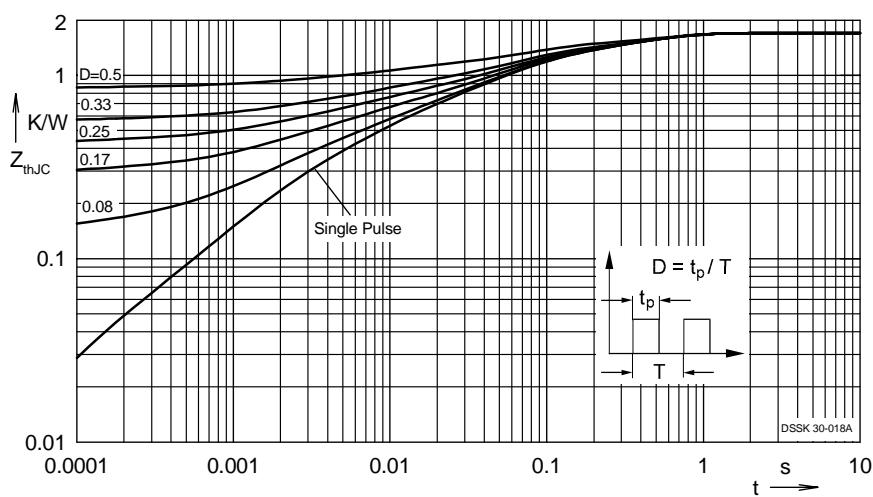
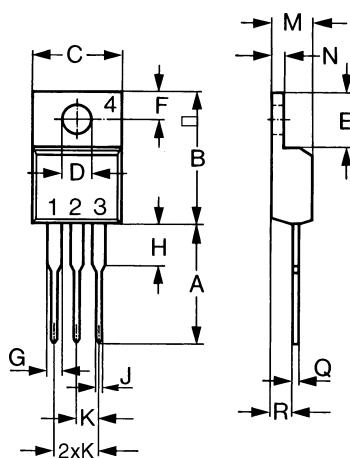


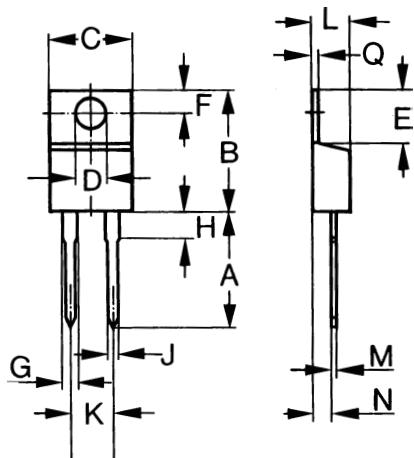
Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

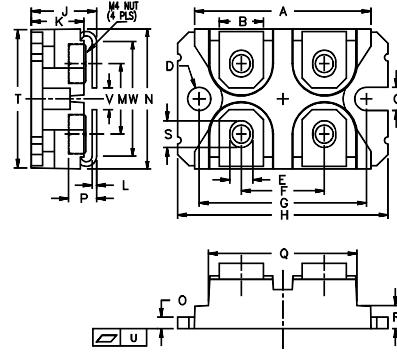
Dimensions

TO-220 AB


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.38	0.56	0.015	0.022
R	2.29	2.79	0.090	0.110

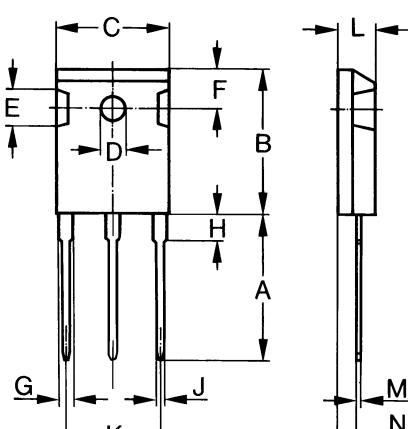
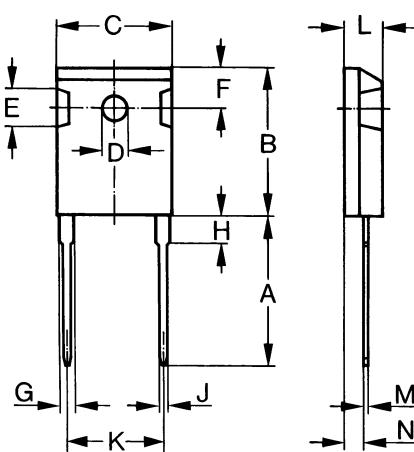
TO-220 AC


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	14.73	0.500	0.580
B	14.23	16.51	0.560	0.650
C	9.66	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.42	0.100	0.135
G	1.15	1.77	0.045	0.070
H	-	6.35	-	0.250
J	0.64	0.89	0.025	0.035
K	4.83	5.33	0.190	0.210
L	3.56	4.82	0.140	0.190
M	0.38	0.56	0.015	0.022
N	2.04	2.49	0.080	0.115
Q	0.64	1.39	0.025	0.055

miniBLOC, SOT-227 B


M4 screws (4x) supplied

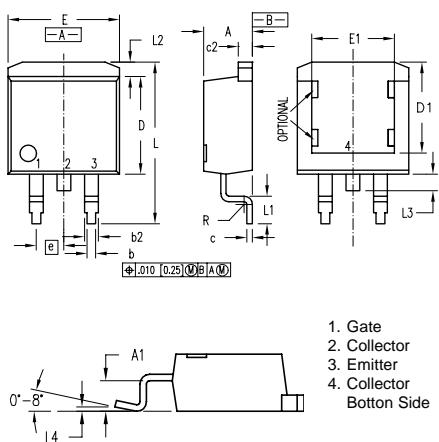
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	19.81	21.08

TO-247 AD and ISOPLUS 247™
TO-247 AD and ISOPLUS 247™


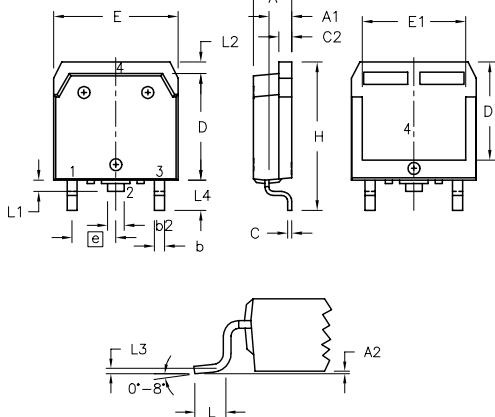
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D*	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

* ISOPLUS 247™ without hole

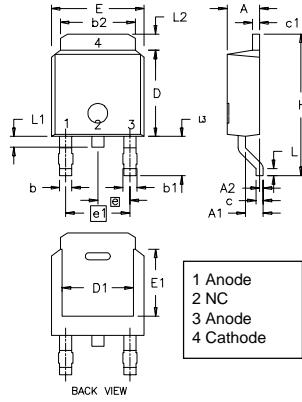
Dimensions

TO-263 AB


Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.315	.350
E	9.65	10.29	.380	.405
E1	6.22	8.13	.245	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.20	0	.008
R	0.46	0.74	.018	.029

TO-268 AA


Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25	BSC	.010	BSC
L4	3.80	4.10	.150	.161

TO-252 AA


Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	2.19	2.38	.086	.094
A1	0.89	1.14	.035	.045
A2	0	0.13	0	.005
b	0.64	0.89	.025	.035
b1	0.76	1.14	.030	.045
b2	5.21	5.46	.205	.215
c	0.46	0.58	.018	.023
c1	0.46	0.58	.018	.023
D	5.97	6.22	.235	.245
D1	4.32	5.21	.170	.205
E	6.35	6.73	.250	.265
E1	4.32	5.21	.170	.205
e	2.28	BSC	.090	BSC
e1	4.57	BSC	.180	BSC
H	9.40	10.42	.370	.410
L	0.51	1.02	.020	.040
L1	0.64	1.02	.025	.040
L2	0.89	1.27	.035	.050
L3	2.54	2.92	.100	.115

